## \*\*\*\*\* QUERY RESULTS \*\*\*\*\*

=> d his 140

L40

(FILE 'WPIX' ENTERED AT 15:11:30 ON 28 OCT 2009) 14 S L38 OR L39 L40 => d que 140 18364 SEA FILE=HCAPLUS ABB=ON PLU=ON ((SELF(W)ASSEMBL?)(W) (MONOLAYER# OR MONO(W)LAYER#)) L9 14707 SEA FILE=HCAPLUS ABB=ON PLU=ON "SAM" L10 1828847 SEA FILE=HCAPLUS ABB=ON PLU=ON PHENYL OR BIPHENYL OR TERPHENYL L11 70335 SEA FILE=HCAPLUS ABB=ON PLU=ON ANTHRACYL OR NAPHTHYL OR BIPYRIDYL OR TERPYRIDYL 6620 SEA FILE=HCAPLUS ABB=ON PLU=ON THIOPHENYL OR BITHIENYL OR L12 TERTHIENYL OR PYRROLYL L13 12 SEA FILE=HCAPLUS ABB=ON PLU=ON (BI OR TRI)(W) CYCLOALKANE# OR TETRA(W)CYCLOALKANE# 258 SEA FILE=WPIX ABB=ON PLU=ON (L8 OR L9) AND ((L10 OR L11 OR L34 L12 OR L13)) 14 SEA FILE=WPIX ABB=ON PLU=ON L34 AND LITHOGRAPH? L35 37 SEA FILE-WPIX ABB-ON PLU-ON L34 AND (SURFAC?) (2A) (TRANSIT? L36 OR MODIF? OR PATTERN?) 8 SEA FILE=WPIX ABB=ON PLU=ON L36 AND LITHOGRAPH? L37 14 SEA FILE=WPIX ABB=ON PLU=ON L35 OR L37 L38 6 SEA FILE=WPIX ABB=ON PLU=ON L38 AND (ARYL OR HETERO(W)ARYL L39 OR ALICYCLIC OR HETERO(W)CYCLIC)

#### => d 140 1-14 iall abeq tech abex

L40 ANSWER 1 OF 14 WPIX COPYRIGHT 2009 THOMSON REUTERS on STN

14 SEA FILE=WPIX ABB=ON PLU=ON L38 OR L39

ACCESSION NUMBER: 2008-M49260 [73] WPIX

DOC. NO. CPI: C2008-385367 [73] DOC. NO. NON-CPI: N2008-919671 [73]

TITLE: Production of nanocomposite film used, e.g. for optical

device, photovoltaic cell, or sensor protection device,

by co-depositing surface polymerizing organic

monomers/oligomers and gaseous lead salt clusters on

polymer film

DERWENT CLASS: A26; A89; L03; U11; U12

INVENTOR: ASUNSKIS D J; BOLOTIN I L; HANLEY L; WROBLE A T; ZACHARY

ΑМ

PATENT ASSIGNEE: (UNII-C) UNIV ILLINOIS FOUND

COUNTRY COUNT: 120

#### PATENT INFORMATION:

PATENT NO	KIND	DATE	WEEK	LA	PG	MAIN	IPC
WO 2008108	8809 A2	20080912	(200873)*	ΕN	54[10]		
WO 2008108	809 A3	20090416	(200926)	EN			

#### APPLICATION DETAILS:

PATENT NO	KIND	APPLICATION	DATE
WO 2008108809 WO 2008108809		WO 2007-US19894 WO 2007-US19894	

PRIORITY APPLN. INFO: US 2006-843996P 20060912 US 2006-843996P 20060912

INT. PATENT CLASSIF.:

IPC ORIGINAL: C23C0014-06 [I,C]; C23C0014-06 [I,A]; C23C0014-06 [I,C];

C23C0014-32 [I,C]; C23C0014-32 [I,A]; C23C0014-32 [I,C]

ECLA: C23C0014-06; C23C0014-22

BASIC ABSTRACT:

WO 2008108809 A2 UPAB: 20090430

 ${\tt NOVELTY}$  - Production of a nanocomposite film comprises co-depositing surface polymerizing organic monomers/oligomers and gaseous lead salt clusters on a polymer film.

USE - Method for the production of a nanocomposite film used, e.g. for an optical device, a photovoltaic cell (claimed), or a sensor protection device.

ADVANTAGE - Gaseous deposition allows direct control over nanocrystal size and density, improves flexibility in the choice of organic phase, and is compatible with lithographic methods.

DESCRIPTION OF DRAWINGS - The drawing is a schematic view of an arrangement for producing nanocomposite films. MANUAL CODE: CPI: A11-B05; A12-E11B; A12-L02A; A12-W14; L03-B05K1

EPI: U11-C01J5; U11-C13; U12-A02A1; U12-A02A4B

TECH

CERAMICS AND GLASS - Preferred Material: The substrate comprises a ceramic material.

INORGANIC CHEMISTRY - Preferred Material: The substrate comprises a metal, a semiconductor, or a nanotube. The lead salt clusters comprise lead sulfides, lead selenide, and/or lead telluride.

ORGANIC CHEMISTRY - Preferred Component: The organic ions comprise H+, H2S+, SO3+, C2Hx+, C4H4S+, C6H6+, C6H7N+, C5H5N+, and/or C4H4O+. The organic ions comprise thiophene.

POLYMERS - Preferred Method: The polymeric film is prepared by co-depositing organic ions and neutral oligomers on a substrate. Preferred Component: The neutral oligomer comprises terthiophene, sexithiophene, ethylenedioxythiophene, terphenyl, quaterphenyl, sexiphenyl, poly(phenylene vinylenes), porphyrins, phthalocyanines, pentacene, and/or diphenyl perylene. The neutral oligomer comprises an oligomer of thiophene including bithiophene, terthiophene, quarterthiophene, pentathiophene, hexathiophene, septathiophene, and/or octathiophene. Preferred Material: The substrate comprises a plastic, polymer, or a self-assembled monolayer.

L40 ANSWER 2 OF 14 WPIX COPYRIGHT 2009 THOMSON REUTERS on STN

ACCESSION NUMBER: 2008-K90834 [64] WPIX

DOC. NO. CPI: C2008-316110 [64] DOC. NO. NON-CPI: N2008-797650 [64]

TITLE: Substrate useful in electroluminescent device for forming

pattern of nanocrystals comprises inorganic layer with

modified surface of bifunctional

molecule having affinity for nanocrystals and surface of

inorganic layer at opposite ends

DERWENT CLASS: A85; E19; L03; P42; P73; T04; U11; U14

INVENTOR: CHO G T; CHO K S; CHOI J Y; CHOI S J; JUNG D Y; LEE J H;

SHIN H J; SONG I Y; YI D K; YOON S M; DONG K Y; DUK Y J; HYEON J S; IN Y S; IN Z; JAE Y C; JONG H L; KEUN T C;

KYUNG S C; SAI S; SEON M Y; SEONG J C

PATENT ASSIGNEE: (SMSU-C) SAMSUNG ELECTRONICS CO LTD

COUNTRY COUNT: 3

PATENT INFORMATION:

PATENT NO	KIN	D DATE	WEEK	LA	PG	MAIN IPC
US 2008018207 JP 2008183702			(200864) * (200864)			
KR 825176	В1	20080424	(200924)	KO		

#### APPLICATION DETAILS:

PATENT NO	KIND	APPLICATION	DATE
US 20080182072 JP 2008183702 F KR 825176 B1		US 2007-757018 JP 2007-274254 KR 2007-8357 2	20071022
PRIORITY APPLN. INFO: INT. PATENT CLASSIF.:	: KR 2007-8357	20070126	
	B05D0005-00 [I,A]; B B29C0059-02 [I,C]; B B32B0003-14 [I,A]; B B82B0001-00 [I,C]; B	332B0003-02 [I,A 332B0003-14 [I,C 382B0003-00 [I,A	]; B29C0059-02 [I,A]; ]; B32B0003-02 [I,C]; ]; B82B0001-00 [I,A]; ]; B82B0003-00 [I,C]; ]; H01L0021-027 [I,A];
USCLASS NCLM:	428/148.000 427/180.000; 428/156	. 000	
JAP. PATENT CLASSIF.:	•	.000	
MAIN/SEC.:	B29C0059-02 B; B82B0	0001-00; B82B000	3-00; H01L0021-30 502
MAIN: SECONDARY: FTERM CLASSIF.:	B29C0059-02 B; B82B0	5F046/AA17; 5F	046/AA28; 4F209/AD08;

BASIC ABSTRACT:

US 20080182072 A1 UPAB: 20090423

NOVELTY - A substrate (S1) for forming a pattern comprises an inorganic layer having a modified surface, where the modified surface is formed by coating a surface of the inorganic layer with a bifunctional molecule comprising a functional group that has an affinity for a nanocrystal at one end of the molecule and a functional group that has an affinity for the surface of the inorganic layer at the other end of the molecule.

4F209/AJ08; 4F209/AJ09; 4F209/PA02; 4F209/PB01;

DETAILED DESCRIPTION - INDEPENDENT CLAIMS are included for the following:

4F209/PN06; 4F209/PN09; 4F209/PQ11

- (1) an electroluminescent device (D1) comprising the substrate (S1) and a nanocrystal light-emitting layer (440); and
- (2) forming (M1) a nanocrystal pattern involving contacting a stamp comprising a nano-scale concavo-convex pattern formed on it that comprises a nanocrystal-coated surface against a substrate having an inorganic layer formed on it; and transferring and forming a nanocrystal pattern on the substrate (S1).

USE - In an electroluminescent (EL) device i.e. inorganic EL device or an organic EL device useful for forming pattern of nanocrystals; as lightemitting materials for light-emitting layers of various devices such as electroluminescent devices, display devices (claimed), backlight units (BLU) and nano-bio devices; in an ink-jet printing, self-assembly method, nanoimprinting lithography technique and semiconductor industry; as a promising ultra-fine patterning technique useful in nano-devices.

ADVANTAGE - The substrate utilizes the stable pattern of nanocrystals exhibiting quantum confinement effects and demonstrates electrical, magnetic,

optical, chemical and mechanical properties; have high luminescence efficiency and a small half bandwidth within the photoluminescence spectrum; ensures the efficient transfer high-resolution fine patterns through a low-cost and simple process in an effective manner that improves reliability of the nanocrystal thin film.

DESCRIPTION OF DRAWINGS - The figure shows an exemplary schematic process view of the fabrication of an electroluminescent device using the nanocrystal patterning method.

Anode (410)

Electron transport layer (420)

Surface-modified layer (430)

Nanocrystal light-emitting layer (440)

Hole transport layer. (450) MANUAL CODE:

CPI: A11-B05D; A11-

C04B1; A11-C04B2; A12-E11; A12-E11C;

A12-L02B2; A12-W14; E05-E02D; E05-E03B; E05-G03; E10-A15F; E10-B01A4; E10-B01C1; E10-B01C3; E10-B01D; E10-B01E; E10-B02E; E10-B03B2; E10-C02D2; E10-C04; E10-D03D; E10-E03H; E10-E03M; E31-D04; E31-G; E31-H05; E31-K07; E31-L; E31-P03; E31-P05A; E31-P06D; E34-C02; E34-E01; E35; L03-G05; L03-G05F; L04-C06 EPI: T04-G02J; U11-C04J; U11-C05E; U14-J02D1

TECH

INORGANIC CHEMISTRY - Preferred Substrate: The substrate (S1) is a glass substrate, silicon substrate or plastic substrate, and is coated with an electrically conductive material. Preferred Components: The inorganic layer is formed of a material selected from metal oxides and/or metal nitrides. The metal oxide selected from titanium dioxide, zinc oxide, silicon dioxide, tin dioxide, tungsten trioxide, tantalum trioxide, barium titanate, barium zirconate, zirconium dioxide, hofnium dioxide, aluminum trioxide, yttrium trioxide, and zirconium orthosilicate. The metal nitride is silicon nitride and/or at least one metal oxide. In device (D1), the nanocrystal light-emitting layer comprises nanocrystals selected from metal nanocrystals containing gold, silver, platinum, palladium, cobalt, copper, molybdenum and/or their alloys; Group II-VI compound semiconductor nanocrystals containing cadmium sulfate, cadmium selenite, cadmium tellurite, zinc sulfate, zinc selenite, zinc tellurite, mercury sulfate, mercury selenite, mercury tellurite and/or their alloys; Group III-V compound semiconductor nanocrystals containing gallium nitrate, gallium phosphate, gallium arsenate, indium phosphate, indium arsenate and/or their alloys; and lead sulfate, lead selenite, lead tellurite and/or their alloys. Preferred Method: The method (M1) further involves preparing a stamp having a pattern corresponding to a nanocrystal pattern formed on the substrate (S1); coating nanocrystals on a surface of the patterned stamp to form a nanocrystal thin film; surface-treating an inorganic layer on the substrate (S1) with a bifunctional molecule to form a surface treated substrate; and contacting the stamp to the surface-treated substrate to transfer the nanocrystal pattern. In method (M1), the nanocrystal coating is carried out by spin coating, dip coating, spray coating, or blade coating. The bifunctional molecule treatment is carried out at 1-15 degrees C for 10 minutes to 1 hour using a solution (0.001-10 wt.%) obtained by dissolving the bifunctional molecules in a solvent selected from water, an organic solvent and a mixture of water and solvent. The bifunctional molecule treatment is application of the solution using a wet coating method selected from spin coating, dip coating, spray coating, a dispensing or sol-gel method, printing and casting, or a vapor-phase coating method selected from chemical vapor deposition (CVD) and vacuum deposition. ORGANIC CHEMISTRY - Preferred Components: The bifunctional molecule is a compound capable of forming a self-assembled

monolayer and is of formula A1-X-B1 (I). The bifunctional molecule

is selected from 2-carboxyethylphosphonic acid, mercaptoacetic acid, mercaptohexanol, and cysteamine. In method (M1), the stamp is formed of a material selected from polydimethylsiloxane, polyimide and polymethylmethacrylate. The organic solvent is selected from pyridine, ethanol, propanol, butanol, pentanol, hexanol, toluene, chloroform, chlorobenzene, tetrahydrofuran, cyclohexane, cyclohexene, methylene chloride, pentane, hexane, heptane, octane, nonane, decane and/or undecane.

Al=functional group selected from acetyl, acetic acid, phosphine, phosphonic acid, alcohol, vinyl, amide, phonyl, amine, acrylic, silane, cyano, and thiol;

X=1-20C linear or branched carbon chain or siloxane chain; and B1=functional group selected from carboxylic acid, amine, phosphine, phosphonic acid and thiol.

ABEX EXAMPLE - Sylgard 184 (RTM: silicone elastomer base) and a curing agent were mixed at a weight ratio of 10:1 and stirred for 5 minutes. Bubbles were removed using a vacuum pump and the mixture was dropped on a wafer. Then, the wafer was cured in an oven at 80 degrees C for 1 hour and removed to prepare a polydimethylsiloxane (PDMS) stamp. A dispersion of cadmium selenite (CdSe)/zinc sulfate (ZnS) nanoparticles in hexane (1 wt.%) was dropped on the PDMS stamp, washed with isopropyl alcohol and spin-coated at 4000 rate per minutes for 20 seconds to form a nanocrystal thin film on the PDMS stamp. An indium tin oxide-patterned glass substrate was sequentially washed with a neutral detergent, deionized water, water and isopropyl alcohol and subjected to ultra-violet-ozone treatment. The percentage of isopropyl alcohol was 99 wt. %. The ultra-violet treatment was performed for 10 minutes. Then, the prepared substrate was placed in a solution of 2-carboxyethylphosphonic acid for 2 hours, and the solution was sufficiently adsorbed by the substrate. The substrate was washed with ethanol and subjected to heat treatment at 100 degrees C for 10 minutes. The resulting CdSe/ZnS nanoparticle-arranged stamp was in contact with the surface-treated substrate for 30 seconds, detached, and then subjected to heat treatment at 100 degrees C for 5 minutes to prepare a nanocrystal-patterned substrate (test). A control nanocrystal-patterned substrate was prepared in the same manner as that of the test nanocrystal-patterned substrate except that the surface of an inorganic layer was not subjected to surface treatment. The test/control substrates were evaluated for luminescence intensity. The test/control substrates showed luminescence intensity of approximately 0.7/0.25 au.

L40 ANSWER 3 OF 14 WPIX COPYRIGHT 2009 THOMSON REUTERS on STN

ACCESSION NUMBER: 2007-445316 [43] WPIX

DOC. NO. CPI: C2007-161851 [43] DOC. NO. NON-CPI: N2007-335970 [43]

TITLE: Patterning molecules, e.g. proteins, on substrate useful

in sensor involves using a micro-contact printing

process, where patterned molecules are kept in solvent or

are covered by solvent during entire micro-contact

printing process

DERWENT CLASS: A89; A97; B04; D16; P42; P75

INVENTOR: KRON G; MAYER D; OFFENHAEUSSER A; SCHWAAB D; WESSELS J;

YASUDA A

PATENT ASSIGNEE: (KERJ-C) FORSCHUNGSZENTRUM JUELICH GMBH; (SONY-C) SONY

DEUT GMBH

COUNTRY COUNT: 38

PATENT INFORMATION:

PATENT NO KIND DATE WEEK LA PG MAIN IPC

US	20070098899	A1	20070503	(200743)*	ΕN	13[4]
ΕP	1782886	Α1	20070509	(200743)	EN	
CN	1958301	Α	20070509	(200760)	ZH	

#### APPLICATION DETAILS:

PATENT NO	KIND	APPLICATION DATE	
US 20070098899 EP 1782886 A1 CN 1958301 A		US 2006-477655 20060630 EP 2005-23880 20051102 CN 2006-10143605 20061102	
PRIORITY APPLN. INFO: INT. PATENT CLASSIF.:	: EP 2005-23880	20051102	
IPC ORIGINAL:	B01J0019-00 [I,A]; F	B01J0019-00 [I,C]; B01L0011-00 [I,A	A];
	B01L0011-00 [I,C]; F	B05C0001-00 [I,A]; B05C0001-00 [I,C	C];
	B05D0001-28 [I,A]; H	B05D0001-28 [I,C]; B05D0005-00 [I, <i>F</i>	A];
	B05D0005-00 [I,C]; F	B41M0001-00 [I,A]; B41M0001-00 [I,C	C];
	B41M0003-00 [I,A]; H	B41M0003-00 [I,A]; B41M0003-00 [I,C	C];
	B41M0003-00 [I,C];	C12N0011-00 [I,A]; C12N0011-00 [I,C	C];
	C12N0015-09 [I,A]; (	C12N0015-09 [I,C]; C12Q0001-68 [I,F	A];
	C12Q0001-68 [I,C]; (	G01N0033-48 [I,A]; G01N0033-48 [I,C	C]
ECLA:	B41M0003-00P; B81C00	001-00C8; G03F0007-00A	_
ICO:	L01J0219:00C10B4; L0	01J0219:00C2D8; L01J0219:00C2L8;	
	L01J0219:00C4L12; L(	01J0219:00C4L2; L01L0003:02D4;	
	Y01N0004:00	,	
USCLASS NCLM:	427/256.000		
NCLS:	118/211.000; 427/429	9.000	
BASIC ABSTRACT:	,		

US 20070098899 A1 UPAB: 20080918

NOVELTY - Patterning (M1) molecules on a substrate involves using a micro-contact printing process, where the patterned molecules are kept in solvent or are covered by solvent during the entire micro-contact printing process.

 ${\tt DETAILED}$  <code>DESCRIPTION</code> — <code>INDEPENDENT</code> <code>CLAIMS</code> are included for the following:

- (1) a substrate is produced by the method (M1) and comprising a pattern of molecules have retained their function and/or activity and/or native conformation;
- (2) a device for performing the method (M1) comprising a first unit holding a solution of patterned molecules, patterned surface (preferably in the form of a stamp), substrate, kept in a solvent or covered by a solvent; a second unit to transfer the molecules is patterned form the first unit to the patterned surface; a third unit to transfer the patterned molecules from the patterned surface to the substrate; a fourth unit to ensure that the patterned molecules are kept in a solvent or covered by a solvent during the transfer from the first unit to the patterned surface to the substrate.
- USE For patterning molecules e.g. protein molecules, redox proteins, nucleic-acid binding proteins, enzymes, metallo-proteins, cytochrome c, azurin, cytoskeleton-proteins, antibodies, nucleic acids, deoxyribonucleic acid, ribonucleic acid, peptide nucleic acid, aptamers, lipids, phospholipids and sphingolipids on a substrate which is useful in a sensor, a bioreactor or for guiding cell growth (all claimed).

ADVANTAGE - The method allows to pattern biomolecules to dimensions down to 150 nm, while preserving their structural integrity and functionality by using an in-situ process; allows the immobilization and patterning of molecules on a substrate; is easy to perform even with biological macromolecules whilst maintaining their functionality; prevents drying or denaturation of the molecules. The molecules is patterned retain their function and/or activity and/or native conformation throughout the entire process, due to their kept in solvent or covered

by solvent during the entire micro-contact printing process. The patterned molecules are kept under physiological conditions such as  $\mathfrak{p}\mathfrak{A}$  and salinity, throughout the entire micro-contact printing process. The patterned molecules having a length of approximately 10 nm - 500microns (preferably 10 nm - 200 microns, especially approximately 10 nm - 150 microns).

MANUAL CODE:

CPI: A12-L04; B04-B01B; B04-B04C; B04-C01; B04-E01; B04-E07F; B04-E10; B04-F01; B04-G01; B04-K01; B04-L01; B04-N04; B11-C08B; B12-K04; D05-A01A; D05-A01B; D05-H10; D05-H11

TECH

BIOTECHNOLOGY - Preferred Components: The substrate comprises a modified with molecular layers with antibodies for binding corresponding antigens, or modified with molecular layers with antigens for binding corresponding antibodies; or modified with molecular layers with receptors for specific binding of molecules (preferably gold modified with a mercapto undecanoic acid layer (MUA)).

IMAGING AND COMMUNICATION - Preferred Method: The method (M1) involves a) providing molecules to be patterned in a solvent and providing a patterned surface (preferably in the form of a stamp),

b) transferring the molecules are patterned onto the patterned surface and immobilizing them whilst keeping the molecules in the solvent or covered by the solvent, c) providing a substrate and bringing the patterned surface having the molecules immobilized into conformal contact with the substrate thus creating a pattern of the molecules on the substrate, whilst keeping the molecules in the solvent or covered by the solvent. In the step a), the molecules are provided in the solvent and are first immobilized on an ink-pad (preferably in the form of a non-patterned surface), within the solvent. The

molecules are provided in the solvent. In the step b), the ink-pad having the molecules immobilized is brought into conformal contact with the patterned surface in a first solvent environment

containing the molecules is patterned, the solvent and, optionally, a buffer, thus transferring the molecules onto the patterned surface and immobilizing. The molecules are immobilized on the patterned surface within the solvent. The step b) occurs by immersing the patterned surface in the solvent. The ink-pad having the molecules immobilized is brought into conformal contact

with the patterned surface in a second solvent environment containing the solvent and, optionally, a buffer, after

transfer of the ink-pad having the molecules immobilized to the second solvent environment, thus transferring the molecules onto the patterned surface and immobilizing. In the step c), the substrate is provided in a second solvent environment containing the

solvent and, optionally a buffer, and the patterned surface having the molecules immobilized, after step b), molecule is transferred to the second solvent environment and is brought into conformal contact with the substrate. The substrate is provided in a third solvent environment containing the solvent and, optionally, a buffer, and

the patterned surface having the molecules immobilized, after step b), molecule is transferred to the third solvent environment and is brought into conformal contact with the substrate. The substrate is provided in a fourth solvent environment containing the solvent and, optionally, a buffer, and wherein the patterned surface having the molecules immobilized, after step b), molecule is transferred to the fourth solvent environment and is brought into conformal contact with the substrate. The substrate is provided without a solvent environment, and the patterned surface having

the molecules immobilized is brought into conformal contact with the substrate whilst keeping the molecules covered by the solvent, and the patterned surface is transferred to a fifth solvent

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environment containing the solvent and, optionally a buffer, whilst is in
contact with the substrate, the transfer of the patterned
surface and the substrate occurring immediately after the
patterned surface is brought into conformal contact with
the substrate, thus avoids a drying of the patterned
surface on the substrate. The bringing into conformal contact of
the patterned surface with the substrate of step c)
occurs in a period of not greater than 180 (preferably not greater than
120, especially not greater than 1, particularly 1) minutes after
immobilizing the molecules is patterned on the patterned
surface. After step c), the patterned surface
is lifted from the substrate, thereby leaving behind a substrate having a
pattern of the molecules. The substrate having a pattern of molecules is
kept in or covered by solvent optionally containing a buffer. The
micro-contact printing process occurs in the absence of a drying step.
Preferred Components: The ink-pad (preferably at least a surface of the
ink-pad) is made from a material selected from the single-crystalline
materials and polycrystalline materials (such as silicon, silicon oxide,
layered composite systems, silicon oxide on silicon, metal layers on
silicon/siliconoxide); amorphous materials (such as glass); plastics (such
as elastomers, preferably polydimethylsiloxane, plastomers, polyolefines,
polyolefinic plastomers), ionomers, resist materials, (such as
ultraviolet-nanoimprint lithography-resists (UV-NIL-resists)).
The second unit is an ink-pad (preferably a non-patterned
surface).
INORGANIC CHEMISTRY - Preferred Components: The substrate comprises a
spacer layer and/or a binding layer which facilitates binding of the
substrate to the molecules is patterned through covalent binding,
electrostatic forces, Vander Waals forces, H-bonding and/or London forces.
The substrate is selected from the metals and semi metals, single or
polycrystalline materials (preferably single or polycrystalline metals and
semi metals, especially gold, platinum, silicon) or composite materials
(preferably single or polycrystalline composites, especially siliconoxide,
gallium arsenide) or amorphous composite materials (preferably glass). The
patterned surface is made from a material selected from
the single-crystalline materials and polycrystalline materials (such as
silicon, silicon oxide, layered composite systems, silicon oxide on
silicon, metal layers on silicon/siliconoxide); amorphous materials (such
as glass); plastics (such as elastomers, preferably polydimethylsiloxane),
plastomers (preferably polyolefines, especially polyolefinic plastomers),
ionomers, resist materials (such as ultraviolet-nanoimprint
lithography-resists (UV-NIL-resists)).
POLYMERS - Preferred Components: The substrate comprises a plastics
(preferably elastomers, especially polydimethylsiloxane), plastomers
(preferably polyolefines), ionomers (preferably resist materials,
especially ultraviolet-nanoimprint lithography-resists (UV-NIL
resists)); modified with molecular layers (preferably self
assembling monolayers (SAMs), for direct
binding or indirect binding; self assembling
monolayers (SAMs) for indirect binding with one or
multiple chemicals or treatments to achieve the binding site. ORGNIC
CHEMISTRY - Preferred Components: The substrate comprises a self
assembling monolayers (SAMs) with two termini
such as one for attaching the molecule to the substrate such as a
thiol-headgroup for binding on gold (preferably self
assembling monolayers (SAMs) with a
silane-headgroup terminus for binding on siliconoxide); the second
terminus for coupling the ink, such as self assembling
monolayers (SAMs) with mercapto- or amino-groups for
binding metals, self assembling monolayers (
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SAMs) with carboxy-groups for electrostatic binding, self assembling monolayers (SAMs) with mercapto-groups for binding metals with plain alkyl chains having methylene groups for van der Waals interaction, with -COOH, -OH or vinyl-groups for covalent coupling, self assembling monolayers (SAMs) with antibodies for binding corresponding antigens, self assembling monolayers (SAMs) with antigens for binding corresponding antibodies, self assembling monolayers (SAMs) with receptors for specific binding of molecules. The patterned molecules are protein molecules having one or several lysine residues, and the substrate is gold, preferably having a spacer layer on its surface to avoid denaturation of the protein, the spacer layer preferably having a thickness of 0.5 - 200 nm, on a substrate.

L40 ANSWER 4 OF 14 WPIX COPYRIGHT 2009 THOMSON REUTERS on STN

ACCESSION NUMBER: 2006-162430 [17] WPIX DOC. NO. CPI: C2006-054284 [17] DOC. NO. NON-CPI: N2006-140133 [17]

TITLE: Photovoltaic cell comprises absorber; two substrates

comprising respective conductive surfaces; electron

transporter and hole transporter

DERWENT CLASS: A18; A28; A85; E13; E24; L03; U12; X15

ALIZADEH A; CELLA J A; DUGGAL A R; GUI J Y; SPIVACK J L; INVENTOR:

YAKIMOV A

PATENT ASSIGNEE: (ALIZ-I) ALIZADEH A; (CELL-I) CELLA J A; (DUGG-I) DUGGAL

A R; (GENE-C) GENERAL ELECTRIC CO; (GUIJ-I) GUI J Y;

(SPIV-I) SPIVACK J L; (YAKI-I) YAKIMOV A

COUNTRY COUNT:

## PATENT INFORMATION:

PAT	TENT NO	KINI	D DATE	WEEK	LA	PG	MAIN	IPC
US	20060021647	 A1	20060202	(200617)*	EN	 19[4]		
ΕP	1630883	A2	20060301	(200617)	EN			
JP	2006049890	Α	20060216	(200617)	JA	28		
CN	1734792	Α	20060215	(200639)	ZH			
CN	100539201	С	20090909	(200965)	ZH			

#### APPLICATION DETAILS:

PATENT NO	KIND	APPLICATION	DATE
US 20060021647 EP 1630883 A2 JP 2006049890 CN 1734792 A CN 100539201 C	A	US 2004-900624 EP 2005-254258 JP 2005-216748 CN 2005-100879 CN 2005-100879	20050707 20050727 71 20050728

PRIORITY APPLN. INFO: US 2004-900624 20040728

INT. PATENT CLASSIF.:

IPC ORIGINAL: H01G0009-20 [I,A]; H01G0009-20 [I,C]; H01L0021-00 [I,A]; H01L0021-00 [I,C]; H01L0031-00 [I,A]; H01L0031-00 [I,C]; H01L0031-04 [I,A]; H01L0031-04 [I,C]; H01L0051-00 [I,A]; H01L0051-00 [I,C]; H01L0051-42 [I,A]; H01L0051-42 [I,C]; H01M0014-00 [I,A]; H01M0014-00 [I,C]; H01G0009-20 [I,A]; H01G0009-20 [I,C]; H01L0031-04 [I,A]; H01L0031-04 [I,C]; H01M0014-00 [I,A]; H01M0014-00 [I,C]

ECLA: H01L0051-00T; H01L0051-42B; H01L0051-42F

ICO: L82T0201:01T; T01L0051:00M12B; T01L0051:00M6F;

T01L0051:00M6H; T01L0051:00M6H12B; Y01N0006:00

USCLASS NCLM: 136/252.000

NCLS: 136/256.000; 438/057.000

JAP. PATENT CLASSIF.:

MAIN/SEC.: H01L0031-04 D; H01M0014-00 P

MAIN: H01L0031-04 D SECONDARY: H01M0014-00 P

FTERM CLASSIF.: 5F051; 5H032; 5H032/AA06; 5F051/AA08; 5F051/AA09;

5F051/AA11; 5F051/AA20; 5H032/AS16; 5H032/BB05; 5H032/BB10; 5F051/CB11; 5H032/EE04; 5H032/EE16;

5H032/EE18; 5F051/FA12; 5H032/HH07

BASIC ABSTRACT:

US 20060021647 A1 UPAB: 20060310

NOVELTY - A photovoltaic cell comprises an absorber to absorb electromagnetic radiation; two substrates comprising respective conductive surfaces; an electron transporter in electrical communication with the second conductive surface and is electrically insulated from first substrate; and a hole transporter that is in electrical communication with the first conductive surface and electrically insulated from the second substrate.

DETAILED DESCRIPTION - A photovoltaic cell comprises an absorber that can absorb electromagnetic radiation; a first substrate comprising a first conductive surface; a second substrate comprising a second conductive surface that is opposed to the first conductive surface and faces the first conductive surface of the first substrate; an electron transporter that is in electrical communication with the second conductive surface of the second substrate, but is electrically insulated from the first substrate; and a hole transporter that is in electrical communication with the first conductive surface of the first substrate, but is electrically insulated from the second substrate. The hole transporter and/or the electron transporter are chemically bonded to an electrically insulating sheath; and to the absorber. INDEPENDENT CLAIMS are included for the following:

- (A) a photovoltaic cell comprising: a cylinder comprising a first intrinsically conducting polymer capable of transporting electrons to a second substrate; a matrix capable of conducting holes to a first substrate. The matrix is optically transparent and surrounds the cylinder, but is not in electrical communication with it; a sheathed layer disposed between the cylinder and the matrix and in intimate contact with the cylinder and the matrix. The sheathed layer comprises electrically insulating molecules and is at least 0.2 nanometer thick; an absorber chemically bonded to the first intrinsically conducting polymer and disposed between the cylinder and the matrix in a manner such that it is in electrical communication with the cylinder while being electrically insulated from the matrix. The absorber is capable of absorbing electromagnetic radiation of wavelengths of 300 1100 nanometers. The first and the second substrate are in electrical communication with one another;
- (B) a photovoltaic composition comprising: the electron transporter optionally bonded to an electrically insulating molecule; the hole transporter optionally bonded to the electrically insulating molecule; and the absorber;
  - (C) a device comprising the composition;
- (D) manufacturing a photovoltaic cell involving: blending a composition comprising an absorber that is capable of absorbing electromagnetic radiation; an electron transporter and/or a hole transporter; and/or an electrically insulating molecule; and depositing the composition upon a substrate.

USE - In photovoltaic cells as solar cells.

ADVANTAGE - The photovoltaic cells can provide an energy conversion efficiency of greater than or equal to10 (preferably greater than or equal to20, especially greater than or equal to30)% and are versatile and flexible, have a light weight and can be manufactured by flexible methods such as using roll mills.

The photovoltaic cells have reduced charge transport distances and minimize or prevent recombinations and backreactions, and can be easily mass produced. MANUAL CODE: CPI: A04-H00H; A05-K00K; A12-E06; A12-E11B; E05-H; E05-U;

E06-D13; E06-D15; E07-D13C; E07-E04; E08-H; E10-B01A4; E10-B04A2; E23-B; E25; E31-P06A; L04-E05D EPI: U12-A02A; X15-A02A

TECH

ELECTRONICS - Preferred Cell: The first substrate and/or the second substrate is transparent to light having a wavelength of 300 - 1100 nanometers. The conductive surface of the first substrate is in electrical communication with the conductive surface of the second substrate through an electrical circuit that is external to the photovoltaic cell. The conductive surfaces of the first and/or the second substrate comprise at least one layer of electrically conducting materials that can comprise metals, semiconductors, doped semiconductors and/or intrinsically conducting polymers. The electron transporter and hole transporter are in the form of interdigitated fingers that form an interpenetrating structure and are parallel to each other. The interdigitated fingers have a random configuration or have a characteristic dimension that is greater than or equal to 2 nanometers. The characteristic dimension is a layer thickness or a diameter and the interdigitated fingers and/or the insulating sheath have a cross-section that is substantially rectangular or circular. The electron transporter and the hole transporter are of a similar chemical composition and comprise intrinsically conductive polymers. The electron transporters are in the form of nano-structures. The nano-structures include nanowires, nano-rods, or nanosheets, and comprise metals, semiconductors and/or inherently conducting polymers. The electrically insulating sheath is bonded to the electron transporter and/or the hole transporter and prevents electrons from recombining with holes and the electrically insulating sheath has a characteristic dimension that is greater than or equal to0.2 nanometers. The electrically insulating sheath can comprise a partial monolayer or multiple layers of electrically insulating material. The electrically insulating material can comprise non-conductive inorganic compounds, non-conjugated monomers, polymeric molecules, oligomeric molecules and/or nanoparticles. The first conductive surface is a patterned electrically conductive surface. The second conductive surface is a patterned electrically conductive surface. The absorber is disposed between the electron transporter and the hole transporter and is capable of absorbing electromagnetic radiation. The patterning of the second/first substrate permits electrical communication with the electron transporter/the hole transporter respectively, while prohibiting electrical communication with the hole transporter/the electron transporter. The patterned electrically conductive surface comprise nanowires. The electron transporter and the hole transporter self assemble into structures that have a lamellar, cylindrical, bicontinuous or interpenetrating morphology. The photovoltaic cell further comprises the electrically insulating sheath that is disposed between the electron transporter and the hole transporter; and electrically insulating sheath minimizes electron transport from the electron transporter to the hole transporter. The absorber resides in an interface between the electron transporter and the hole transporter. In the composition, the electron transporter and/or the hole transporter comprises the intrinsically conducting polymer. The electrically insulating molecules comprise non-conductive inorganic oxides and/or non-conjugated organic molecules. The electron transporter is in the form of a nanowire that comprises an oxide of titanium. Preferred Method: The photovoltaic cell is manufactured by a process involving self assembly of the electron transporter and the hole transporter. The self assembly is accomplished by using templates, masks, electrical fields, magnetic

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fields, shear fields, and/or hydrophobic-hydrophilic interactions. The
patterned electrically conductive surface is chemically
bonded to the electron transporter or the hole transporter through a
self assembled monolayer or a polymer brush.
The patterned electrically conductive surface is
patterned by using e-beam lithography, nano-imprinting,
extreme UV lithography, and/or block copolymer
lithography. The blending involves solution blending and/or melt
blending. The method further involves reacting the absorbing molecule with
the electron transporter and/or the hole transporter, or reacting the
absorber and/or the electron transporter and/or the hole transporter with
the insulating molecule. The depositing the composition on a substrate
facilitates a self-assembly into cylinders that comprise the electron
transporters surrounded by a matrix that comprises the hole transporters.
The self-assembly promotes the electron transporters to be in electrical
communication with a conductive surface of one substrate, while the hole
transporters are in electrical communication with a conductive surface of
another substrate; promotes an absorber to be disposed on an outer surface
of the electron transporter and/or the hole transporter; or promotes a
sheathed layer to be disposed on an outer surface of the electron
transporter and/or the hole transporter.
ORGANIC CHEMISTRY - Preferred Components: The hole transporter and/or the
electron transporter comprise hydrazone compounds, styryl compounds,
diamine compounds, aromatic tertiary amine compounds, butadiene compounds,
indole compounds, carbazole derivatives, triazole derivatives, imidazole
derivatives, oxadiazole derivatives having an amino group,
triphenylmethane, bis(4-diethylamine-2-methylphenyl) phenylmethane,
stylbene, hydrozone; aromatic amines comprising tritolylamine; arylamine;
enamine phenanthrene diamine; N, N'-bis-(3, 4-dimethylphenyl)-4-
biphanyl amine; N, N'-bis-(4-methylphenyl)-N, N'-bis(4-ethylphenyl)-
1,1'-3,3'-dimethylbiphenyl)-4,4'-diamine;
4-4'-bis(diethylamino)-2,2'-dimethyltriphenylmethane;
N, N'-diphenyl-N, N'-bis(3-methylphenyl)-(1,1'-biphenyl
)-4,4'-diamine; N,N'-diphenyl-N,N'-bis(4-methylphenyl)-1,1'-
biphenyl-4,4'-diamine; N,N'-diphenyl-N,N'-bis(alkylphenyl)-1,1'-
biphenyl-4,4'-diamine; or N,N'-diphenyl-N,N'-bis(chlorophenyl)-
1,1'-biphenyl-4,4'-diamine;
1,1-bis(4-di-para-tolylaminophenyl)cyclohexane;
1,1-bis(4-di-p-tolylaminophenyl)-4-phenylcyclohexane;
4,4'-bis(diphenylamino)quadriphenyl;
bis (4-dimethylamino-2-methylphenyl)-phenylmethane;
N, N, N-Tri(para-tolyl) amine; 4-(di-para-tolylamino)-4'-(4(di-para-
tolylamino)-styryl) stilbene; N,N,N',N'-tetra-para-tolyl-4-4'-
diaminobiphenyl; N,N,N',N'-tetraphenyl-4,4'-diaminobiphenyl;
N, N, N', N'-tetra-1-naphthyl-4, - 4'-diaminobiphenyl;
N, N, N', N'-tetra-2-naphthyl-4, 4'-diaminobiphenyl;
N-phenylcarbazole; 4,4'-bis(N-(1-naphthyl)-N-phenylamino)
biphenyl; 4,4'-bis(N-(1-naphthyl)-N-(2-naphthyl
)amino)biphenyl; 4,4'-bis(N-(1-naphthyl
)-N-phenylamino)para-texphenyl; 4,4'-bis(N-(2-maphthyl
)-N-phenylamino)biphenyl;
4,4'-bis(N-(3-acenaphthenyl)-N-phenylamino)biphenyl;
1,5-bis(N-(1-naphthyl)-N-phenylamino)naphthalene;
4,4'-bis(N-(9-anthryl)-N-phenylamino)biphenyl;
4,4'-bis(N-(1-anthryl)-N-phenylamino)-para-terphenyl;
4,4'-bis(N-(2-phenanthryl)-N-phenylamino)biphenyl;
4,4'-bis(N-(8-fluoranthenyl)-N-phenylamino)biphenyl;
4,4'-bis(N-(2-pyrenyl)-N-phenylamino)biphenyl;
4,4'-bis(N-(2-naphthacenyl)-N-phenylamino)biphenyl;
4,4'-bis(N-(2-perylenyl)-N-phenylamino)biphenyl;
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4,4'-bis(N-(1-coronenyl)-N-phenylamino)biphenyl;
2,6-bis(di-para-tolylamino)-naphthalene; 2,6-bis(di-(1-naphthyl
)amino)naphthalene; 2,6-bis(N-(1-naphthyl)-N-(2-naphthyl
)amino)naphthalene; N,N,N',N'-tetra(2-naphthyl
)-4,4'-diamino-para-temphenyl; 4,4'-bis (N-phenyl
-N-(4-(1-naphthyl)-phenyl)amino) biphenyl;
4,4'-bis(N-phenyl-N-(2-pyrenyl)amino)biphenyl;
2,6-bis(N,N-di(2-naphthyl)- amine)fluorine; and/or 1,5-bis(N-(1-
naphthyl)-N-phenylamino)naphthalene. The electron transporters are
functionalized fullerenes, 6,6-phenyl-61C-butyl
acid-methylester, difluorovinyl-(hetero)arylenes,
3-(1,1-difluoro-alkyl)thiophene group, pentacene, poly(3-hexylthiophene),
alpha, omega-substituted sexithiophenes,
n-decapentafluoroheptyl-methylnaphthalene-1,4,5,8-tetracarboxylic diimide,
dihexyl-quinquethiophene, poly(3-hexylthiophene), poly(3-alkylthiophene),
di-hexyl-hexathiophene, dihexyl-anthradithiophene-, phthalocyanine and/or
60C fullerene. The absorber comprises an absorbing molecule and a charge
separator that is chemically bonded to the absorbing molecule. The
absorbing molecule comprises at least one long wavelength absorbing
molecule and at least one short wavelength absorbing molecule capable of
absorbing electromagnetic radiation of wavelengths of 700 - 1100 and 300 -
700 nanometers respectively. The short wavelength absorbing molecule and
the long wavelength absorbing molecule are chemically compatible with one
another and can reside in a single phase. The charge separator is a
substituted phenothiazine moiety, a substituted carbazole moiety, and/or a
substituted dibenzochalcophene moiety and comprises an electron donating
moiety and/or a reducing agent. The absorber displays a push-pull
capability and the push-pull capability enables an ejected electron to
move towards the electron transporter rather than towards the hole
transporter. The absorber has a lowest unoccupied molecular orbital (LUMO)
level to eject an electron directly into the conduction band of the
electron transporter, and a highest occupied molecular orbital (HOMO)
level effective to eject a hole directly into the hole conduction band of
the hole transporter. The matrix is a liquid electrolyte, ionic liquid,
inorganic or organic hole conducting compound. The ionic liquid is
methylpropylimidazolium triflate, methylpropylimidazolium bistriflimide;
methylpropylimidazolium nanoflate, methylpropylimidazolium ethersulfonate,
methylpropylimidazolium iodide, methylpropylimidazolium triiodide,
methylpropylimidazolium pseudo-halides and/or metal complex cations with a
phosphonium anion. In the composition, the absorbing molecules are dyes
and/or pigments. The dyes and/or pigments are anthranones; anthraquinones;
croconines; azos; benzimidazolones; diketo pyrrole pyrroles; dioxazines;
diarylides; indanthrones; isoindolines; isoindolinones; naphtols;
perinones; perylenes; ansanthrones; dibenzpyrenequinones; pyranthrones;
bioranthorones; isobioranthorone or their respective derivatives;
diphenylmethane and triphenylmethane pigments; cyanine and azomethine
pigments; indigoid pigments; bisbenzoimidazole pigments; azulenium salts;
pyrylium salts; thiapyrylium salts; benzopyrylium salts; phthalocyanines,
pryanthrones or their derivatives; quinacidones; quinophthalones;
squaraines and/or squarilyiums or their respective derivatives. The azos
and their derivatives comprise monoazos, disazos, trisazos or their
derivatives. The azos comprise azo pigments having a triphenylamine
structure, a carbazole structure, a fluorene structure, an oxadiazole
structure, a bisstilbene structure, a dibenzothiophene structure, a
distyrylbenzene structure, a distyrylcarbazole structure,
distyryloxadiazole structure, an anthraquinone structure or a stilbene
structure; trisazo pigments having a carbazole structure; and/or bisazo
pigments having a diphenylpolyene structure. The electron transporter/the
hole transporter comprises reactive groups that only permit chemical
bonding with the second substrate/the first substrate respectively.
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POLYMERS - Preferred Components: The intrinsically conducting polymers are poly(acetylene) and its derivatives; poly(thiophenes) and its derivatives; poly(3,4-ethylenedioxythiophene) and poly(3,4-ethylenedithiathiophene) and their derivatives; poly(isathianaphthene), poly(pyridothiophene), poly(pyrizinothiophene), and their derivatives; poly(pyrrole) and its derivatives; poly(3,4-ethylenedioxypyrrole) and its derivatives; poly(aniline) and its derivatives; poly(phenylenevinylene) and its derivatives; poly(p-phenylene) and its derivatives; poly(thionapthene), poly(benzofuran), and poly(indole) and their derivatives; poly(dibenzothiophene), poly(dibenzofuran), poly(carbazole) and their derivatives; poly(bithiophene), poly(bifuran), poly(bipyrrole), and their derivatives; poly(thienothiophene), poly(thienofuran), poly(thienopyrrole), poly(furanylpyrrole), poly(furanylfuran), poly(pyrolylpyrrole), and their derivatives; poly(terthiophene), poly(terfuran), poly(terpyrrole), and their derivatives; poly(dithienothiophene), poly(difuranylthiophene), poly(dipyrrolylthiophene), poly(dithienofuran), poly(dipyrrolylfuran), poly(dipyrroly)pyrrole) and their derivatives; poly(phenyl acetylene) and its derivatives; poly(biindole) and derivatives; poly(dithienovinylene), poly(difuranylvinylene), poly(dipyrrolylvinylene) and their derivatives; poly(1,2-trans(3,4-ethylenedioxythienyl)vinylene), poly(1,2-trans(3,4-ethylenedioxyfuranyl)vinylene), poly(1,2-trans(3,4-ethylenedioxypyrrolyl)vinylene), and their derivatives; poly(bis-thienylarylenes) and poly(bis-pyrrolylarylenes) and their derivatives; poly(dithienylcyclopentenone); poly(quinoline); poly(thiazole); poly(fluorene); and/or poly(azulene). The oligomeric molecules or polymeric molecules are polyacetals, polyurethanes, polyolefins, polyacrylics, polycarbonates, polyalkyds, polystyrenes, polyesters, polyamides, polyaramides, polyamideimides, polyarylates, polyarylsulfones, polyethersulfones, polyphenylene sulfides, polysulfones, polyimides, polyetherimides, polytetrafluoroethylenes, polyetherketones, polyether etherketones, polyether ketone ketones, polybenzoxazoles, polyoxadiazoles, polybenzothiazinophenothiazines, polybenzothiazoles, polypyrazinoquinoxalines, polypyromellitimides, polyquinoxalines, polybenzimidazoles, polyoxindoles, polyoxoisoindolines, polydioxoisoindolines, polytriazines, polypyridazines, polypiperazines, polypyridines, polypiperidines, polytriazoles, polypyrazoles, polycarboranes, polyoxabicyclononanes, polydibenzofurans, polyphthalides, polyacetals, polyanhydrides, polyvinyl ethers, polyvinyl thioethers, polyvinyl alcohols, polyvinyl ketones, polyvinyl halides, polyvinyl nitriles, polyvinyl esters, polysulfonates, polysulfides, polythioesters, polysulfones, polysulfonamides, polyureas, polyphosphazenes, and/or polysilazanes. The electron transporter, the hole transporter or the absorber are present in the form of a block copolymer. The matrix comprises a second intrinsically conducting polymer that is not chemically similar to the first intrinsically conducting polymer, which that is used as the electron transporter.

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L40 ANSWER 5 OF 14 WPIX COPYRIGHT 2009
                                              THOMSON REUTERS on STN
ACCESSION NUMBER:
                    2005-758275 [77]
                                       WPIX
DOC. NO. CPI:
                     C2005-231332 [77]
DOC. NO. NON-CPI:
                   N2005-625761 [77]
TITLE:
                     Stabilized system as resists for nanofabrication,
                     includes stabilizing solution of solvent and stabilizing
                     component that contains molecules with solvent-philic and
                     surface layer-philic portions
DERWENT CLASS:
                     A85; L03; P73; U11
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INVENTOR:

A85; L03; P73; U11

AMRO N A; LIU G; YANG G

PATENT ASSIGNEE: (AMRO-I) AMRO N A; (LIUG-I) LIU G; (REGC-C) UNIV

CALIFORNIA; (UYWA-N) UNIV WAYNE STATE; (YANG-I) YANG G

COUNTRY COUNT: 107

#### PATENT INFORMATION:

PAI	ENT NO	KINI	D DATE	WEEK	LA	PG	MAIN IPC
WO	2005089415	A2	20050929	(200577)*	EN	74[13]	
US	20050221081	A1	20051006	(200577)	ΕN		
WO	2005089415	А3	20090423	(200929)	ΕN		

#### APPLICATION DETAILS:

BASIC ABSTRACT:

PATENT NO	KIND	APPLICATION	DATE
WO 2005089415 A US 20050221081 US 20050221081 WO 2005089415 A	Al Provisional Al		2 20040323 20050317
PRIORITY APPLN. INFO:	US 2004-555770P	20040323	
	US 2005-83739	20050317	
	US 2004-555770P	20040323	
INT. PATENT CLASSIF.:			
IPC ORIGINAL:	B05D0001-00 [I,A]; B	05D0001-00 [I,C]	; B05D0001-18 [N,A];
	B05D0001-18 [N,C]; B	05D0001-36 [N,A]	; B05D0001-36 [N,C];
	B32B0015-04 [I,A]; B		
IPC RECLASSIF.:	B05D0001-18 [I,A]; B	05D0001-18 [I,C]	: B05D0003-10 [N.A]:
	B05D0003-10 [N,C]; B		
	G01N0033-543 [I,A];	- , -	
ECLA:	B05D0001-18C; G01N00	- ,	01
ICO:	L05D0001:18C; L05D00		.01. V01N0006.00
	428/338.000	00.100, 10210201	.01, 101110000.00
		000	
NCLS:	428/420.000; 428/457	.000	

WO 2005089415 A2 UPAB: 20090509

NOVELTY - Stabilized system comprises a solid support, a surface-layer bonded to a portion of a surface of the solid support, and a stabilizing solution contacted with a portion of the surface-layer. The stabilizing solution comprises a solvent and a stabilizing component, which contains molecules having a solvent-philic portion and a surface layer-philic portion.

DETAILED DESCRIPTION - INDEPENDENT CLAIMS are also included for:

- (1) stabilized surface-layer comprising self-assembled monolayer and stabilizing solution contacting a portion of the self-assembled monolayer;
- (2) kit for use in stabilizing a system comprising the stabilizing solution and instructions for contacting the stabilizing solution with a surface-layer bonded to a solid support surface; and
- (3) method for stabilizing the surface-layer bonded to a surface portion of the solid support comprising contacting the surface-layer with a fluid having the stabilizing component containing molecules that associate preferentially with defect sites in the surface-layer.

Each molecule of the self-assembled monolayer contains 1-30C alkyl linker, a head group bonded to a surface portion of a solid support and terminal group(s). The stabilizing solution comprises water and a stabilizing component containing amphiphilic molecules.

USE - For use as resists for nanofabrication.

ADVANTAGE - The inventive system is capable of preventing the degradation of the surface-layer bonded to the solid support. The protected layer formed at defects sites lowers the free energy of adsorbed surface layers and increases the activation energy to inhibit degradation pathways.

MANUAL CODE: CPI: A12-E01; L04-C05

EPI: U11-A06

TECH

BIOTECHNOLOGY - Preferred Component: The pre-engineered surface layer includes biomolecule(s) of antibodies, oligonucleotides, DNA, RNA, oligopeptides, peptides, and/or proteins. CERAMICS AND GLASS - Preferred Component: The metal thin film of the solid support can be mica surface, glass surface, or quartz surface. ELECTRONICS - Preferred Component: The surface portion of the solid support can be semiconductor surface, or insulator surface. A portion of the surface-layer is a monolayer, a multilayer, or a thin film. The monolayer is a self-assembled monolayer. The surface of the solid support is immersed in the stabilizing solution. The stabilizing component contains molecules that associate preferentially with defect sites in the surface-layer. The defect sites are domain boundaries, holes, pits, cracks, dislocations, island edges, and/or step edges. The solid support comprises a pre-engineered surface layer having microstructures, and/or nanostructures surrounded by a selfassembled monolayer, multilayer, or thin film . The microstructures are prepared by microcontact printing, photolithography, micromachining, and/or soft lithography. The nanostructures are prepared by nanografting, scanning probe lithography, mixing of multicomponents, e-beam lithography, and/or atom lithography.

INORGANIC CHEMISTRY - Preferred Material: The surface portion of the solid support is a metal surface, metal thin film, or preferably gold, silver, platinum, palladium or copper surface. The solid support comprises a metal (preferably gold) thin film on a silicon wafer surface. The solvent is water.

ORGANIC CHEMISTRY - Preferred Material: The surface portion of the solid support is a metal surface, metal thin film, or preferably gold, silver, platinum, palladium or copper surface. The solid support comprises a metal (preferably gold) thin film on a silicon wafer surface. The solvent is water.

ORGANIC CHEMISTRY - Preferred Component: A portion of the surface-layer is a self-assembled monolayer made of

molecules, each contains surface-adhesive head group, a linker group and/or terminal group(s). It is a self-assembled

monolayer made of alkyl containing molecules. Surface adhesive head group(s) is a thiol. The linker group contains an alkyl group, polyethylene glycol, and/or an amide group. The terminal group(s) is -CH3, -CF3, -OH, -CHO, -COOH, -NH2, -NHR1, -NR12, -NR1R2, -OCH2CH3-, -SH, -biotin, -phenyl, an-RGD (Arg-Gly-Asp peptide), or

a-carbohydrate. The alkyl containing molecules contain a 1-30C alkyl. They are bonded to the solid support surface via a thiol moiety. The solvent can be an aqueous solvent, an organic solvent, a protic solvent, an aprotic solvent, and/or preferably an aqueous buffer. The stabilizing component contains amphiphilic molecules. It contains molecules of formula ABn. The stabilizing component contains N,N-dimethylformamide, dimethyl sulfoxide, N,N-dimethylacetamide, and/or N-methylformamide.

R1, R2 = alkyl or axyl;

A = solvent-philic moiety of amide, -OH, ether, ester, amine, sulfoxide, or preferably formamide, sulfoxide, or acetamide; B = surface-philic moiety, preferably alkyl or axyl; n = 1-3.

Preferred Composition: The solvent comprises minor components of non-reactive additives with a concentration of less than 15% mole fraction. The concentration of the stabilizing component in the stabilizing solution is less than or equal to 45 (preferably 0.01-15) vol.%.

POLYMERS - Preferred Component: The metal thin film of the solid support

can be a plastic surface, a polymeric surface or a waveguide.

ABEX EXAMPLE - Gold (Au) (99.99%) was deposited in a high-vacuum evaporator at  $2 \times 10-7$  Torr onto mica substrates (clear ruby muscovite mica). The mica was freshly cleaved immediately before being mounted on the substrate holder inside the vacuum chamber. The evaporation rate was 3 Angstrom /s, and the mica substrate was maintained at 625degreesK during Au deposition. After evaporation, films were annealed at 625degreesK for 20 minutes to yield relatively large Au(111) terraces, 100-200 nm in lateral dimension. Alkanethiol self-assembled monolayers (

SAMs) were formed by soaking gold thin films (immediately after vacuum deposition or peeling) in 1 mM ethanolic solutions of alkanethiol. Each gold substrate remained in a thiol solution for 2-7 days at room temperature to ensure the formation of mature monolayers with high coverage and a low density of defects. The preformed SAMs were rinsed with ethanol and dried in air for less than 5 minutes prior to soaking in solvents.

L40 ANSWER 6 OF 14 WPIX COPYRIGHT 2009 THOMSON REUTERS on STN

ACCESSION NUMBER: 2005-664931 [68] WPIX DOC. NO. NON-CPI: N2005-544598 [68]

TITLE: Surface-modified layer system

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production method involves treating polymorphic

self-assembled monolayer

anchored on substrate, thermally, to change structural

form of SAM

DERWENT CLASS: P42

INVENTOR: BUCK M; CYGANIK P

PATENT ASSIGNEE: (UYSA-N) UNIV ST ANDREWS; (BUCK-I) BUCK M; (CYGA-I)

CYGANIK P

COUNTRY COUNT: 107

## PATENT INFORMATION:

PAT	TENT NO	KINI	DATE	WEEK	LA	PG	MAIN	IPC	
WO	2005092516	A1	20051006	(200568)*	EN	 24[7]			
GB	2426724	Α	20061206	(200680)	EN				
US	20070140901	A1	20070621	(200741)	EN				
GB	2426724	В	20080903	(200858)	EN				

# APPLICATION DETAILS:

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PATENT NO KIND	APPLICATION DATE
WO 2005092516 A1	WO 2005-GB1159 20050324
GB 2426724 A	GB 2006-18673 20060922
US 20070140901 A1	US 2006-594654 20060926
GB 2426724 A PCT Application	WO 2005-GB1159 20050324
US 20070140901 A1 PCT Application	WO 2005-GB1159 20050324
GB 2426724 B PCT Application	WO 2005-GB1159 20050324
GB 2426724 B	GB 2006-18673 20060922

# FILING DETAILS:

PATENT NO	KIND		PA:	TENT NO	
GB 2426724	A	Based on	WO	2005092516	Α
GB 2426724	В	Based on	WO	2005092516	Α

PRIORITY APPLN. INFO: GB 2004-6841 20040326

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INT. PATENT CLASSIF.:
   IPC ORIGINAL:
                     B05D0001-18 [I,A]; B05D0001-18 [I,C]; B05D0003-02 [I,A];
                     B05D0003-02 [I,C]; B05D0003-06 [I,A]; B05D0003-06 [I,C];
                      G01N0031-22 [I,A]; G01N0031-22 [I,C]
 IPC RECLASSIF.:
                      B05D0001-18 [I,A]; B05D0001-18 [I,C]; B05D0003-02 [I,A];
                     B05D0003-02 [I,C]; B05D0005-00 [N,A]; B05D0005-00 [N,C]
ECLA:
                     B05D0007-24
ICO:
                     L05D0001:18C; L05D0003:02S; L05D0005:00; L05D0202:40;
                     L82T0201:01S; L82T0201:01T; Y01N0006:00
USCLASS NCLM:
                      422/057.000
BASIC ABSTRACT:
           WO 2005092516 A1
                             UPAB: 20051223
            NOVELTY - The method involves treating polymorphic self- assembled
     monolayer (SAM) (1) anchored on substrate (2), thermally, to change the
     structural form of the SAM.
            DETAILED DESCRIPTION - An INDEPENDENT CLAIM is also included for
     surface-modified layer system.
            USE - For producing surface-modified layer system (claimed), using
     thermo-lithographic technique.
            ADVANTAGE - Effectively increases structural perfection of thermally-
     treated SAM with significantly increased domain size and resistance to
     structural disruption by surface discontinuities in the substrate surface.
            DESCRIPTION OF DRAWINGS - The figure shows a schematic view explaining
     the SAM patterning process.
              SAM (1)
            substrate (2)
            pattern (3)
            laser radiation (4)
TECH
     INORGANIC CHEMISTRY - The substrate is made of indium phosphide, gallium
     arsenide, and alloys and oxides, including glass.
     METALLURGY - The substrate is made of material selected from a group
     consisting of gold, silver, chromium, manganese, vanadium, tungsten,
     molybdenum, zirconium, titanium, platinum, aluminum, iron and steel.
     ORGANIC CHEMISTRY - The substrate is made of indium phosphide, gallium
     arsenide, and alloys and oxides, including glass.
     ORGANIC CHEMISTRY - The SAM which is 4-(4'-methyl-
     biphenyl-4-yl)-alkane-1-thiol, comprises anchor moiety and
     optionally substituted aryl e.g. hetero-aryl
     moiety. The anchor moiety is selected from thio, seleno, carboxyl,
     phosphonate, phosphate and hydroxyl. The aryl moiety is selected
     from phenyl, biphenyl and terphenyl, and
     fused ring systems selected from anthracryl and naphthyl, and
     hetero-arvl selected from bipyridvl,
     terpyridyl, thiophenyl, bithienyl,
     terthienyl and pyrrolyl and alicyclic moieties
     selected from bridged alievelic systems such as bi-, tri- or
     tetracycloalkanes. The xyl moiety has substituent selected from
     halogen, carboxy, trifluoromethyl, thiol, hydroxy, cyano, amino, nitro, C1
     to C6 alkyl and carbonyl.
L40 ANSWER 7 OF 14 WPIX COPYRIGHT 2009
                                               THOMSON REUTERS on STN
ACCESSION NUMBER:
                     2004-447945 [42]
                                        WPIX
DOC. NO. CPI:
                     C2004-168125 [42]
DOC. NO. NON-CPI:
                    N2004-354276 [42]
TITLE:
                     Patterning object surface in
                     microcontact printing involves forming one self
                      -assembled monolayer on the object
                      and the other monolayer of a complementary pattern on
                      uncovered regions followed by etching
```

DERWENT CLASS: L03; U11

INVENTOR: DELAMARCHE E; GEISSLER M; WOLF H PATENT ASSIGNEE: (IBMC-C) INT BUSINESS MACHINES CORP

COUNTRY COUNT:

PATENT INFORMATION:

PATENT NO KIND DATE WEEK LA PG MAIN IPC

US 20040102050 A1 20040527 (200442)\* EN 10[6]

US 6893966 B2 20050517 (200533) EN

APPLICATION DETAILS:

PATENT NO KIND APPLICATION DATE \_\_\_\_\_\_ US 20040102050 A1 US 2002-307069 20021127

PRIORITY APPLN. INFO: US 2002-307069 20021127

INT. PATENT CLASSIF.:

IPC RECLASSIF.:

B81C0001-00 [I,A]; B81C0001-00 [I,C]; G03F0007-00 [I,A];

G03F0007-00 [I,C]

B81C0001-00F2F; G03F0007-00A

L81C0201:03S; L82T0201:01; Y01N0004:00; Y01N0006:00

JSCLASS NCLM:

NCLS:

438/689.000

ECLA:

ICO:

USCLASS NCLM: NCLS:

BASIC ABSTRACT:

US 20040102050 A1 UPAB: 20060121

NOVELTY - Patterning the surface of an object involves forming first self-assembled monolayer (a) of first material (m1) on a layer (L1) of a surface of an object according to a desired pattern; forming a second selfassembled monolayer (b) of a second material (m2) on uncovered region of layer (L1) in a configuration that is complementary to the desired pattern and etching layer (L1) through monolayer (a).

DETAILED DESCRIPTION - Patterning the surface of an object involves forming a first self-assembled monolayer (a) of a first material (m1) on a layer (L1) of a surface of an object according to a desired pattern; forming a second self-assembled monolayer (b) of a second material (m2) on uncovered region of layer (L1) in a configuration that is complementary to the desired pattern; and etching layer (L1) through monolayer (a). Material (m1) Is capable of binding to layer (L1), prevents the formation of monolayer (b) on monolayer (a) and substantially does not block the etching of an underlying region of layer (L1).

USE - In patterning the surface of an object e.g. in microcontact printing (claimed).

ADVANTAGE - The method provides a printing process of the positive type where the structures formed on the stamps have better mechanical stability; allows to fabricate more stable patterns on the stamps without requiring the use of a reactive ion etcher, thus reducing cost and process complexity; forms high resolution lines on a substrate that are produced using high-resolution grooves on the stamps allowing easier unmolding; and allows fast printing operation on an object for higher manufacturing throughput.

MANUAL CODE: CPI: L04-C07

EPI: U11-C04A1B; U11-C04A1C; U11-C04D; U11-C07D1

TECH

IMAGING AND COMMUNICATION - Preferred Process: Formation of monolayer (a) involves depositing material (m1) using a negative microcontact printing utilizing a stamp surface (preferably in hydrophylized state) containing an elastomer body provided with an inking layer of material (m1), a writing technique to localize the formation of monolayer (a), or

depositing material (m1) from a solution on the substrate and forming monolayer (a) by removing material (m1) from a desired area using one of electron-beam lithography, photolithography, mechanical indentation, atomic force microscope lithography or scanning tunneling microscope lithography.

ORGANIC CHEMISTRY - Preferred Process: Formation of monolayer (b) involves depositing material (m2) from a solution. The method further involves selecting material (m1) containing at least 2 thiol groups (preferably alkyl chains attached to either thiol having less than 7 consecutive carbon atoms, especially pentaerythritoltetrakis (3-mercaptopropionate) molecules) or cysteamine hydrochloride. The method further involves selecting material (m2) containing a thiol having at least 7 consecutive carbon atoms (preferably eicosanethiol). Etching of layer (L1) containing gold is performed in a solution of cyanide containing oxygen and having a ps of approximately 12, and etching of layer (L1) containing copper is performed in a solution of peroxodisulfate.

L40 ANSWER 8 OF 14 WPIX COPYRIGHT 2009 THOMSON REUTERS on STN

ACCESSION NUMBER: 2004-430162 [40] WPIX CROSS REFERENCE: 2004-095982; 2005-028796

TITLE: Formation of self-aligned pattern on existing pattern on

substrate by applying a coating of masking material to top surface of substrate, and allowing portion of masking

US 2003-421355 20030424

material to attach to portions of existing

pattern to top surface

A85; E19; L03; U11 DERWENT CLASS:

COLBURN M E; GATES S M; HEDRICK J C; HUANG E; NITTA S V; INVENTOR:

PURUSHOTHAMAN S; SANKARAPANDIAN M
PATENT ASSIGNEE: (IBMC-C) INT BUSINESS MACHINES CORP
COUNTRY COUNT: 1

PATENT INFORMATION:

PATENT NO KIND DATE WEEK LA PG MAIN IPC \_\_\_\_\_\_

US 20040087177 A1 20040506 (200440)\* EN 20[8]

APPLICATION DETAILS:

FILING DETAILS:

KIND PATENT NO APPLICATION DATE \_\_\_\_\_\_ US 20040087177 A1 Div Ex US 2002-287935 20021105

US 20040087177 A1

PATENT NO KIND PATENT NO

US 20040087177 A1 Div ex US 6641899 B

PRIORITY APPLN. INFO: US 2002-287935 20021105 US 2003-421355 20030424

INT. PATENT CLASSIF.:

IPC RECLASSIF.: G03F0007-16 [I,A]; G03F0007-16 [I,C]

G03F0007-16L ECLA: 438/758.000 USCLASS NCLM:

NCLS: 428/195.100; 438/778.000; 438/780.000

BASIC ABSTRACT:

US 20040087177 A1 UPAB: 20090327

NOVELTY - A self-aligned pattern on an existing pattern on a substrate having a top surface is formed by applying a coating of the masking material to the top surface of the substrate; and allowing a portion of the masking material to preferentially attach to portions of the existing pattern to the top surface.

DETAILED DESCRIPTION - INDEPENDENT CLAIMS are also included for:

- (a) a structure comprising a self aligned pattern on an existing pattern on a substrate; and
- (b) a composition for selectively coating a pattern on a substrate, comprising a carrier material for application to the substrate; and a polymer in the carrier that reactively grafts to regions of the substrate having first chemical characteristics.

The self-aligned pattern includes a masking material having an affinity for portions of the existing pattern, so that the masking material preferentially reactively grafts to the portions of the existing pattern.

 $\ensuremath{\mathsf{USE}}$  - For forming a self-aligned pattern on an existing pattern on a substrate.

ADVANTAGE - The self-aligned pattern is fabricated accurately and inexpensively without the use of lithography. The use of self-aligned masks allows a simplified fabrication process in which the effective dielectric constant between metal lines can be reduced through selective application of various materials to the metal lines. This is central to maximizing the propagation speed of interconnect signals and ultimately provides faster overall circuit performance. Further, the inventive method leads to a higher level of protection and reliability of interconnect structures as the errors attributed to conventional patterning methods are eliminated and to reduced processing costs. The use of the self-aligned masks allows a unique process in which the masks can be generated without the need to perform additional pattern defining steps.

 ${\tt DESCRIPTION}$  OF  ${\tt DRAWINGS}$  — The figure is a cross sectional view of a semiconductor device.

Interconnect structure (30)
Interlayer dielectric (31)

Metal wiring (32)

Liner barrier layer (34)

Cap barrier layer (36)

MANUAL CODE:

CPI: A11-B05; A12-E07C; E05-A; E05-E; E10-A01; E10-A03B; E10-A04B1B; E10-A04B1D; E10-A04B2B; E10-A04B2D; E10-A09B4; E10-A09B8; E10-A16B; E10-A23B; E10-E04; E10-F02; E10-F02A2; E10-G01; E10-H04; E31-P06B; E31-P06E;

E35-A; L04-C06; L04-C10A

EPI: U11-C04B; U11-C05D3

TECH

ELECTRONICS - Preferred Component: The pattern applied to the top surface comprises a first set of regions of the substrate having a first atomic composition, and a second set of regions of the substrate having a second atomic composition different from the first composition. The masking material comprises a self-assembled monolayer

that selectively binds to the second set of regions of the pattern. The first set of regions includes one or more metal elements. The second set of regions includes a dielectric. The areas of second atomic composition are patterned electrical interconnects. The substrate is a silicon wafer containing microelectronic devices, a ceramic chip carrier, an organic chip carrier, a glass substrate, a gallium arsenide substrate, a silicon carbide substrate, a semiconductor wafer, a circuit board, or a plastic substrate. The masking material also includes a reactive molecule having functional groups for polymerization propagation; a composition where polymerization proceeds by reactions that combine monomers and polymers having two or more functionalities that react with each other to produce polymers of a larger molecular weight; or the reactive molecule, where

reaction of the reactive molecule with the portion of the pattern generates a layer having reactive groups, which participate in step growth polymerization. The structure further comprises conductive feature(s) formed on the substrate; and conductive barrier layer(s). The substrate further comprises insulating layer(s) surrounding the conductive feature. The conductive barrier layer is disposed at interface(s) between the insulating layer and the conductive feature. The insulating layer surrounds the conductive feature at its bottom and lateral surfaces. Preferred Method: The method further comprises applying a reactive monomer to the layer of functional groups so that the reactive monomer polymerizes on the layer, applying the reactive monomer which undergoes polymerization on the layer, or applying the reactive monomer having one or more functionalities to the layer a form a self-aligned mask layer; preparing a polymer to act as the masking material; forming a condensed phase containing the polymer or the reactive molecule, and contacting the portions of the pattern with the condensed phase; preparing the reactive molecule or the reactive monomer; removing the masking material from the portions of the pattern to which it does not attach; and chemically treating regions of the substrate prior to applying the coating. The polymerization comprises a chain growth mechanism wherein polymerization proceeds through addition of a monomer to a reactive polymer. The removing step is accomplished through rinsing, ultrasonication, dissolution, thermolysis, irradiation, or annealing. The masking material is applied to the substrate by a spin coating, scan coating, dip coating or spray coating, or using a doctor blade. The chemically treating step includes plasma treatment, application of an oxidizing or reducing solution, annealing in a reducing or oxidizing atmosphere, or application of a material that renders surface portions of the substrate, to which it is applied, to be hydrophobic or hydrophilic; and applying an organosilane comprising SixLyRz. It changes the wetting characteristics of the regions of the substrate. The reactive monomer polymerizes when exposed to a free radical, an anion, a cation, and a transition metal catalyst; or polymerizes when exposed to thermal annealing or irradiation. The reactive molecule or reactive monomer is prepared in a vapor phase. The irradiating step includes exposure to ultraviolet light, visible light, x-rays, or electrons. L = hydroxy, methoxy, ethoxy, acetoxy, alkoxy, carboxy, amines, or halogens; and R = hydrido, Me, Et, vinyl, or Ph (any alkyl or aryl).

POLYMERS - Preferred Material: The masking material comprises a polymer containing a reactive grafting site that selectively binds to the second set of regions of the pattern applied to the top surface; or a polymer that is generated from the reactive molecule that binds to the portions of the pattern to provide a molecular monolayer of functional groups. Preferred Component: The coating comprises a polymer that covalently bonds to the portions of the pattern. The polymer is poly(oxides), poly-(carbonates), poly(esters), poly(anhydrides), poly(urethanes), poly(sulfonates), poly(siloxanes), poly(sulfides), poly(thioethers), poly(thioesters), poly(sulfones), poly(sulfonamides), poly(amides), poly(imines), poly(ureas), poly-(phosphazene), poly(silanes), poly(siloxanes), poly(silazane), poly(nitriles), poly(imides), poly(oxazole), poly(benzoxazole), poly(thiazoles), poly(pyrazoles), poly-(triazoles), poly(thiophenes), poly(oxadiazole), poly(thiazine), poly(thiazoles), poly(quinoxaline), poly(benzimidazoles), poly(oxindoles), poly(indolines), poly(pyridines), poly(triazines), poly(piperazine), poly(pyridines), poly(piperidines), poly(pyrrolidines), poly(carborane), poly(fluoresceins), poly(acetals), or poly(anhydrides). The polymer is an amorphous polymeric system having any chain architecture; a main chain acyclic hetero-atom polymer; a main chain heterocyclic polymer; or one of linear, networked, branched, and dendrimeric. It has an acyclic main

chain, a carbon containing backbone, and a reactive functional group serving as the grafting site.

ORGANIC CHEMISTRY - Preferred Component: The functional group is acyl chlorides, anhydrides, hydroxy, esters, ethers, aldehydes, ketones, carbonates, acids, epoxies, aziridines, phenols, amines, amides, imides, isocyanates, thiols, sulfones, halides, phosphines, phosphine oxides, nitros, azo, benzophenones, acetals, ketals, diketones, or the organosilanes. The reactive monomer comprises a monomeric ring. It is dienes, alkene, acrylics, methacrylic, acrylamides, methacrylamides, vinylethers, vinyl alcohols, ketones, acetals, vinylesters, vinylhalide, vinylnitrile, styrene, vinyl pyridine, vinyl pyrrolidone, vinyl imidazoles, vinyl heterocyclics, cyclic lactam, cyclic ether, cyclic lactones, cycloalkene, cyclic thioester, cyclic thioether, aziridines, phosphozine, siloxane, oxazoline, oxazine, thiirane, caprolactone, propylene glycol, or a substituted ethylenic organic molecule. The reactive molecule is bi-functional. It includes a first moiety that binds to the portions of the pattern; and a second moiety that serves as a polymerization initiator, a monomeric unit, or a reaction site. It is deposited as a thin layer or a molecular monolayer. The first moiety is acyl chloride, anhydride, hydroxy, ester, ether, aldehyde, ketone, carbonate, acid, epoxy, aziridine, phenol, amine, amides, imides, isocyanates, thiols, sulfones, halides, phosphines, phosphine oxides, nitros, azo, benzophenones, acetals, ketals, diketone, or the organosilane; or the organosilane, hydroxy, acyl chloride, or carboxylic acid. The second moiety comprises a substituted ethylenic organic molecule, or a monomeric ring. It is dienes, alkenes, acrylics, methacrylic, acrylamides, methacrylamides, vinylethers, vinyl alcohols, ketones, acetals, vinylesters, vinylhalide, vinylnitrile, styrene, vinyl pyridines, vinyl pyrrolidone, vinyl imidazoles, vinyl heterocyclics, styrene, cyclic lactams, cyclic ethers, cyclic lactones, cycloalkenes, cyclic thioesters, cyclic thioethers, aziridines, phosphozines, siloxanes, oxazolines, oxazine, or thiirane; amines, nitrites, alcohols, carboxylic acids, sulfonic acids, isocyanate, acyl chloride, ester, amide, anhydride, epoxy, halide, acetoxy, vinyl, or silanol; or peroxide, nitroxide, halide, azo, perester, thioester, hydroxy, metal organics having the stoichiometry of RX. The one or more functionalities react with each other to form a covalent bond. The functionalities are provided by one or more functional groups from amines, nitriles, alcohols, acids, carboxylic acids, sulfonic acids, isocyanates, acyl chlorides, esters, amides, anhydrides, epoxies, halides, acetoxy, vinyl, or silanol. The condensed phase is a liquid. The liquid is a solvent for the polymer, a solvent for the reactive molecule, or a solvent for the reactive monomer.

R = benzyl, cumyl, butyl, alkyl, or naphthalene; and

X = sodium, lithium, and potassium; protonic acids, Lewis acids, carbenium salts, tosylates, triflates, benzophenones, aryldiazonium, diaryliodonium, triarylsulfonium, acetals, ketals, or diketones.

INORGANIC CHEMISTRY - Preferred Component: The areas of second atomic composition comprise copper.

L40 ANSWER 9 OF 14 WPIX COPYRIGHT 2009 THOMSON REUTERS on STN

ACCESSION NUMBER: 2004-023263 [02] WPIX

DOC. NO. CPI: C2004-007311 [02]
DOC. NO. NON-CPI: N2004-018013 [02]

TITLE: Forming inorganic structure, for use as e.g. electronic

photonic and nano composite materials, comprises providing substrate with repeat protein polymer, and exposing substrate to precursor containing inorganic

species

DERWENT CLASS: J04; P42 INVENTOR: KUMAR M

PATENT ASSIGNEE: (DOWO-C) DOW CORNING CORP; (GEMV-C) GENENCOR INT INC;

(KUMA-I) KUMAR M

COUNTRY COUNT: 101

PATENT INFORMATION:

PATENT NO	KIND DATE	WEEK LA	PG	MAIN IPC
WO 2003099465 US 20040014186 AU 2003233579 EP 1509336 AU 2003233579 US 7381789		(200443) EN (200517) EN (200559) EN	27[0]	

#### APPLICATION DETAILS:

PATENT NO KIND	APPLICATION DATE
WO 2003099465 A1 US 20040014186 A1 Provisional AU 2003233579 A1 AU 2003233579 A8	WO 2003-US15757 20030520 US 2002-381913P 20020520 AU 2003-233579 20030520 AU 2003-233579 20030520
EP 1509336 A1	EP 2003-729016 20030520
US 20040014186 A1	US 2003-441965 20030520
EP 1509336 A1	WO 2003-US15757 20030520
US 7381789 B2 Provisional	US 2002-381913P 20020520
US 7381789 B2	US 2003-441965 20030520

#### FILING DETAILS:

PATENT NO	KIND	PATENT NO		
EP 1509336 A1	.1 Based on Based on .8 Based on	WO 2003099465 A		
PRIORITY APPLN. INFO:	US 2002-381913P US 2003-441965			
INT. PATENT CLASSIF.:		20030320		
IPC ORIGINAL:	C07K0017-00 [I,A];	C07K0017-00 [I,C]		
IPC RECLASSIF.:	B05D0001-36 [I,A];	B05D0001-36 [I,C];	B05D0007-00	[I,A];
	B05D0007-00 [I,C];			
	C07K0017-00 [I,C];			
	C08J0007-06 [I,A];			
	C09D0189-00 [I,A];			
	C12P0003-00 [I,C]			
ECLA:	C07K0014-00B1; C07F	<0017-14		
	Y01N0002:00			
USCLASS NCLM:	435/168.000			
NCLS:	530/400.000; 530/42	20.000; 977/715.000		
BASIC ABSTRACT:				

WO 2003099465 A1 UPAB: 20060120

NOVELTY - Forming an inorganic structure comprises providing substrate with a repeat protein polymer, and exposing the substrate to a precursor comprising inorganic species. The repeat protein polymer catalyzes the formation of an inorganic structure on the substrate.

DETAILED DESCRIPTION - Forming inorganic structure comprises providing substrate with repeat protein polymer, and exposing the substrate to a precursor comprising inorganic species. The repeat protein polymer catalyzes

the formation of an inorganic structure on the substrate. The repeat protein polymer has formula Ty((Anx(B)b(A'n')x'(B')b'(A''n'')x'')iT'y'.

A, A' and A'' = individual unit of repeat amino acid sequence;

B, B' and b' = any amino acid sequence of 4-50 amino acids;

n, n' and n'' = at least 2 - 250;

i = 1-100;

T, T', y and y' = 1-100 amino acid sequence containing fewer than 20% of the amino acids in the repeat protein copolymer; and

x = 0- at least 1 and varies with the number of different amino acids in A to provide for at least 30 amino acids in each A repeat sequence.

 $\mbox{USE}$  -  $\mbox{Used}$  for forming inorganic structure useful for, e.g. electronic photonic and nano composite materials.

 ${\tt ADVANTAGE}$  — The process is highly controlled from the nanometer scale to the macroscopic scale.

MANUAL CODE: CPI: J04-E

TECH

BIOLOGY - Preferred Components: The substrate has repeat protein polymers on it. Each repeat protein polymer are the same or different from another at least one of the repeat protein polymer. The repeat protein polymer has a SEQ ID NO. 20-25. The inorganic species comprises species containing silicon, zirconium, silver (preferred), copper, cadmium, tantalum, yttrium, iron, titanium, cobalt, and/or calcium. The inorganic species is preferably tetraethyl orthosilicate (TEOS), 3-aminopropyltriethoxy silane, and/or phenyl tri ethoxy silane. The inorganic species is yttrium ethoxide, silver nitrate, and/or calcium chloride. The substrate has a surface. The repeat protein polymer is on a portion of the surface of the substrate. The inorganic structure forms on the surface of the substrate in areas with repeat protein polymer. The repeat protein polymer forms a pattern on the surface. The inorganic structure forms on the substrate in areas with the repeat protein polymer. The inorganic structure has features with a size of 1-999 nm. The repeat polymer comprises self-assembled monolayer.

polymer comprises self-assembled monolayer on the substrate. The inorganic structure comprises meso porous fibrous silica particles. The repeat protein polymer has an overall cationic charge. The repeat protein polymer has lysine(s). Preferred Methods: The method also comprises placing the repeat protein polymer on the substrate with soft lithographic stamp, and placing the repeat protein polymer on the substrate by rapid printing. The method also comprises providing second repeat protein polymer in contact with the first organic structure. The first and second inorganic structures comprise single inorganic structure containing 3-dimensional structure.

ABEX DEFINITIONS - Preferred Definitions: - A, A' and A'' = 3-30, preferably SEQ ID NO. 1, 3-11; - i = 1-50, preferably 1-30; and - T = 1-60 amino acid sequence.

L40 ANSWER 10 OF 14 WPIX COPYRIGHT 2009 THOMSON REUTERS on STN

ACCESSION NUMBER: 2004-022536 [02] WPIX

DOC. NO. CPI: C2005-142522 [48] DOC. NO. NON-CPI: N2005-379459 [48]

TITLE: Deriving fluid-impervious surface with mixed monolayer

used in lab-on-a-chip technology, by exposing base

surface to first solution, removing portion of monolayer, and exposing base surface portion to second molecule(s)

DERWENT CLASS: A35; A85; A89; A96; B04; D16; D22; J04; L03; P42; S03;

U11; U12; U13

INVENTOR: BABCOCK B

PATENT ASSIGNEE: (BABC-I) BABCOCK B

COUNTRY COUNT: 99

PATENT INFORMATION:

PAT	ENT NO	KINI	D DATE	WEEK	LA	PG	MAIN	IPC
AU US	2003076082 2002367538 20050227232 2002367538	A1 A1	20030922 20051013	(200402) * (200431) (200567) (200615)	EN EN	34[10]		

#### APPLICATION DETAILS:

PATENT NO KIND	APPLICATION DATE
TIO 2002076002 72	TAO 2002 HG2E124 20021101
WO 2003076082 A2	WO 2002-US35134 20021101
US 20050227232 A1 Provisional	US 2001-335165P 20011101
AU 2002367538 A1	AU 2002-367538 20021101
US 20050227232 A1	WO 2002-US35134 20021101
US 20050227232 A1	US 2004-494122 20040812
AU 2002367538 A8	AU 2002-367538 20021101

#### FILING DETAILS:

PATENT NO	KIND	P <i>P</i>	ATENT NO
AU 2002367538	A1 Base	ed on WC	2003076082 A
AU 2002367538	A8 Base	ed on WC	2003076082 A

PRIORITY APPLN. INFO: US 2001-335165P 20011101 US 2004-494122 20040812

INT. PATENT CLASSIF.:

MAIN: B01J019-00 SECONDARY: B05D001-28

IPC RECLASSIF.: B01L0003-00 [I,A]; B01L0003-00 [I,C]; B05D0001-18 [I,A];
B05D0001-18 [I,C]; B05D0003-00 [I,A]; B05D0003-00 [I,C];
B05D0003-12 [I,A]; B05D0003-12 [I,C]; C07B0061-00 [N,A];
C07B0061-00 [N,C]; C12M0001-34 [I,A]; C12M0001-34 [I,C];

C12Q0001-68 [I,A]; C12Q0001-68 [I,C]

C12Q0001-00 [1,A], C12Q0001-00 [1,C]

ECLA: B01L0003-00C6M; B05D0001-18C; B05D0003-00S; B05D0003-12;

C12Q0001-68B10A+527/150+527/125+523/308

ICO: L01J0219:00C; L01L0300:00S; L01L0400:08P4; M07B0061:00L;

M07M0011:00; Y01N0006:00

USCLASS NCLM: 435/006.000

NCLS: 427/002.110; 435/287.200

BASIC ABSTRACT:

WO 2003076082 A2 UPAB: 20060120

NOVELTY - Derivatizing fluid-impervious surface with mixed monolayer by exposing base surface with proximal and distal portion(s) to first solution to form monolayer surface, removing portion of monolayer to expose base surface portion, and exposing base surface portion to second molecule(s). The second molecule(s) has functional group with different surface energy to form surface energy gradient.

DETAILED DESCRIPTION - Deriving fluid-impervious surface with mixed monolayer comprises exposing base surface with proximal and distal portion(s) to a first solution to promote formation of self-assembled monolayer from solution for time to form monolayer surface, removing portion of the monolayer such that portion of the base surface is again exposed, and exposing portion of the base surface to second molecule(s). The first solution comprises molecule(s) of formula X-J-M1. The second molecule(s) includes functional group with different surface energy from the functional group removed in the removing step to form a surface energy gradient from a proximal location to a distal location.

M1, X = separate functional groups; and J = spacer moiety.

 ${\tt USE-For\ deriving\ fluid-impervious\ surface\ with\ mixed\ monolayer\ useful} \\ {\tt in\ lab-on-a-chip\ technology\ (claimed).} \\$ 

ADVANTAGE - The invention allows to produce micro-fabricated systems smaller and more energy-efficient. It provides fluid to be transported with minimal or reduced external forces.

DESCRIPTION OF DRAWINGS - The figure shows a blown-up schematic view of the method for producing mixed monolayer surface energy gradient. MANUAL CODE: CPI: A10-E01; A11-C04D; A12-E13; A12-L04B; A12-V03C2;

A12-V03D; B04-C03; B05-A01B; B05-A02; B05-A03; B05-B02C; D05-H10; D09-C05; J04-B01; L04-C22 EPI: S03-E15; U11-A09; U11-C05A; U11-C05B9; U11-C18B9; U12-B03F1; U13-D04

TECH

INORGANIC CHEMISTRY - Preferred Methods: The portion of monolayer is removed while the base and monolayer surfaces are immersed in the first or second solution, or while a third solution amount containing molecule of formula X-J-M2 is increased.

J, X = separate functional groups;

X = carboxylic acids or sulfur-containing functional group, e.g. thiols,
(di)sulfides, (chloro)silanes, (iso)nitriles, hydroxamic acid, phosphoryl
groups, sulfonyl groups, hydroxyl group, or amino acid groups;

J = preferably hydrocarbon chain of formula (CH2)n, e.g. methyl, propenyl, ethynyl, cyclohexyl, phenyl, tolyl, or benzyl;

M = -OH, -OHNH-, -CONHCO-, -NH2, -NH-, -COOH, -COOR, -CSNH-, -NO2-, -SO2-, -RCOR-, -RCSR-, -RSR, -ROR-, -PO4-3, -OSO3-2, -SO3-, -NHxR4-x+, -COO, -SOO, -RSOR, -CONR2, -(OCH2CH2)nOH, -CH3, -PO3H-, 2-imidazole, -N(CH-sub.3), -NR2, -PO3H2, -CN, -(CF2)n, CF3, CO2CH3, CONHCH3, CH3, CHCH2, OCH2CF2CF3, (CF2)5CF3, (CF2)7CF3, OCH3, Cl, CN, Br, or olefins; n = 1-22;

R = H or organic group, e.g. hydrocarbon or fluorinated hydrocarbon including (cyclo)alkyl, alkenyl, alkynyl, aryl, alkaryl, or aralkyl; and

M2 = functional group with different surface energy than M1 to allow the mixed monolayer surface of the two moieties to be formed with an increasing molar ratio M2:M1 to create a gradient.

The portion of monolayer is removed by passing an instrument along the monolayer surface with force, etching chemically the monolayer portion, cutting with laser or water, drilling, sonic mechanism, etching through thermometric exposure, blasting with grit, or cutting with an instrument. The monolayer is preferably removed by atomic force microscopy probe or scanning probe lithography probe.

Preferred Components: The gradient is created on the inside or outside of the tube, or on face(s) of a rectangular channel. The base surface is metal (oxide). The metal oxide comprises silica, alumina, quartz, or glass. The metal is gold, silver, copper, cadmium, zinc, palladium, platinum, mercury, lead, iron, chromium, manganese, tungsten, or their alloys. The base surface can also be germanium, gallium, arsenic, gallium arsenide, epoxy compounds, polysulfone compounds, plastics, polyanhydride, poly lactic acids, polyglycolic acid, or other polymers.

L40 ANSWER 11 OF 14 WPIX COPYRIGHT 2009 THOMSON REUTERS on STN

ACCESSION NUMBER: 2003-765226 [72] WPIX

CROSS REFERENCE: 2004-088997

DOC. NO. CPI: C2003-210013 [72] DOC. NO. NON-CPI: N2003-612910 [72]

TITLE: Formation of anti-charging layers for beam

lithography, comprises applying self-assembled monolayer with metal ligand

sites to substrate, binding metal deposit to ligand

sites, and applying resist to metal deposit

DERWENT CLASS: A26; A89; G06; L03; P84; U11

INVENTOR: BRANDOW S L; CHEN M; DOBISZ E; DRESSICK W J

PATENT ASSIGNEE: (BRAN-I) BRANDOW S L; (CHEN-I) CHEN M; (DOBI-I) DOBISZ E;

(DRES-I) DRESSICK W J; (USNA-C) US SEC OF NAVY; (USNA-C)

US SEC OF NAVY NAVAL RES LAB

COUNTRY COUNT: 93

#### PATENT INFORMATION:

PATENT NO	KIND DATE	WEEK LA	PG	MAIN IPC
US 20020177083 US 6586158	A1 20021128 B2 20030701			
WO 2002095787	A2 20021128	, ,		
AU 2002321990	A1 20021203	(200452) EN		
AU 2002321990	A8 20051006	(200612) EN		

#### APPLICATION DETAILS:

US 20020177083 A1 US 2001-864384 20010525 AU 2002321990 A1 AU 2002-321990 20020208 WO 2002095787 A2 WO 2002-US3885 20020208 AU 2002321990 A8 AU 2002-321990 20020208	

#### FILING DETAILS:

PA:	TENT NO	KIND			PA:	TENT NO	
AU	2002321990	A1	Based	on	WO	2002095787	A
AU	2002321990	A8	Based	on	WO	2002095787	A

PRIORITY APPLN. INFO: US 2001-864384 20010525

INT. PATENT CLASSIF.:

MAIN: G03F007-00; G03F007-16

SECONDARY: G03F007-00

IPC RECLASSIF.: G03C0005-04 [I,A]; G03C0005-04 [I,C]; G03C0007-04 [N,A];

G03C0007-04 [N,C]; G03F0007-09 [I,A]; G03F0007-09 [I,C];

G03F0007-16 [I,A]; G03F0007-16 [I,C]

ECLA: G03C0005-04; G03F0007-09C; G03F0007-16L

ICO: \$03C0007:04 USCLASS NCLM: 430/324.000

NCLS: 430/005.000; 430/296.000; 430/322.000; 430/942.000;

430/967.000

BASIC ABSTRACT:

US 20020177083 A1 UPAB: 20050905

NOVELTY - Formation of anti-charging layers for beam lithography comprises applying a self-assembled monolayer (SAM) (26) having metal ligand sites to a substrate (20), binding a metal deposit to the ligand sites of the metal ligating self-assembled monolayer, and applying a resist to the metal deposit.

DETAILED DESCRIPTION - INDEPENDENT CLAIMS are included for:

(1) a method for conducting beam lithography comprising applying a SAM having metal ligand sites to a resist, binding a metal deposit to the SAM, forming an anti-charging layer, exposing the resist with a beam, and developing the resist; and

(2) an improved resist layer comprising a layer of polymer resist, disposed over a wafer for lithographic patterning, a metal deposit for conductively dissipating charge, in contact with the polymer resist layer either directly or through a SAM, and a ground connect for connecting the metal deposit to the ground.

USE - For forming anti-charging layers for conducting beam lithography (claimed) and mask fabrication.

ADVANTAGE - The formation of anti-charging layers reduces beam displacement and increases pattern placement accuracy. The method utilizes economical wet chemical processing involving simple dip-coating or spin-coating steps for application of the charge dissipation layer. The use of electroless plating without the metal-binding organosiloxane film offers similar cost advantages. The method offers a unique, economical method for controlling workpiece charging.

DESCRIPTION OF DRAWINGS - The figure shows the successive stages of using a SAM-metal layer to reduce charging in e-beam lithography using electroless plating of metal on SAM on bare substrate or polymer prior to photoresist coating.

substrate (20)
planarizer (23)

self-assembled mono layer (26)

MANUAL CODE:

CPI: A12-E07C; A12-L02B2; G06-A; G06-D06; G06-E02; G06-E04; G06-F03C; G06-G17; G06-G18; L04-C06A EPI: U11-C04F1; U11-C04F2; U11-C04G1; U11-C04G2

TECH

ELECTRONICS - Preferred Method: Alternately, a resist is applied to substrate, an SAM (II) having metal ligand sites is applied to the metal, and a metal deposit (II) is bound to the SAM (II). The SAM is applied by physisorption, chemisorption, wet chemical dipping, or spin casting. The metal deposit forms a conductive pathway. The step of binding the metal deposit to the ligand sites, involves binding by electroless metallization. The metal deposit is removed. Preferred Substrate: The substrate is patterned or non-patterned. The substrate is a surface with a planarizer (23). Preferred Resist: The resist is a composite SAM film. ORGANIC CHEMISTRY - Preferred Compound: The SAM is assembled from monomers having formula RSiR'nX3-n, where R is a ligand group, R' is an alkyl or axyl group, X is a halide or alkoxide group, and n is 0-2.

METALLURGY - Preferred Metals: The metal is chosen from copper, cobalt, nickel and gold.

ABEX EXAMPLE - A ligand self-assembled monolayer

(SAM) organosilane layer was deposited from a 1 vol% aqueous solution of (2-aminoethyl)-3-aminopropyltrimethoxysilane (EDA) containing 0.001 M acetic acid (p $\Re$  5). A puddle of the EDA solution was placed on the substrate surface for approximately 15 seconds. Excess solution was removed by spin-casting at 3000 rpm for 15 seconds while rinsing the substrate in a stream of water, followed by spinning an additional 15 seconds to remove water. The substrate was dried by baking at 120degreesC for 4 minutes to complete the chemisorption of the EDA SAM. A palladium/tin catalyst was applied for 5 minutes and the sample was gently rinsed 3 times in 0.1 M hydrochloric acid (aq). An accelerator was applied for 90 seconds and removed. Copper was then deposited by immersion of the substrate in copper bath for 30 seconds at 25degreesC. The resist was then spun onto the copper-coated workpiece and processed, exposed, and developed under standard conditions. The developed pattern was wet-etched into the 15 nm thick copper layer by a 5-10 second immersion in 50% nitric acid solution. The pattern was etched into the planarizer and then into the substrate. The resist was removed, followed by 5-10 second immersion in 50% nitric acid to remove the remaining copper

discharge layer. The planarizer was then removed.

L40 ANSWER 12 OF 14 WPIX COPYRIGHT 2009 THOMSON REUTERS on STN

ACCESSION NUMBER: 2003-671372 [63] WPIX

DOC. NO. CPI: C2003-183086 [63]

TITLE: Reversibly modifying property of

surface e.g. plate for offset printing or

chromatographic medium, comprises depositing nanolayer of material and applying external stimulus so that nanolayer

shifts to different conformation state

DERWENT CLASS: B04; E17; J04; P81

INVENTOR: LAHANN J; LANGER R S; MITRAGOTRI S; MITRAGOTRI S S PATENT ASSIGNEE: (LAHA-I) LAHANN J; (LANG-I) LANGER R S; (MASI-C)

MASSACHUSETTS INST TECHNOLOGY; (MITR-I) MITRAGOTRI S S

COUNTRY COUNT: 99

#### PATENT INFORMATION:

PATENT NO	KIND DATE	WEEK LA	PG	MAIN IPC
WO 2003055590	A2 20030710	(200363)* EN	66[12]	
US 20030142901	A1 20030731	(200363) EN		
AU 2002365147	A1 20030715	(200421) EN		
EP 1441695	A2 20040804	(200451) EN		
AU 2002365147	A8 20051020	(200615) EN		
US 7020355	B2 20060328	(200623) EN		
US 20060263033	A1 20061123	(200678) EN		

#### APPLICATION DETAILS:

PATENT NO KIND	APPLICATION DATE
WO 2003055590 A2	WO 2002-US34970 20021101
US 20030142901 A1 Provisional	US 2001-350090P 20011102
US 7020355 B2 Provisional	US 2001-350090P 20011102
US 20030142901 A1	US 2002-284794 20021031
US 7020355 B2	US 2002-284794 20021031
AU 2002365147 A1	AU 2002-365147 20021101
AU 2002365147 A8	AU 2002-365147 20021101
EP 1441695 A2	EP 2002-803299 20021101
EP 1441695 A2	WO 2002-US34970 20021101
US 20060263033 A1 Provisional	US 2001-350090P 20011102
US 20060263033 A1 Div Ex	US 2002-284794 20021031
US 20060263033 A1	US 2006-390405 20060327

## FILING DETAILS:

PA	PATENT NO		KIND		PA.	PATENT NO	
EF AU	200236 144169 200236 200602	5 5147	A1 A2 A8 A1	Based on Based on Based on Div ex	WO WO	2003055590 2003055590 2003055590 7020355	A A A A
			US US	2002-284794 2001-350090P 2006-390405	2002	21031 11102 50327	_

INT. PATENT CLASSIF.:

MAIN: B01J019-00

IPC ORIGINAL: G02B0006-00 [I,A]; G02B0006-00 [I,C]; G02B0006-35 [I,A];

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G02B0006-35 [I,C]; H01M0004-86 [I,A]; H01M0004-86 [I,C]
 IPC RECLASSIF.:
                      A61K0009-00 [I,A]; A61K0009-00 [I,C]; B01J0020-281 [I,C];
                      B01J0020-286 [I,A]; B01J0020-30 [I,C]; B01J0020-32 [I,A];
                      B01L0003-00 [I,A]; B01L0003-00 [I,C]; B05D0001-18 [N,A];
                      B05D0001-18 [N,C]; B05D0005-04 [N,A]; B05D0005-04 [N,C];
                      B05D0005-08 [N,A]; B05D0005-08 [N,C]; B29C0059-00 [I,C];
                      B29C0059-16 [I,A]; B41C0001-10 [I,A]; B41C0001-10 [I,C];
                      C40B0060-14 [N,A]; C40B0060-14 [N,C]; F15C0005-00 [I,A];
                      F15C0005-00 [I,C]; F16K0099-00 [I,A]; F16K0099-00 [I,C];
                      G01N0030-00 [N,A]; G01N0030-00 [N,C]; G02B0006-35 [I,A];
                      G02B0006-35 [I,C]; G11B0007-00 [N,C]; G11B0007-0045 [N,A]
                      ; G11C0013-02 [I,A]; G11C0013-02 [I,C]; H01M0008-04 [I,A]
                      ; H01M0008-04 [I,C]; H01M0008-06 [I,A]; H01M0008-06 [I,C]
                      B01J0020-286; B01J0020-32; B01L0003-00C2S;
ECLA:
                      B01L0003-00C6M; B29C0059-16; B41C0001-10B; F16K0099-00M;
                      G02B0006-35L; G11C0013-02; H01M0008-04C2E; H01M0008-06C
ICO:
                      L01J0219:00C2D24D; L01L0003:00C2S; L01L0003:00C6M;
                      L01L0300:00G14; L01L0300:00G4S; L01L0400:06S;
                      L05D0001:18C; L05D0005:04; L05D0005:08; L82T0201:01;
                      M40B0060:14; S01N0030:00+L01D15/20;
                      S01N0030:00+L01D15/38S; S02B0006:35E4; S02B0006:35N4D2;
                      S02B0006:35P4; S02B0006:35P4E; S11B0007:0045;
                      T01M0008:04F; Y01N0004:00; Y01N0006:00
USCLASS NCLM:
                      385/016.000
                      365/151.000; 365/153.000; 429/041.000
       NCLS:
BASIC ABSTRACT:
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WO 2003055590 A2 UPAB: 20060120

NOVELTY - Reversibly modifying a property of a surface comprises depositing a nanolayer of a material on the substrate and applying an external stimulus to the nanolayer. When the stimulus is applied, the nanolayer shifts from a first conformation state to a second conformation state.

DETAILED DESCRIPTION - INDEPENDENT CLAIMS are also included for:

- (a) operating a microfluidic system which comprising adjusting the conformation state of portions of a surface to create a predetermined pattern of channels defined by hydrophilic and hydrophobic regions; and
- (b) a switch for a waveguide positioned at a junction between an incoming waveguide and first and second outgoing waveguides, which comprises a chamber having a surface and containing a liquid and a gas and an interface between them. The surface comprises a nanolayer of material.

USE - The reversibly modified surface is used in a plate for offset printing, a data storage medium, a polymer electrolyte membrane fuel cell, a switch for a waveguide, a microfluidic system, a biosensor or a medium for chromatographic separation (all claimed). It is used to produce optical switches, useful in e.g. cross connects and add drop multiplexes, and for use in fiber optical devices, drug delivery, exploiting simultaneous dual surface properties, electronic and physical applications, biological and chemical applications, absorption and desorption in response to an external stimulus, and photolithography.

ADVANTAGE - The process dynamically controls surface wettability without chemical reactions, but exploits conformational transitions of molecules confined as a low-density film on a surface. MANUAL CODE: CPI: B04-C03; B05-B02C; B10-C04E; E10-C04D2; J04-C TECH

CHEMICAL ENGINEERING - Preferred Components: When the nanolayer is in the first and second conformation states, the surface is attributed by a first and second property, respectively. The property is the degree of hydrophilicity, degree of hydrophobicity, electrical charge, chemical composition, polarizability, transparency, conductivity, light absorption, affinity for a biomolecule, affinity for a small molecule, affinity for a bioactive agent, osmotic potential, zeta potential, surface energy,

coefficient of friction and/or tackiness.

The change in conformation state comprises a change from a cis to a trans configured double bond, rotating a molecular group about an axis, opening a hinged molecular group, bending a molecular chain or unbending a molecular chain. The nanolayer comprises a self-

assembled monolayer comprising molecular assemblies each

having a cleavable end-group. It comprises molecular assemblies each comprising first and second information carriers.

Preferred Method: The external stimulus is application of a voltage, a change in an applied voltage, a change in temperature, a change in pi, exposure to UV light, exposure to electromagnetic radiation, application of a magnetic field, removal of a magnetic field, a change in capacitance, application of an electrostatic charge and/or removal of an electrostatic charge, or exposure to a ligand, exposure to a biomolecule, exposure to a small molecule, exposure to a bioactive agent and/or exposure to an ion.

The substrate comprises a metal, ceramic, glass, non-crystalline solid, semiconductor, polymer and/or composite. A surface of the substrate is pretreated before the step of depositing. Pretreatment comprises depositing a material on portion(s) of the surface, oxidizing portion(s) of the surface and/or etching portion(s) of the surface. The deposition step comprises chemical vapor deposition, metal oxide chemical vapor deposition, sputtering, sol-gel techniques, evaporation, pulsed laser deposition, ion beam assisted deposition, molecular self assembly, soft lithography, layer by layer deposition or Langmuir Blodgett techniques. The end group is removed. A change in conformation state comprises causing a terminal group of the molecular assembly to bend towards the substrate.

ORGANIC CHEMISTRY - Preferred Components: The monolayer comprises 16-mercaptohexadecanoic acid.

L40 ANSWER 13 OF 14 WPIX COPYRIGHT 2009 THOMSON REUTERS on STN

ACCESSION NUMBER: 2003-559303 [52] WPIX

DOC. NO. CPI: C2003-150813 [52] DOC. NO. NON-CPI: N2003-444606 [52]

TITLE: Functional element, useful e.g. for analyte detection and

controlling cell growth, comprises nanoparticles immobilized on a surface and having specific-binding

properties

DERWENT CLASS: A89; B04; C07; D13; D15; D16; J04; Q68; S03; T01

INVENTOR: BRUNNER H; HAUSER N; RUPP S; SCHIESTEL T; TOVAR G; WEBER

Α

PATENT ASSIGNEE: (FRAU-C) FRAUNHOFER GES FOERDERUNG ANGEWANDTEN; (FRAU-C)

FRAUNHOFER GES FOERDERUNG ANGEWANDTEN EV

COUNTRY COUNT: 101

# PATENT INFORMATION:

PAT	TENT NO	KINI	D DATE	WEEK	LA	PG	MAIN IPC
WO	2003056336	A2	20030710	(200352)*	DE	92[9]	
DE	10164309	A1	20030710	(200355)	DE		
AU	2002358799	A1	20030715	(200421)	EN		
EP	1461619	A2	20040929	(200463)	DE		
US	20050048570	A1	20050303	(200517)	EN		
JP	2005524829	W	20050818	(200555)	JA	41	
ΑU	2002358799	A8	20051027	(200624)	EN		

#### APPLICATION DETAILS:

PATENT NO	KIND	APPLICATION DATE	
WO 2003056336 DE 10164309 A AU 2002358799 EP 1461619 A2 EP 1461619 A2 US 2005004857 JP 2005524829 JP 2005524829 US 2005004857 AU 2002358799	A2 l A1 O A1 W W O A1	WO 2002-EP14769 20021227 DE 2001-10164309 20011228 AU 2002-358799 20021227 EP 2002-793118 20021227 WO 2002-EP14769 20021227 WO 2002-EP14769 20021227 WO 2002-EP14769 20021227 JP 2003-556808 20021227 US 2004-500425 20040907 AU 2002-358799 20021227	
FILING DETAILS:			
PATENT NO	KIND	PATENT NO	
AU 2002358799	A1 Based on A2 Based on W Based on A8 Based on	WO 2003056336 A	
PRIORITY APPLN. INFO	D: DE 2001-10164309	20011228	
MAIN:	G01N033-53; G01N033-B01J0019-00 [I,A]; C12N0001-00 [I,C]; C12Q0001-04 [I,A]; C12Q0001-68 [I,C]; CG01N0021-31 [I,C]; CG01N0021-64 [I,C]; CG01N0033-53 [I,A]; CG01N0033-547 [I,A]; G01N0033-547 [I,A]; G01N0033-552 [I,A]; G01N0033-552 [I,A]; G01N0037-00 [I,C] B01J0019-00C; G01N00 L01J0219:00C2D24; L01J0219:00C2D24; L01J0219:00C2D24; L01J0219:00C2L8; L01	-543 301J0019-00 [I,C]; C12N0001 C12N0015-09 [I,A]; C12N0015 C12Q0001-04 [I,C]; C12Q0001 G01N0021-25 [I,C]; G01N0021 G01N0021-33 [I,A]; G01N0027 G01N0033-53 [I,C]; G01N0033 G01N0033-544 [I,C]; G01N00 [I,A]; G01N0033-551 [I,C]; G01N0033-553 [I,A]; G01N00 033-543D6; G01N0033-543M 01J0219:00C2D8; L01J0219:00 01J0219:00C4L12; L01J0219:00	-09 [I,C]; -68 [I,A]; -27 [I,A]; -64 [I,A]; -62 [I,C]; -543 [I,A]; 33-545 37-00 [I,A] C2H2D; C4L2;
USCLASS NCLM:	M40B0060:14; Y01N000		-7
NCLS: JAP. PATENT CLASSIF	435/287.200		
MAIN/SEC.:	C12N0001-00; C12N000 G01N0021-27 Z; G01N0 G01N0033-53 D; G01N0 G01N0033-543 521; G	15-00 A; C12Q0001-04; C12Q0 0021-33; G01N0021-64 Z; G01 0033-53 M; G01N0033-543 501 01N0033-543 525 U; G01N0033 033-552; G01N0033-553; G01N	N0027-62 V; J; -545 Z;
FTERM CLASSIF.:	2G041; 2G043; 2G045 4B065/AA01.X; 2G043 4B065/AA57.X; 4B065 4B065/AA95.X; 4B065 4B065/BC42; 2G041/C 4B024/CA05; 4B024/C 2G059/CC16; 2G043/D 2G043/EA01; 2G041/E 2G059/EE07; 2G059/E 2G041/FA12; 2G059/F	: 2G058; 2G059; 4B024; 4B06 /AA03; 2G059/AA05; 4B024/AA /AA83.X; 4B065/AA86.X; 4B06 /AC20; 2G043/BA16; 2G059/BB A01; 2G043/CA04; 4B024/CA04 A06; 4B024/CA09; 4B065/CA46 A01; 2G041/DA04; 2G059/DD01 A11; 2G043/EA13; 2G059/EE01 E12; 2G043/FA02; 2G041/FA11 F03; 2G041/GA06; 2G043/GA07 A08; 4B024/HA12; 4B024/HA14	3; 4B065; 11; 5/AA87.X; 12; ; ; ; ;

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2G059/HH02; 2G059/HH03; 2G041/JA08; 2G041/JA09; 2G059/JJ01; 2G059/JJ11; 2G043/KA02; 2G043/KA03; 2G059/KK01; 2G043/LA01; 2G059/NN01; 4B063/QA01; 4B063/QA17; 4B063/QA18; 4B063/QA19; 4B063/QQ05; 4B063/QQ16; 4B063/QQ18; 4B063/QQ19; 4B063/QQ42; 4B063/QQ53; 4B063/QR08; 4B063/QR14; 4B063/QR32; 4B063/QR42; 4B063/QS10; 4B063/QS12; 4B063/QS24; 4B063/QS25; 4B063/QS28; 4B063/QS34; 4B063/QS36; 4B063/OS39; 4B063/OX01; 4B063/OX04; 4B063/OX10
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#### BASIC ABSTRACT:

WO 2003056336 A2 UPAB: 20060120

NOVELTY - Functional element (A) comprises a carrier having a surface and at least one microstructure (MS), on the surface, where MS consists of individual nanoparticles (NP) which exhibit molecule-specific recognition sites (X) that make MS addressable.

DETAILED DESCRIPTION - An INDEPENDENT CLAIM is also included for preparation of (A) by applying to the carrier surface first a layer of at least one binding agent and then NP.

USE - (A) are useful:

- (i) in detection processes (mass spectrometry, fluorescence or UV/vis spectrometry, fluorescent or light microscopy, wave-guide or impedance spectrometry and other electrical methods);
  - (ii) for controlling adhesion and growth of cells;
- (iii) for detection/isolation of biomolecules, e.g. interacting
  proteins;
- (iv) for development of pharmaceutical preparations, and for assessing their effects and side-effects;
- (v) for diagnosis of diseases, e.g. identification of pathogens or mutated genes, in humans or animals;
- (vi) to analyze microbial contamination of samples (water, soil, food and animal fodder); and

(vii) as electrical components in a biocomputer.

ADVANTAGE - In (A), biomolecules are immobilized with retention of activity and at high density. NP are morphologically and chemically stable for a long time in solution; provide a very high surface area:volume ratio and make possible a degree of miniaturization not previously achieved.

MANUAL CODE:

CPI: A12-L04B; A12-W11L; B04-B04C; B04-C01; B04-C02C; B04-C03; B04-E01; B04-E10; B04-G01; B04-H01; B04-K01; B04-L01; B04-N04; B05-A01B; B05-A02; B05-A03B; B05-B02A3; B05-B02C; B06-F03; B10-E04C; B11-C07A; B11-C07B1; B11-C07B2; B11-C07B3; B11-C08A; B12-K04A; B12-K04E; B12-K04F; C04-B04C; C04-C01; C04-C02C; C04-C03; C04-E01; C04-E10; C04-G01; C04-H01; C04-K01; C04-L01; C04-N04; C05-A01B; C05-A02; C05-A03B; C05-B02A3; C05-B02C; C06-F03; C10-E04C; C11-C07A; C11-C07B1; C11-C07B2; C11-C07B3; C11-C08A; C12-K04A; C12-K04E; C12-K04F; D05-A02; D05-H09; D05-H10; D05-H11; D05-H12; J04-B01A EPI: S03-E14H4; T01-E05D

TECH

INSTRUMENTATION AND TESTING - Preferred Element: MS covers a flat region of the surface and at least one face-length dimension of the coated region is 10 nm to 999 microns. The surface may be planar or prestructured and carries a layer of a compound that inhibits non-specific attachment of biomolecules. Optionally a layer of binding agent (BA) is present between the surface and MS, e.g. a polymer with charged or uncharged reactive groups, especially a hydrogel; a plasma layer (with similar reactive groups), or a silane- or thiol-based self-assembled monolayer. BA can be switched on or off by alterations in pH, ion concentration or temperature.

Preparation: One or more MS are applied using a needle-ring printer; by lithography (especially photo- or micro-pen- lithography); by ink-jet methods or by micro-contact printing. The surface may be cleaned and/or activated (chemically or by deposition of electrical charges) before application of BA, especially by applying a primer and, after application of BA, it is dipped into a suspension of NP. BA may also be applied by dipping so that the entire surface is treated. Biologically active molecules are attached to (X) before and/or after deposition of NP on the surface.

Preferred Materials: The carrier and/or surface is made of metal (oxide), polymer, semiconductor, glass and/or ceramic. NP consist of a core (organic polymer or inorganic material, preferably of diameter 5-500 nm) and its surface carries (X), covalently or non-covalently linked to one or more biologically active molecules so that these retain their biological activity. The core may include an additional function, e.g. a fluorescent, UV/visible or radioactive marker, or a superparamagnetic or ferromagnetic function. In this case, the core is modified with an (in)organic layer containing reactive groups and exhibiting the second function. The core surface may also be contain a compound that provides steric stabilization; inhibition of conformational change in immobilized molecules and/or inhibition of binding of additional biomolecules. The bound molecules are labeled and/or have further molecules bound to them. The MS consists of one or more layers of NP, and different NP carry different (X). BIOLOGY - Preferred Materials: Materials bound to (X) are proteins (especially antibodies, antigens, enzymes, cytokines or receptors), nucleic acids or peptide nucleic acids, or their fragments. Particularly (X) and the bound molecules contain complementary reactive groups, e.g. reactive ester, aldehyde, amino, carboxy, epoxy, oligohistidine, metal chelate, biotin, streptavidin etc. Both function groups may be present in a spacer, or attached through a spacer.

POLYMERS - Preferred Materials: Suitable polymers for the core of NP are polypropylene, polystyrene and/or polyacrylate. The material that provides steric stabilization etc. is a poly- or oligo-ethylene glycol and/or dextran.

INORGANIC CHEMISTRY - Preferred Materials: Suitable materials for the core of NP include metals (gold, silver or nickel); silicon or its oxides; silicates; alumina; zeolites; indium-tin oxide, hydroxylapatite etc.

EXAMPLE - Silica particles (mean diameter 125 nm) were prepared by

ABEX EXAMPLE - Silica particles (mean diameter 125 nm) were prepared by hydrolysis of tetraethoxysilane with ammonia in ethanol. Separately, a silicon carrier was treated with 2wt.% Hellmanex (RTM) solution at 40 degrees Centigrade; then rinsed and dried; hydroxylated with ammonia/hydrogen peroxide and incubated for 20 minutes with a solution of poly(diallyldimethylammonium chloride). It was washed and dried again, then the suspension of silica particles applied to the treated surface using a commercial ring/pin microarrayer, to form 150-200 micron diameter dots a few microns apart. When the suspension was applied once or twice, distribution of particles over the dot was uniform, but if many (10) applications were made, the particles concentrated at the edge of the dot.

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L40 ANSWER 14 OF 14 WPIX COPYRIGHT 2009
                                                THOMSON REUTERS on STN
ACCESSION NUMBER:
                     2001-308300 [32]
                                        WPIX
                     1993-406102; 2000-686478; 2002-224757; 2002-371471;
CROSS REFERENCE:
                      2003-220243; 2005-402422
DOC. NO. CPI:
                     C2001-095244 [32]
DOC. NO. NON-CPI:
                     N2001-220629 [32]
TITLE:
                     Electronic device for memory applications comprises two
                      or more contacts and monolayer of conductive organic
                      material forming conductive path including electron
                      withdrawing group(s) between contacts
DERWENT CLASS:
                      E19; L03; P73; U14
```

INVENTOR: CHEN J; PRICE D W; RAWLETT A M; REED M A; TOUR J M

PATENT ASSIGNEE: (UYYA-C) UNIV YALE

COUNTRY COUNT:

## PATENT INFORMATION:

PAT	CENT NO	KINI	D DATE	WEEK	LA	PG	MAIN IPC
WO	2001027972	A2	20010419	(200132)*	EN	47[20]	
ΑU	2001032614	Α	20010423	(200147)	EN		
TW	463183	А	20011111	(200248)	ZH		
JΡ	2004518268	W	20040617	(200440)	JA	124	
US	6756605	В1	20040629	(200443)	ΕN		
EΡ	1542869	A2	20050622	(200541)	ΕN		

#### APPLICATION DETAILS:

PATENT NO KIND	APPLICATION DATE
WO 2001027972 A2	WO 2000-US25518 20000918
US 6756605 B1 Provisional	US 1999-154716P 19990920
US 6756605 B1 Provisional	US 1999-157149P 19990930
US 6756605 B1 CIP of	US 2000-527885 20000320
US 6756605 B1	US 2000-551716 20000418
EP 1542869 A2	EP 2000-991376 20000918
JP 2004518268 W	WO 2000-US25518 20000918
EP 1542869 A2	WO 2000-US25518 20000918
TW 463183 A	TW 2000-119232 20001216
AU 2001032614 A	AU 2001-32614 20000918
JP 2004518268 W	JP 2001-530895 20000918

## FILING DETAILS:

PATENT NO	KIND	PATENT NO
AU 2001032614 A JP 2004518268 W EP 1542869 A2	Based on Based on Based on	WO 2001027972 A WO 2001027972 A WO 2001027972 A
PRIORITY APPLN. INFO:	US 2000-551716 US 1999-154716P US 1999-157149P	20000418 19990920 19990930
INT. PATENT CLASSIF.:	US 2000-527885	20000320

MAIN: H01B003-18; H01L051-00 SECONDARY: H01L027-10

IPC RECLASSIF.: G11C0013-02 [I,A]; G11C0013-02 [I,C]; H01L0027-10 [I,A]; H01L0027-10 [I,C]; H01L0027-28 [I,A]; H01L0027-28 [I,C];

H01L0051-05 [I,A]; H01L0051-05 [I,C]

ECLA: G11C0013-02; H01L0051-00T

ICO: L82T0201:01; Y01N0004:00; Y01N0006:00

USCLASS NCLM: 257/040.000

257/041.000; 977/936.000 NCLS:

JAP. PATENT CLASSIF.:

MAIN/SEC.: H01L0027-10 449; H01L0027-10 451; H01L0029-28 FTERM CLASSIF.: 5F083; 5F096; 5F083/FZ07; 5F083/JA19; 5F083/JA37;

5F083/JA38; 5F083/JA39; 5F083/JA60

BASIC ABSTRACT:

WO 2001027972 A2 UPAB: 20080523

NOVELTY - An electronic device comprises two or more contacts and a monolayer of conductive organic material forming a conductive path including electron withdrawing group(s) between the contacts.

DETAILED DESCRIPTION - INDEPENDENT CLAIMS are included for:

- (1) an electronic device comprises two or more contacts at least one being palladium and a self assembled monolayer of a conductive organic molecule comprising phenyl-ethynyl-substituted phenyl-ethynyl- phenyl linkage between the contacts, the substituted phenyl includes nitro group(s) and the organic molecule is bonded to the palladium contact by isocyano group(s) on the terminal phenyl of the linkage;
  - (2) a memory circuit comprises:
  - (a) an input;
  - (b) an output;
- (c) a molecular electronic device as described above where one contact bridges the input and output an another is grounded; and
- (d) a comparator (in electrical communication with a reference voltage) bridging the input and output;
- (3) a memory array comprises the memory circuits above in an addressable array;
- (4) a static random access memory cell comprises at least a first and a second molecular electronic device as described above with the first device connected to a reference voltage and another connected to a node; the second device has one contact connected to ground and another to the node; the node is further connected to ground.

 ${\sf USE}$  - The device is used in memory circuits and arrays and in static random access memory cells (all claimed).

ADVANTAGE - Molecular scale systems offer uniformity of structure, lowered fabrication costs, ease of synthesis and a range of structures.

DESCRIPTION OF DRAWINGS - The drawing shows an embodiment of a molecular scale electronic device.

device (1)
substrate (3)
insulating material (5)
cavity (7)

MANUAL CODE:

CPI: E10-B04E; E10-G03; E35-B; E35-X; L03-G04A; L04-C10F; L04-C11 EPI: U14-A03X

TECH

ELECTRONICS - Preferred Memory Cell: The memory cell (3) further comprises a gain component. Preferred Device: The device has low (current of less than 100 pA, preferably less than 1 pA) and high (more than 200 times higher than low state, preferably more than 1000 times higher) conductivity states and can be repeatedly switched between the two. The device exhibits negative differential resistance at room temperature. ORGANIC CHEMISTRY - Preferred Electron Withdrawing Group: the electron withdrawing group is from cyano, isocyano, nitro, sulfonyl, beta-carboxyvinyl, sulfinyl, beta, beta-dicyanovinyl, halogenated alkyl, formyl, carboxyl, carbonyl, alkyl/axyl-oxycarbonyl, 1-tetrazoyl, 5-chloro-1-tetrazoyl, carbamoyl and sulfamoyl (cyano, isocyano, nitro). The group is bonded to a phanyl ring in the conductive path. Preferred Device: The device further contains electron donating group(s). The conductive path comprises atoms, at least 70% of which are sp- or sp2-hybridized and comprises alternating ethyl and aryl groups with at least one phenyl-ethynyl linkage. At least one phenyl group is substituted with an electron withdrawing group. the conductive path further comprises binding groups (S/O atoms, cyano, carboxy, diazonium salt, halide, isocyano, phosphine, Te/Se atoms) which bind it to the contacts. The conductive path comprises biphenyl and/or ethenyl groups.

ABEX EXAMPLE - Devices were fabricated using low pressure chemical vapor

deposition of Si3N4 onto a silicon (100) wafer, optically etched on one side to remove a  $400 \times 400$  microm square of nitride. The exposed silicon was etched with KOH until only a  $40 \times 40$  microm silicon nitride membrane was left, a 30 - 50 nm hole was made in this by electron beam lithography and reactive ion etching. A metallic gold contact 200 nm thick was evaporated onto the topside of the membrane filling the pore with gold. The sample was immediately transferred to a solution of 2'-amino-4-ethylphenyl-4'-ethynylphenyl-5'-nitro-1-(thioacetyl)benzene (0.5 mM in THF) and ammonium hydroxide (5 microL per mg of (thioacetyl)benzene) for the self assembly to cover over 48 hours under argon. A bottom gold electrode was then evaporated onto the device under vacuum with at 77K and a rate of less than 1 Angstrom per second. the devices were diced into individual chips. The current/voltage plot (60K) for this device shows a peak of 1.03 nA at 2V with the current being near zero at other voltages. The peak voltage position and current peak magnitude varies with temperature.

# => d his 146

(FILE 'HCAPLUS' ENTERED AT 15:22:08 ON 28 OCT 2009)
L46 16 S L32 NOT L45

FILE 'STNGUIDE' ENTERED AT 15:22:37 ON 28 OCT 2009

FILE 'WPIX' ENTERED AT 15:23:27 ON 28 OCT 2009

FILE 'STNGUIDE' ENTERED AT 15:23:38 ON 28 OCT 2009

=> 4	que 146	
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L10		SEA FILE=HCAPLUS ABB=ON PLU=ON PHENYL OR BIPHENYL OR
		TERPHENYL
L11	70335	SEA FILE=HCAPLUS ABB=ON PLU=ON ANTHRACYL OR NAPHTHYL OR
		BIPYRIDYL OR TERPYRIDYL
L12	6620	SEA FILE=HCAPLUS ABB=ON PLU=ON THIOPHENYL OR BITHIENYL OR
		TERTHIENYL OR PYRROLYL
L13	12	SEA FILE=HCAPLUS ABB=ON PLU=ON (BI OR TRI)(W) CYCLOALKANE#
		OR TETRA(W)CYCLOALKANE#
L19	245508	SEA FILE=HCAPLUS ABB=ON PLU=ON ARYL
L20	21238	SEA FILE=HCAPLUS ABB=ON PLU=ON ALICYCLIC
L21	165	SEA FILE=HCAPLUS ABB=ON PLU=ON (L8 OR L9) AND (L19 OR L20)
L23	69	SEA FILE=HCAPLUS ABB=ON PLU=ON L21 AND 66/SC,SX
L24	1	SEA FILE=HCAPLUS ABB=ON PLU=ON L23 AND L7
L25	4	SEA FILE=HCAPLUS ABB=ON PLU=ON L23 AND (SURFACE(W)MODIF?)
L26	8	SEA FILE=HCAPLUS ABB=ON PLU=ON L21 AND LITHOGRAPH?
L27	10	SEA FILE=HCAPLUS ABB=ON PLU=ON (L24 OR L25 OR L26)
L28	46	SEA FILE=HCAPLUS ABB=ON PLU=ON L21 AND ((L10 OR L11 OR L12
		OR L13))
L30	9	SEA FILE=HCAPLUS ABB=ON PLU=ON L28 AND (SURFAC?) (2A)
		(TRANSIT? OR MODIF? OR PATTERN?)
L31	17	SEA FILE=HCAPLUS ABB=ON PLU=ON L27 OR L30
L32		SEA FILE=HCAPLUS ABB=ON PLU=ON L31 AND (L8 OR L9)
L45	18	SEA FILE=WPIX ABB=ON PLU=ON (WO2002-EP14769/AP OR WO2005-GB11
		59/AP OR US2001-350090P/AP OR US2002-284794/AP OR WO2000-US2551
		8/AP OR AU2002-321990/AP OR AU2002-358799/AP OR AU2002-365147/A
		P OR AU2002-367538/AP OR AU2002321990/PN OR AU2002358799/PN OR
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		AU2003233579/PN OR CN2005-10087971/AP OR GB2006-18673/AP OR
		GB2426724/PN OR US2002-381913P/AP OR US2003-441965/AP OR
		WO2002-US34970/AP OR WO2002-US35134/AP OR WO2003-US15757/AP OR
		WO2005-US8850/AP OR WO2005089415/PN OR WO2007-US19894/AP OR
		WO2008108809/PN OR AU2001-32614/AP OR AU2001032614/PN OR
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		143605/AP OR DE10164309/PN OR DE2001-10164309/AP OR EP1441695/P
		N OR EP1461619/PN OR EP1509336/PN OR EP1542869/PN OR EP1630883/
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		EP2002-803299/AP OR EP2003-729016/AP OR EP2005-23880/AP OR EP2005-254258/AP OR JP2001-530895/AP OR JP2003-556808/AP OR
		JP2004518268/PN OR JP2005-216748/AP OR JP2005524829/PN OR
		JP2006049890/PN OR JP2007-274254/AP OR JP2008183702/PN OR
		KR2007-8357/AP OR KR825176/PN OR TW2000-119232/AP OR TW463183/P
		N OR US1999-154716P/AP OR US1999-157149P/AP OR US2000-527885/AP
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OR US2000-551716/AP OR US2001-335165P/AP OR US2001-864384/AP OR US2002-287935/AP OR US2002-307069/AP OR US20020177083/PN OR US2003-421355/AP OR US20030142901/PN OR US2004-494122/AP OR US2004-500425/AP OR US2004-555770P/AP OR US2004-900624/AP OR US20040014186/PN OR US20040087177/PN OR US20040102050/PN OR US2005-83739/AP OR US20050048570/PN OR US20050221081/PN OR US20050227232/PN OR US2006-390405/AP OR US2006-477655/AP OR US2006-594654/AP OR US20060021647/PN OR US20060263033/PN OR US2007-757018/AP OR US20070098899/PN OR US20070140901/PN OR US20080182072/PN OR US6586158/PN OR US6756605/PN OR US6893966/PN OR US7020355/PN OR US7381789/PN OR WO2001027972/PN OR WO2002-US3885/AP OR WO2002095787/PN OR WO2003055590/PN OR WO2003056336/PN OR WO2003076082/PN OR WO2003099465/PN OR WO2005092516/PN)

L46 16 SEA FILE=HCAPLUS ABB=ON PLU=ON L32 NOT L45

#### => d his 144

(FILE 'EMA, COMPENDEX, INSPEC, SCISEARCH, PASCAL, JAPIO' ENTERED AT 15:18:20 ON 28 OCT 2009)

L44 11 S L42 OR L43

#### => d que 144

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L11	70335	SEA FILE=HCAPLUS ABB=ON PLU=ON ANTHRACYL OR NAPHTHYL OR					
		BIPYRIDYL OR TERPYRIDYL					
L12	6620	SEA FILE=HCAPLUS ABB=ON PLU=ON THIOPHENYL OR BITHIENYL OR					
		TERTHIENYL OR PYRROLYL					
L13	12	SEA FILE=HCAPLUS ABB=ON PLU=ON (BI OR TRI)(W) CYCLOALKANE#					
		OR TETRA(W)CYCLOALKANE#					
L34	258	SEA FILE=WPIX ABB=ON PLU=ON (L8 OR L9) AND ((L10 OR L11 OR					
		L12 OR L13))					
L35	14	SEA FILE=WPIX ABB=ON PLU=ON L34 AND LITHOGRAPH?					
L41	102	SEA L35					
L42	11	SEA L41 AND (SURFAC?) (2N) (TRANSIT? OR MODIF? OR PATTERN?)					
L43	1	SEA L41 AND (ARYL OR HETERO(W) ARYL OR ALICYCLIC OR HETERO(W)					
		CYCLIC)					
L44	11	SEA L42 OR L43					

#### => dup rem 146 144

FILE 'HCAPLUS' ENTERED AT 15:24:08 ON 28 OCT 2009
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> 22 DUP REM L46 L44 (5 DUPLICATES REMOVED) ANSWERS '1-16' FROM FILE HCAPLUS ANSWER '17' FROM FILE COMPENDEX ANSWERS '18-19' FROM FILE INSPEC ANSWERS '20-22' FROM FILE SCISEARCH

=> d 147 1-16 ibib abs hitind; d 147 17-22 ibib ab ind

L47 ANSWER 1 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN DUPLICATE 1

ACCESSION NUMBER: 2008:1207298 HCAPLUS Full-text

DOCUMENT NUMBER: 149:425412

L47

Micrometer and Nanometer Scale Patterning Using the TITLE: Photo-Fries Rearrangement: Toward Selective Execution of Molecular Transformations with Nanoscale Spatial

Resolution

Griesser, Thomas; Adams, Joseph; Wappel, Julia; Kern, AUTHOR(S):

Wolfgang; Leggett, Graham J.; Trimmel, Gregor

CORPORATE SOURCE: Institute for Chemistry and Technology of Materials

(ICTM), Graz University of Technology, Graz, 8010,

Austria

Langmuir (2008), 24(21), 12420-12425 SOURCE:

CODEN: LANGD5; ISSN: 0743-7463

PUBLISHER: American Chemical Society

DOCUMENT TYPE: Journal LANGUAGE: English

OTHER SOURCE(S): CASREACT 149:425412

The photolithog. modification of monolayers provides a versatile and powerful means of fabricating functionalized nanostructured surfaces. In this contribution, we present photosensitive thiol-bearing axyl ester groups which are capable of undergoing the so-called photo-Fries rearrangement to yield hydroxy ketones. Ft 16-mercaptohexadecanoate was prepared by a three-step synthesis. This mol. undergoes a photoisomerization reaction upon illumination with UV light at ca. 250 nm. Subsequently this mol. was applied as a self-assembled monolayer on gold. Following photochem. modification, the adsorbates were selectively derivatized to yield amino-functionalized surfaces using a simple two-step reaction. This reaction was monitored by XPS and contact angle measurements and friction force microscopy. Micrometerscale patterned surfaces were produced using a contact mask in conjunction with a frequency-doubled argon ion laser ( $\lambda = 244 \text{ nm}$ ). Near-field optical exposure was carried out by coupling the laser to a scanning near-field optical microscope and yielded nanometer-scale resolution Following derivatization, the resulting structures were analyzed by friction force microscopy. Clear contrast was observed in the friction signal following surface modification. Safety: caution is recommended with UV irradiation, especially with UV lasers. Safety: Piranha solution reacts violently with organic materials.

22-6 (Physical Organic Chemistry) CC Section cross-reference(s): 66, 74

Adsorbed monolavers ΙT Chemoselectivity

(chemoselective photo-Fries rearrangement of adsorbed  $\mathfrak{P}h$  16-mercaptohexadecanoate not accompanied by thiol headgroup photooxidn.)

IT Shadow masks

(for micro-scale photolithog.; chemoselective photo-Fries rearrangement of adsorbed  $\Re h$  16-mercaptohexadecanoate not accompanied by thiol headgroup photooxidn.)

IT Scanning probe microscopy

(frictional-force, for analyzing micro- and nanopatterned monolayers; chemoselective photo-Fries rearrangement of adsorbed %% 16-mercaptohexadecanoate not accompanied by thiol headgroup photooxidn.)

IT Self-assembled monolayers

(micro- and nanoscale patterning using the photo-Fries rearrangement of  $self-assembled\ monolayers$  of Ph

16-mercaptohexadecanoate)

IT Photolithography

(micro- and nanoscale; chemoselective photo-Fries rearrangement of adsorbed Ph 16-mercaptohexadecanoate not accompanied by thiol headgroup photooxidn.)

IT Lithography

(nano-; chemoselective photo-Fries rearrangement of adsorbed  $\mathfrak{Ph}$  16-mercaptohexadecanoate not accompanied by thiol headgroup photooxidn.)

IT Nanostructures

(nanostructure fabrication using photo-Fries rearrangement; chemoselective photo-Fries rearrangement of adsorbed  $\Re h$  16-mercaptohexadecanoate not accompanied by thiol headgroup photooxidn.)

IT Microscopes

(near-field, scanning, used for nanostructure patterning; chemoselective photo-Fries rearrangement of adsorbed  $\mathfrak{Ph}$  16-mercaptohexadecanoate not accompanied by thiol headgroup photooxidn.)

IT Contact angle

ΙT

(of water (sessile drop) as function of SAM modification;
micro- and nanoscale patterning using the photo-Fries rearrangement of
self-assembled monolayers of Ph
16-mercaptohexadecanoate)

Fries rearrangement

(photochem.; micro- and nanoscale patterning using the photo-Fries rearrangement of self-assembled monolayers of Ph 16-mercaptohexadecanoate)

IT 1064082-12-7DP, gold surface-adsorbed

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (amino-terminated SAM; micro- and nanoscale patterning using the photo-Fries rearrangement of self-assembled monolayers of Ph 16-mercaptohexadecanoate)

IT 506-13-8, 16-Hydroxyhexadecanoic acid

RL: RCT (Reactant); RACT (Reactant or reagent)
(bromination; micro- and nanoscale patterning using the photo-Fries rearrangement of self-assembled monolayers of Ph 16-mercaptohexadecanoate)

IT 108-95-2, Phenol, reactions

RL: RCT (Reactant); RACT (Reactant or reagent)
(esterification; micro- and nanoscale patterning using the photo-Fries rearrangement of self-assembled monolayers
of Ph 16-mercaptohexadecanoate)

IT 2536-35-8P, 16-Bromohexadecanoic acid

```
RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT
     (Reactant or reagent)
        (esterification; micro- and nanoscale patterning using the photo-Fries
        rearrangement of self-assembled monolayers
        of Ph 16-mercaptohexadecanoate)
ΙT
     12033-89-5, Silicon nitride, uses
     RL: PEP (Physical, engineering or chemical process); TEM (Technical or
     engineered material use); PROC (Process); USES (Uses)
        (friction force microscopic probe; micro- and nanoscale patterning
        using the photo-Fries rearrangement of self-assembled
       monolayers of Ph 16-mercaptohexadecanoate)
     1064082-11-6DP, gold surface-adsorbed
     RL: RCT (Reactant); SPN (Synthetic preparation); TEM (Technical or
     engineered material use); PREP (Preparation); RACT (Reactant or reagent);
     USES (Uses)
        (hydroxy ketone SAM, post-illumination modification with
        polar amino groups; micro- and nanoscale patterning using the
       photo-Fries rearrangement of self-assembled
       monolayers of Ph 16-mercaptohexadecanoate)
     107-15-3, Ethylenediamine, reactions
                                           111-50-2, Adipoyl chloride
ΤТ
     RL: RCT (Reactant); RACT (Reactant or reagent)
        (post-illumination modification agent; micro- and nanoscale patterning
        using the photo-Fries rearrangement of self-assembled
       monolayers of Ph 16-mercaptohexadecanoate)
     7440-57-5, Gold, uses
ΤT
     RL: TEM (Technical or engineered material use); USES (Uses)
        (substrate; micro- and nanoscale patterning using the photo-Fries
        rearrangement of self-assembled monolayers
        of Ph 16-mercaptohexadecanoate)
ΙT
     1064082-06-9DP, Phanyl 16-mercaptohexadecanoate, gold
     surface-adsorbed
     RL: RCT (Reactant); SPN (Synthetic preparation); TEM (Technical or
     engineered material use); PREP (Preparation); RACT (Reactant or reagent);
     USES (Uses)
        (target aryl ester SAM, photolysis; micro- and
        nanoscale patterning using the photo-Fries rearrangement of
        self-assembled monolayers of Ph
        16-mercaptohexadecanoate)
     1064082-06-9P, Phenyl 16-mercaptohexadecanoate
ΤТ
     RL: PEP (Physical, engineering or chemical process); SPN (Synthetic
     preparation); TEM (Technical or engineered material use); PREP
     (Preparation); PROC (Process); USES (Uses)
        (target axyl ester, surface adsorption; micro- and nanoscale
       patterning using the photo-Fries rearrangement of self-
        assembled monolayers of Ph
        16-mercaptohexadecanoate)
ΙT
     1064082-05-8P, Phenyl 16-bromohexadecanoate
     RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT
     (Reactant or reagent)
        (thiolation; micro- and nanoscale patterning using the photo-Fries
        rearrangement of self-assembled monolayers
        of Ph 16-mercaptohexadecanoate)
OS.CITING REF COUNT:
                               THERE ARE 3 CAPLUS RECORDS THAT CITE THIS RECORD
                         3
                               (3 CITINGS)
REFERENCE COUNT:
                         54
                               THERE ARE 54 CITED REFERENCES AVAILABLE FOR THIS
                               RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT
L47 ANSWER 2 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN
                     2005:453718 HCAPLUS Full-text
ACCESSION NUMBER:
```

142:492259

DOCUMENT NUMBER:

TITLE: Field-assisted micro- and nano-fabrication method

INVENTOR(S): Huang, Wen C.; Jang, Bor Z.

PATENT ASSIGNEE(S): USA

SOURCE: U.S. Pat. Appl. Publ., 12 pp.

CODEN: USXXCO

DOCUMENT TYPE: Patent LANGUAGE: English

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 20050112505	A1	20050526	US 2003-720891	20031125
PRIORITY APPLN. INFO.:			US 2003-720891	20031125

OTHER SOURCE(S): MARPAT 142:492259

AB It is an object of the present invention to provide an improved micro- or nanolithog. method for creating submicrometer or nanometer-size self-assembled monolayers with controlled orientations. A direct-write micro- or nanolithog. method for depositing a functional material with a preferred orientation onto a target surface. The method includes the steps of (1) forming a precursor fluid to the functional material; (2) operating a submicrometer tip to discharge, on contact, the precursor fluid onto the target surface so as to produce a desired pattern of deposited functional material in sub-micrometer dimensions; and (3) during the pattern-producing step, subjecting the deposited material to a highly localized elec. or magnetic field for attaining a preferred orientation in at least a portion of the functional material. The method is particularly useful for microfabrication, nanotechnol., and mol. electronics.

IC ICM G03F007-16

INCL 430315000; 430935000

CC 76-14 (Electric Phenomena)

Section cross-reference(s): 48, 74, 77

IT Thiols, processes

RL: PEP (Physical, engineering or chemical process); PYP (Physical process); TEM (Technical or engineered material use); PROC (Process); USES (Uses)

(axy1; field-assisted micro-fabrication and nano-fabrication method)

IT Antiferromagnetic materials

Conducting polymers

Controlled atmospheres

Electric field effects

Electronic device fabrication

Ferrimagnetic materials Ferroelectric materials

Ferromagnetic materials

Fluids

Liquid crystals

Lithography

Magnetic field effects

Molecular electronic devices

Nanomachines

Nonlinear optical materials

Nozzles

Optical fibers

Piezoelectric materials

Pyroelectric substances

Self-assembled monolayers

Vacuum

(field-assisted micro-fabrication and nano-fabrication method)

OS.CITING REF COUNT: 1 THERE ARE 1 CAPLUS RECORDS THAT CITE THIS RECORD (1 CITINGS) L47 ANSWER 3 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2005:945241 HCAPLUS Full-text DOCUMENT NUMBER: 143:346764 TITLE: Spatially Resolved Suzuki Coupling Reaction Initiated and Controlled Using a Catalytic AFM Probe Davis, Jason J.; Coleman, Karl S.; Busuttil, Katerina AUTHOR(S): L.; Bagshaw, Claire B. CORPORATE SOURCE: Inorganic Chemistry Department Central Research Laboratory, Oxford University, Oxford, OX1 3TA, UK SOURCE: Journal of the American Chemical Society (2005), 127(38), 13082-13083 CODEN: JACSAT; ISSN: 0002-7863 PUBLISHER: American Chemical Society DOCUMENT TYPE: Journal LANGUAGE: English CASREACT 143:346764 OTHER SOURCE(S): Appropriately modified proximal probes can be utilized in the spatially resolved chemical coupling of surface-bound and solution-phase reagents. Herein we report a chemical specific Suzuki coupling reaction between a surface-confined axyl bromide and boronic acid reagents in solution achieved using a catalytic AFM probe. 22-13 (Physical Organic Chemistry) CC Section cross-reference(s): 66, 67 Lithography ΙT (scanning probe; spatially resolved Suzuki coupling reaction initiated and controlled using a catalytic AFM probe) Self-assembled monolayers ΙT Surface reaction Suzuki coupling reaction Suzuki coupling reaction catalysts (spatially resolved Suzuki coupling reaction initiated and controlled using a catalytic AFM probe) 866006-10-2P ΤТ RL: CPS (Chemical process); PEP (Physical, engineering or chemical process); PRP (Properties); RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); PROC (Process); RACT (Reactant or reagent) (preparation, characterization, and Suzuki coupling reaction as \$₩1£ -assembled monolayer on gold; spatially resolved Suzuki coupling reaction initiated and controlled using a catalytic AFM probe) OS.CITING REF COUNT: 10 THERE ARE 10 CAPLUS RECORDS THAT CITE THIS RECORD (10 CITINGS) THERE ARE 35 CITED REFERENCES AVAILABLE FOR THIS REFERENCE COUNT: 35 RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT L47 ANSWER 4 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2005:189321 HCAPLUS Full-text TITLE: Patterned reduction of aryl-azide terminated self-assembled monolayers photocatalyzed by CdS or CdSe quantum dots AUTHOR(S): Radhakrishnan, Chander; Lo, Michael K. F.; Garcia-Garibay, Miguel; Monbouquette, Harold CORPORATE SOURCE: Department of Chemical Engineering, University of California, Los Angeles, Los Angeles, CA, 90095-1592, SOURCE: Abstracts of Papers, 229th ACS National Meeting, San

Diego, CA, United States, March 13-17, 2005 (2005),

COLL-621. American Chemical Society: Washington, D.

С.

CODEN: 69GOMP

DOCUMENT TYPE: Conference; Meeting Abstract

LANGUAGE: English

We recently reported that thiolamine-capped CdS and CdSe quantum dots (Qdots) effectively photocatalyze the reduction of <code>sryl</code> azides to <code>sryl</code> amines in solution The corresponding surface reaction also has been demonstrated using <code>sryl-azide</code> terminated <code>self-assembled monolayers</code> (SAMs) on evaporated gold. The SAMs were characterized fully, before and after photocatalysis, by XPS, contact angle measurements and FTIR. The Qdots adsorb strongly to the <code>sryl-azide</code> terminated SAMs, which facilitates the photocatalyzed reaction. However, subsequent Qdot desorption from the SAM could not be accomplished by sonication in solns. at high or low <code>ph</code>, or at high salt concentration (2M KCl), which suggests that something other than a charge-dipole interaction governs Qdot adsorption. Interestingly, 6M guanidineHCl treatment effected removal of adsorbed Qdots. Reversible Qdot adsorption to <code>sryl-azide SAMs</code> before and after photocatalysis enabled the creation of <code>surface patterns</code> observable with a fluorescence microscope.

L47 ANSWER 5 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2005:348430 HCAPLUS Full-text

DOCUMENT NUMBER: 144:157459

TITLE: Mapping molecular orientation of pentacene on

patterned Au surface

AUTHOR(S): Hsu, Y. J.; Hu, W. S.; Wei, D. H.; Wu, Y. S.; Tao, Y.

Τ.

CORPORATE SOURCE: National Synchrotron Radiation Research Center,

Hsinchu, 30076, Taiwan

SOURCE: Journal of Electron Spectroscopy and Related Phenomena

(2005), 144-147, 401-404

CODEN: JESRAW; ISSN: 0368-2048

PUBLISHER: Elsevier B.V.

DOCUMENT TYPE: Journal LANGUAGE: English

With a photoemission electron microscope, the authors studied the orientation of pentacene films deposited on Au surface that was patterned with self-assembled monolayers (SAMs). Organic thiols X(CH2)nSH- with X = -COOH or -Me and an aromatic thiol; served as alignment layers to control the orientation of pentacene mols. thermally deposited on top of the SAM. According to the PEEM images and near-edge x-ray absorption fine structure spectra, a SAM exposing a nonpolar Me group, a terphenyl group or a polar carboxyl group all induced perpendicular alignment of the pentacene moiety, in contrast with parallel alignment on a bare Au surface.

CC 66-3 (Surface Chemistry and Colloids)

ST pentacene orientation thiol self assembled

monolayer patterned gold surface

IT Thiols, properties

RL: PRP (Properties)

(aryl; mapping mol. orientation of pentacene on Au surface patterned with thiol self-

assembled monolayers using photoemission electron

microscopy and NEXAFS spectra)

IT Molecular orientation

NEXAFS spectra

Self-assembled monolayers

(mapping mol. orientation of pentacene on Au surface

patterned with thiol self-assembled

monolayers using photoemission electron microscopy and NEXAFS

spectra) ΙT Thiols, properties RL: PRP (Properties) (mapping mol. orientation of pentacene on Au surface patterned with thiol self-assembled monolayers using photoemission electron microscopy and NEXAFS spectra) Phenols, properties ΤТ RL: PRP (Properties) (thiophenols; mapping mol. orientation of pentacene on Au surface patterned with thiol selfassembled monolayers using photoemission electron microscopy and NEXAFS spectra) 135-48-8, Pentacene 7440-57-5, Gold, properties 78540-82-6, ТТ [1,1':4',1''-Temphenyl]-4-methanethiol RL: PRP (Properties) (mapping mol. orientation of pentacene on Au surface patterned with thiol self-assembled monolayers using photoemission electron microscopy and NEXAFS spectra) OS.CITING REF COUNT: 2 THERE ARE 2 CAPLUS RECORDS THAT CITE THIS RECORD (2 CITINGS) REFERENCE COUNT: 12 THERE ARE 12 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT L47 ANSWER 6 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN 2004:81557 HCAPLUS Full-text ACCESSION NUMBER: DOCUMENT NUMBER: 140:287126 TITLE: Synthesis, structural analysis, and self-assembly of phenylene ethynylene oligomers and their -F, -CF3, and -CH3 substituted derivatives AUTHOR(S): Percec, Simona; Getty, Ross; Marshall, Will; Skidd, Gabriel; French, Roger Experimental Station, Central Research and CORPORATE SOURCE: Development, E. I. Du Pont de Nemours and Co., Wilmington, DE, 19880, USA SOURCE: Journal of Polymer Science, Part A: Polymer Chemistry (2004), 42(3), 541-550CODEN: JPACEC; ISSN: 0887-624X PUBLISHER: John Wiley & Sons, Inc. DOCUMENT TYPE: Journal LANGUAGE: English OTHER SOURCE(S): CASREACT 140:287126 4-(2-Arylethynyl)-1-(acetylthio) benzenes 4-(RC.tplbond.C)C6H4SCOCH3 (I) (R = Ph, 4-H3CC6H4, 4-FC6H4, 2-FC6H4, 4-F3CC6H4, 3-F3CC6H4) are prepared as electrochem. active mols. for incorporation into self- assembled monolayers (SAMs). 4-BrC6H4SCOCH3 and 4-IC6H4SCOCH3 are prepared from 4bromobenzenethiol and 4-iodobenzenesulfonyl chloride, resp.; Sonogashira coupling of either 4-BrC6H4SCOCH3 or 4-IC6H4SCOCH3 to aryl alkynes in the presence of bis(dibenzylideneacetone)palladium, copper iodide, triphenylphosphine, and triethylamine yields the desired compds. I. are prepared; the advancing and receding contact angles, monolayer thicknesses, and the differences in surface potential of the SAMs (vs. bare gold) are determined The structures of I are determined by X-ray crystallog. to understand the properties of SAMs containing I. Unsym. substitution of the aromatic rings by electron-active groups in the ortho-, meta-, or para

positions results in changes in mol. parameters such as bonding and torsion angles and planarity. Patterned SAMS of I (R = Ph, 4-FC6H4) on gold are prepared by microcontact printing; the surface potentials of the monolayers differed only slightly from that of a bare gold substrate. Unpatterned SAMS

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of I (R = 4-H3CC6H4, 2-FC6H4, 4-F3CC6H4, 3-F3CC6H4) are formed upon incubation
     of gold substrates with solns. of the thioesters.
     25-7 (Benzene, Its Derivatives, and Condensed Benzenoid Compounds)
     Section cross-reference(s): 66, 75
ST
     arylethynylacetylthiobenzene prepn crystal structure; arylethynyl
     acetylthio benzene prepn crystal structure; phenylene ethynylene oligomer
     prepn crystal structure self assembled
     monolayer; contact angle thickness surface potential
     arylethynylacetylthiobenzene SAM; mol crystal structure
     arylethynylacetylthiobenzene; surface potential
     patterned unpatterned SAM arylethynylacetylthiobenzene
     Coupling reaction
ΙT
        (Sonogashira; preparation and crystal structures of
        (arylethynyl) (acetylthio) benzenes by Sonogashira coupling of
        aryl alkynes and 4-bromo- and 4-iodobenzene thioacetates and
        the properties of arylalkynylbenzenethiol self-
        assembled monolayers)
     Aromatic hydrocarbons, preparation
ΤТ
     RL: PRP (Properties); RCT (Reactant); SPN (Synthetic preparation); PREP
     (Preparation); RACT (Reactant or reagent)
        (axyl alkynes; preparation and crystal structures of
        (arylethynyl) (acetylthio) benzenes by Sonogashira coupling of
        aryl alkynes and 4-bromo- and 4-iodobenzene thioacetates and
        the properties of arylalkynylbenzenethiol self-
        assembled monolayers)
ΙT
     Thiols, preparation
     RL: PRP (Properties); SPN (Synthetic preparation); PREP (Preparation)
        (axyl, S-acetyl; preparation and crystal structures of
        (arylethynyl) (acetylthio) benzenes by Sonogashira coupling of
        aryl alkynes and 4-bromo- and 4-iodobenzene thioacetates and
        the properties of arylalkynylbenzenethiol self-
        assembled monolayers)
ΙT
    Alkynes
     RL: PRP (Properties); RCT (Reactant); SPN (Synthetic preparation); PREP
     (Preparation); RACT (Reactant or reagent)
        (axy1; preparation and crystal structures of
        (arylethynyl) (acetylthio) benzenes by Sonogashira coupling of
        axyl alkynes and 4-bromo- and 4-iodobenzene thioacetates and
        the properties of anylalkynylbenzenethiol self-
        assembled monolayers)
    Contact angle
ΙT
     Ellipsometry
       Self-assembled monolayers
     Surface potential
        (preparation and crystal structures of (arylethynyl) (acetylthio) benzenes by
        Sonogashira coupling of aryl alkynes and 4-bromo- and
        4-iodobenzene thioacetates and the properties of
        arylalkynylbenzenethiol self-assembled
        monolayers)
ΙT
     Phenols, preparation
     RL: PRP (Properties); SPN (Synthetic preparation); PREP (Preparation)
        (thiophenols, S-acetyl; preparation and crystal structures of
        (arylethynyl) (acetylthio) benzenes by Sonogashira coupling of
        aryl alkynes and 4-bromo- and 4-iodobenzene thioacetates and
        the properties of arylalkynylbenzenethiol self-
        assembled monolayers)
                    676094-68-1P 676094-69-2P 676094-70-5P 676094-71-6P
ΙT
     170159-16-7P
     676094-72-7P
     RL: PRP (Properties); SPN (Synthetic preparation); PREP (Preparation)
        (preparation and crystal structures of (arylethynyl) (acetylthio) benzenes by
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Sonogashira coupling of aryl alkynes and 4-bromo- and
4-iodobenzene thioacetates and the properties of
arylalkynylbenzenethiol self-assembled
monolayers)
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ΙT 98-61-3, 4-Iodobenzenesulfonyl chloride 106-53-6, 4-Bromobenzenethiol 536-74-3, Phenylacetylene 705-28-2, 3-(Trifluoromethyl)phenylacetylene 705-31-7, 4-(Trifluoromethyl)phenylacetylene 766-49-4, (2-Fluorophenyl)acetylene 766-97-2, 4-Methylphenylacetylene 4-Fluorophenylacetylene

RL: RCT (Reactant); RACT (Reactant or reagent)

(preparation and crystal structures of (arylethynyl) (acetylthio) benzenes by Sonogashira coupling of aryl alkynes and 4-bromo- and 4-iodobenzene thioacetates and the properties of arylalkynylbenzenethiol self-assembled

monolayers)

ΙT 28122-76-1P 52928-01-5P, 4-Iodobenzenethiol 69746-43-6P RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)

> (preparation and crystal structures of (arylethynyl) (acetylthio) benzenes by Sonogashira coupling of axyl alkynes and 4-bromo- and 4-iodobenzene thioacetates and the properties of arylalkynylbenzenethiol self-assembled

monolayers)

OS.CITING REF COUNT: THERE ARE 4 CAPLUS RECORDS THAT CITE THIS RECORD

(4 CITINGS)

THERE ARE 18 CITED REFERENCES AVAILABLE FOR THIS REFERENCE COUNT: 18

RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L47 ANSWER 7 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2003:445956 HCAPLUS Full-text

DOCUMENT NUMBER: 139:297398

On the re-oxidation of silicon(0 0 1) surfaces TITLE:

modified by self-assembled

monolayers

Narducci, Dario; Pedemonte, Laura; Bracco, Gianangelo AUTHOR(S):

CORPORATE SOURCE: Istituto Nazionale per la Fisica della Materia,

Department of Materials Science, University of Milano

Bicocca, Milan, Italy

Applied Surface Science (2003), 212-213, 649-653 SOURCE:

CODEN: ASUSEE; ISSN: 0169-4332

Elsevier Science B.V. PUBLISHER:

DOCUMENT TYPE: Journal LANGUAGE: Enalish

Protection of Si surface toward oxidation represents a relevant issue in view of many microelectronic applications. In 2000, it was shown how mol. grafting with Me groups could efficiently passivate atomically flat Si(1 1 1). However, neither data are currently available on (0 0 1) surfaces nor systematic analyses of the role played by the organic fragment on the protection efficiency were reported yet. The aim of this paper is to present data on the passivation of (0 0 1) Si surface by different axyl fragments self-assembled onto it. Protection was carried out using nucleophilic organic species that were self-assembled on a previously brominated Si surface. Specifically, 5 differently substituted Ph groups were considered. These samples were characterized by specular reflection IR spectroscopy to detect the presence of axyl -terminating groups. The kinetics of the re-oxidation reaction was then monitored over a time period of 2 mo. We found qual. different mechanisms of re-oxidation, depending on the structure of the organic fragment. The first mechanism is compatible with a model where the aryl group simply hinders the surface Si sites, disabling the access of

oxidizing species to the surface itself. The second process appears to be more complex, with the axyl group interacting with the oxidizing species.

CC 66-3 (Surface Chemistry and Colloids)

ST silicon surface oxidn passivation self assembled monolayer

IT Passivation

Self-assembled monolayers

(re-oxidation of Si(0 0 1) surfaces modified by

self-assembled monolayers)

IT Oxidation

(surface; re-oxidation of Si(0 0 1) surfaces modified

by self-assembled monolayers)

IT 7440-21-3, Silicon, properties

RL: CPS (Chemical process); PEP (Physical, engineering or chemical

process); PRP (Properties); PROC (Process)

(re-oxidation of  $Si(0\ 0\ 1)$  surfaces modified by

self-assembled monolayers)

IT 71-43-2, Benzene, uses 85-01-8, Phenanthrene, uses 100-66-3, Anisole, uses 121-69-7, N,N-Dimethylaniline, uses 462-06-6, Fluorobenzene

RL: MOA (Modifier or additive use); USES (Uses)

(re-oxidation of Si(0 0 1) surfaces modified by self-assembled monolayers)

REFERENCE COUNT: 9 THERE ARE 9 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L47 ANSWER 8 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2003:445928 HCAPLUS Full-text

DOCUMENT NUMBER: 139:203083

TITLE: Investigation of gas-surface interactions at

self-assembled silicon surfaces acting as gas sensors

AUTHOR(S): Narducci, Dario; Bernardinello, Patrizia; Oldani,

Matteo

CORPORATE SOURCE: Istituto Nazionale per la Fisica della Materia and

Department of Materials Science, University of Milano

Bicocca, Milan, 20125, Italy

SOURCE: Applied Surface Science (2003), 212-213, 491-496

CODEN: ASUSEE; ISSN: 0169-4332

PUBLISHER: Elsevier Science B.V.

DOCUMENT TYPE: Journal LANGUAGE: English

This paper reports the results of an investigation aimed at using salf-AB assembled monolayers to modify the supramol. interactions between Si surfaces and gaseous mols. The specific goal is that of employing molecularly imprinted Si surfaces to develop a new class of chemical sensors capable to detect species with enhanced selectivity. Single-crystal p-type (0 0 1) Si was modified by grafting organic mols. onto its surface by wet chemical synthetic methods. Si was activated toward nucleophilic attack by brominating its surface using a modified version of the purple etch, and aromatic fragments were bonded through the formation of direct Si-C bonds onto it using Grignard reagents or Li axyl species. Formation of self -assembled monolayers (SAMs) was verified by using vibrational spectroscopy. Porous metal-SAM-Si diodes were successfully tested as resistive chemical sensors toward NOx, SOx, CO, NH3 and methane. Current-voltage characteristics measured at different gas compns. showed that the mechanism of surface electron d. modulation involves a modification of the junction barrier height upon gas adsorption. Quantum-mech. simulations of the interaction mechanism were carried out using different computational methods to support such an interaction mechanism. results obtained appear to open up new relevant applications of the SAM techniques in the area of gas sensing.

CC 66-3 (Surface Chemistry and Colloids)

Section cross-reference(s): 79

ST silicon surface self assembled monolayer

ammonia gas sensor

Bromination ΤT

Electric current-potential relationship

Gas sensors

Grignard reaction

Self-assembled monolayers

(gas-surface interactions at self-assembled Si surfaces acting as NH3

gas sensors)

591-51-5, Phenyl lithium 7353-91-5 13139-86-1 ΤТ 586346-16-9

RL: RCT (Reactant); RACT (Reactant or reagent)

(gas-surface interactions at self-assembled Si surfaces acting as NH3

gas sensors)

OS.CITING REF COUNT: THERE ARE 4 CAPLUS RECORDS THAT CITE THIS RECORD

(4 CITINGS)

REFERENCE COUNT: 6 THERE ARE 6 CITED REFERENCES AVAILABLE FOR THIS

RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L47 ANSWER 9 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN

2002:650130 HCAPLUS Full-text ACCESSION NUMBER:

DOCUMENT NUMBER: 137:201150

Preparation of mercaptoalkanoic acid p-phenylazophenyl TITLE:

esters and self-assembled monomolecular film and its

production method

Iwayama, Masami; Fujinami, Tatsuo; Tanaka, Masato INVENTOR(S):

Star Mfg. Co., Japan PATENT ASSIGNEE(S):

SOURCE: Jpn. Kokai Tokkyo Koho, 8 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002241734	A	20020828	JP 2001-43802	20010220
PRIORITY APPLN. INFO.:			JP 2001-43802	20010220
OTHER SOURCE(S):	MARPAT	137:201150		

GI

$$HS - R1 - CO_2$$
  $N = N$   $I$ 

A self-assembled monolayer (SAM) of an azobenzene derivative is provided, AB which prevents the decrease of the free space due to the aggregation of the self-assembling compound and thereby maintains the free space so that the azobenzene unit is able to isomerize and efficiently and uniformly changes the surface property. A self-assembled monolayer is formed by adsorbing azobenzene derivs. [I; R1 = C3-21 alkylene; X = OH, linear or branched C1-22alkyl, C1-22 acyloxy, C1-22 fluoroalkyl, C1-21 alkoxy, aliphatic carboxylic acid reside, (un) substituted axyl] on a substrate. Thus, diazotization of 4pentylaniline with NaNO2 in aqueous HCl followed by coupling with phenol gave 4-(4-pentylphenylazo)phenol which was esterified by 11-mercaptoundecanoic acid using DCC in the presence of 4-dimethylaminopyridine in CH2Cl2 at room

temperature for 24 h to give 11-mercaptoundecanoic acid 4-(4-pentylphenylazo)phenyi ester. A glass substrate sequentially vapor-deposited with chrome film (5 nm) and gold film (200 nm) was immersed in a 1 mM solution of the thiol I in ethanol for 48 h, taken out from the solution, and the surface was washed with ethanol to thoroughly remove the excess thiol to give a SAM-modified surface. The SAM-modified surface was irradiated by visible light (300-400 nm) and UV light (300-400 nm) using a 200-W mercury-xenon lamp. The change in the contact angle before and after light-irradiation confirmed cis-trans photoisomerization of I, i.e. isomerization from trans to cis isomer by UV light and that from cis to trans by visible light.

IC ICM C09K003-00

ICS C09K003-00; C07C323-52; C09K003-18

CC 25-18 (Benzene, Its Derivatives, and Condensed Benzenoid Compounds) Section cross-reference(s): 22, 66

ST mercaptoalkanoic acid phenylazophenyl ester prepn self assembled monomol film; azobenzene self assembled monolayer cis trans photoisomerization

IT 452304-37-9P, 11-Mercaptoundecanoic acid 4-(4-pentylphenylazo)

phenyl ester 452304-38-0P 452304-39-1P

RL: CPS (Chemical process); PEP (Physical, engineering or chemical process); PRP (Properties); PYP (Physical process); SPN (Synthetic preparation); PREP (Preparation); PROC (Process)

(preparation of mercaptoalkanoic acid p-phenylazophenyl esters, self-assembly monomol. film on substrate, its production method, and cis-trans photoisomerization)

L47 ANSWER 10 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2001:749739 HCAPLUS  $\underline{\text{Full-text}}$ 

DOCUMENT NUMBER: 136:45544

TITLE: Axyl Ketone Photochemistry on Monolayer

Protected Clusters: Study of the Norrish Type II Reaction as a Probe of Conformational Mobility and for

Selective Surface Modification

AUTHOR(S): Kell, Arnold J.; Workentin, Mark S.

CORPORATE SOURCE: Department of Chemistry, The University of Western

Ontario, London, ON, N6A 5B7, Can. Langmuir (2001), 17(23), 7355-7363 CODEN: LANGD5; ISSN: 0743-7463

PUBLISHER: American Chemical Society

DOCUMENT TYPE: Journal LANGUAGE: English

SOURCE:

A series of axyl ketones, namely, 11-mercapto-1-phanyl -undecanone (1), 1-(4-AR hexyl-phenyl)-11-mercaptoundecanone (2), 1-(4-dodecyl-phenyl)-11mercaptoundecanone (3), 1-[4-(11-mercaptoundecyl)phenyl]hexanone (4), and 1-[4-(11-mercaptoundecyl)phanyl]undecanone (5), anchored as mixed monolayers with one of hexanethiolate, dodecanethiolate, and octadecanethiolate on gold nanoclusters (so-called monolayer-protected clusters, MPCs) were prepared and characterized. The Norrish-Yang type II photoreactivity of these MPCs was investigated in benzene solution to serve as probes of conformational mobility within the monolayer environment. The axyl ketones react efficiently by a Norrish type II reaction (>75% completion) through their triplet excited state to yield a 1,4-biradical that fragments to give the corresponding alkene and substituted acetophenone-modified MPCs for 1-3 and 4 and 5, resp. The extent of reaction and the efficiency do not appear to depend on the length of the alkanethiolate co-adsorbed onto the MPC or on whether the aryl ketone is further embedded into the monolayer. Notably, there was no evidence for the generation of cyclobutanol products that would be generated from cyclization of the 1,4-biradical or other competing photochem. reactions. The findings of this investigation suggest that the MPC environment is quite dynamic; yet, the exclusive fragmentation products indicate that there are some factors

affecting the conformational mobility of the triplet biradical. The authors further suggest that the reactivity in MPCs may be greatest at the edge/vertexes with larger constraints on the terraces. Regardless, the Norrish type II reactivity yields efficient fragmentation of either acetophenone or alkene moiety, suggesting such MPCs could find use for the controlled release of substrates in solution

- CC 74-1 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
- ST aryl ketone photolysis monolayer protected gold cluster; Norrish Yang photoreactivity aryl ketone monolayer gold nanocluster; photoreaction mercaptophenyl aryl ketone triplet state monolayer gold nanocluster
- IT Adsorbed monolayers

Conformation

Norrish type II reaction

Photolysis

Self-assembled monolayers

Triplet state transition

(Norrish-Yang type II photoreactivity via excited triplet state of aryl ketones anchored as mixed monolayers with arylthiolate on gold nanoclusters)

- IT Biradicals
  - RL: CPS (Chemical process); PEP (Physical, engineering or chemical process); PROC (Process)

(Norrish-Yang type II photoreactivity via excited triplet state of axyl ketones anchored as mixed monolayers with arylthicate on gold nanoclusters)

- IT Clusters
  - RL: NUU (Other use, unclassified); USES (Uses)

    (metal, monolayer-protected; Norrish-Yang type II photoreactivity via excited triplet state of aryl ketones anchored as mixed monolayers with arylthiolate on gold nanoclusters)
- IT 304435-86-7DP, 11-Mercapto-1-phenyl-undecanone, gold cluster-bound 380436-07-7DP, 1-(4-Hexyl-phenyl
  - )-11-mercaptoundecanone, gold cluster-bound 380436-08-8DP, 1-(4-Dodecyl-phenyl)-11-mercaptoundecanone, gold cluster-bound 380436-09-9DP, 1-[4-(11-Mercaptoundecyl)phenyl]hexanone, gold cluster-bound 380436-10-2DP, 1-[4-(11-Mercaptoundecyl)phenyl]undecanone, gold cluster-bound
  - RL: CPS (Chemical process); PEP (Physical, engineering or chemical process); PNU (Preparation, unclassified); PRP (Properties); PYP (Physical process); PREP (Preparation); PROC (Process)

(Norrish-Yang type II photoreactivity via excited triplet state of  $\mathtt{ary1}$  ketones anchored as mixed monolayers with arylthiclate on gold nanoclusters)

IT 1322-36-7D, Dodecanethiol, gold cluster-bound 2885-00-9D, Octadecanethiol, gold cluster-bound 7440-57-5D, Gold, clusters 142041-95-0D, Hexanethiolate, gold cluster-bound RL: NUU (Other use, unclassified); USES (Uses)

(Norrish-Yang type II photoreactivity via excited triplet state of axy1 ketones anchored as mixed monolayers with arylthicate on gold nanoclusters)

IT 98-86-2, properties 106-98-9, 1-Butene, properties 124-11-8, 1-Nonene 6313-88-8 37592-72-6 304435-87-8D, 8-Nonene-1-thiol, gold cluster-bound 380436-11-3D, gold cluster-bound RL: CPS (Chemical process); FMU (Formation, unclassified); PEP (Physical, engineering or chemical process); PRP (Properties); FORM (Formation, nonpreparative); PROC (Process)

(photoproduct; Norrish-Yang type II photoreactivity via excited triplet state of axyl ketones anchored as mixed monolayers with

11/594654 arylthiolate on gold nanoclusters) OS.CITING REF COUNT: 16 THERE ARE 16 CAPLUS RECORDS THAT CITE THIS RECORD (16 CITINGS) REFERENCE COUNT: 43 THERE ARE 43 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT L47 ANSWER 11 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 1999:629621 HCAPLUS Full-text DOCUMENT NUMBER: 131:356573 TITLE: Ion-Ion Collisions Leading to Formation of C-C Bonds at Surfaces: An Interfacial Kolbe Reaction Shen, Jianwei; Evans, Chris; Wade, Nathan; Cooks, R. AUTHOR(S): Graham Department of Chemistry, Purdue University, West CORPORATE SOURCE: Lafayette, IN, 47906, USA SOURCE: Journal of the American Chemical Society (1999), 121(41), 9762-9763 CODEN: JACSAT; ISSN: 0002-7863 PUBLISHER: American Chemical Society DOCUMENT TYPE: Journal LANGUAGE: English An 11-mercaptoundecanoic acid SAM surface treated with ammonium hydroxide to convert the acid to the ammonium salt, was bombarded with gas-phase phenylium and halophenylium cations at 12 eV, while a scattered ion mass spectra recorded on collision of 65 eV Xe+• ion beam was used to monitor surface composition before and chemical modification. A new surface modification method, in the form of direct, reactive incorporation of mol. groups into surfaces , has been demonstrated in this study. CC 66-4 (Surface Chemistry and Colloids) ΙT Bond formation (carbon-carbon, interfacial Kolbe's electrochem. reaction; interfacial Kolbe's reaction of axyl cations with ammonium 11-mercaptoundecanoate SAM on gold) Ionic collisions ΙT Self-assembled monolayers (interfacial Kolbe's reaction of axyl cations with ammonium 11-mercaptoundecanoate SAM on gold) Kolbe's electrochemical reaction ΙT (interfacial; interfacial Kolbe's reaction of aryl cations with ammonium 11-mercaptoundecanoate SAM on gold) 250339-43-6D, SAM on gold ΙT RL: PEP (Physical, engineering or chemical process); RCT (Reactant); PROC (Process); RACT (Reactant or reagent) (interfacial Kolbe's reaction of axyl cations with ammonium 11-mercaptoundecanoate SAM on gold) 17333-73-2, Phenylium 64461-40-1 250349-04-3 250349-06-5 ΤТ

RL: RCT (Reactant); RACT (Reactant or reagent)

(interfacial Kolbe's reaction of axyl cations with ammonium

11-mercaptoundecanoate SAM on gold)

OS.CITING REF COUNT: 17 THERE ARE 17 CAPLUS RECORDS THAT CITE THIS

RECORD (17 CITINGS)

REFERENCE COUNT: 24 THERE ARE 24 CITED REFERENCES AVAILABLE FOR THIS

RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L47 ANSWER 12 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 1998:28083 HCAPLUS Full-text

DOCUMENT NUMBER: 128:185950

ORIGINAL REFERENCE NO.: 128:36631a,36634a

TITLE: Surface-Enhanced Raman Imaging (SERI) of Patterned

Self-Assembled Monolayers

```
of Various Derivatized Thiophenols on Silver
AUTHOR(S):
                         Tryk, Donald A.; Yang, Xiaomin; Hashimoto, Kazuhito;
                         Fujishima, Akira
CORPORATE SOURCE:
                         The University of Tokyo, 7-3-1 Hongo, Bunkyo-ku,
                         Tokyo, 113, Japan
SOURCE:
                         Bulletin of the Chemical Society of Japan (1998),
                         71(1), 31-39
                         CODEN: BCSJA8; ISSN: 0009-2673
PUBLISHER:
                         Chemical Society of Japan
DOCUMENT TYPE:
                         Journal
LANGUAGE:
                         English
     Surface-enhanced Raman imaging (SERI) has recently been developed in the
AB
     authors' laboratory as an imaging technique which is chemical selective, has
     monolayer sensitivity, and can be used under ambient conditions. A
     particularly interesting application of this technique is to image patterned
     self-assembled monolayers ( SAMs). The authors used both photopatterning and
     microcontact printing techniques for preparing patterned SAMS with several
     different terminal functional groups (NO2, OH, COOH, and CH3) on evaporated Ag
     films and have imaged them using SERI. The intrinsic subsurface roughness of
     the film provides sufficient enhancement for the imaging.
CC
     73-3 (Optical, Electron, and Mass Spectroscopy and Other Related
     Properties)
     Section cross-reference(s): 66, 74
     Thiols (organic), properties
ΤT
     Thiols (organic), properties
     RL: PEP (Physical, engineering or chemical process); PRP (Properties);
     PROC (Process)
        (axyl; surface-enhanced Raman imaging (SERI) of patterned
        self-assembled monolayers of various
        derivatized thiophenols on silver)
ΙT
     Imaging
        (surface enhanced Raman; surface-enhanced Raman imaging (SERI) of
        patterned self-assembled monolayers of
        various derivatized thiophenols on silver)
ΙT
    Carboxyl group
     Functional groups
     Hydroxyl group
     Instrumentation
     Methyl group
     Nitro group
     Photolysis
     Surface roughness
        (surface-enhanced Raman imaging (SERI) of patterned self-
        assembled monolayers of various derivatized
        thiophenols on silver)
     Phenols, properties
ΤТ
     Phenols, properties
     RL: PEP (Physical, engineering or chemical process); PRP (Properties);
     PROC (Process)
        (thiophenols; surface-enhanced Raman imaging (SERI) of patterned
        self-assembled monolayers of various
        derivatized thiophenols on silver)
     7440-50-8, Copper, uses
ΤТ
     RL: NUU (Other use, unclassified); USES (Uses)
        (grid; surface-enhanced Raman imaging (SERI) of patterned self
        -assembled monolayers of various derivatized
        thiophenols on silver)
     7440-47-3, Chromium, uses
ΙT
     RL: NUU (Other use, unclassified); USES (Uses)
        (lithog. mask; surface-enhanced Raman imaging (SERI) of
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patterned self-assembled monolayers of

various derivatized thiophenols on silver)

ΙT 50926-11-9, Indium tin oxide

RL: NUU (Other use, unclassified); USES (Uses)

(surface-enhanced Raman imaging (SERI) of patterned self-

assembled monolayers of various derivatized

thiophenols on silver)

637-89-8, p-Hydroxythiophenol 1073-72-9, p-Methylthiophenol 1074-36-8, ΤТ 4-Carboxy thiophenol 1849-36-1, p-Nitrothiophenol 7440-22-4, Silver, properties

RL: PEP (Physical, engineering or chemical process); PRP (Properties); PROC (Process)

(surface-enhanced Raman imaging (SERI) of patterned selfassembled monolayers of various derivatized

thiophenols on silver)

OS.CITING REF COUNT: 7 THERE ARE 7 CAPLUS RECORDS THAT CITE THIS RECORD

(7 CITINGS)

REFERENCE COUNT: 72 THERE ARE 72 CITED REFERENCES AVAILABLE FOR THIS

RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L47 ANSWER 13 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN 1999:370936 HCAPLUS Full-text ACCESSION NUMBER:

DOCUMENT NUMBER: 131:136667

TITLE: Photopatterning to create new structures on surfaces

Fox, M. A.; Wolf, M. O.; Stewart, G. M. AUTHOR(S):

Department of Chemistry and Biochemistry, University CORPORATE SOURCE:

of Texas at Austin, Austin, TX, 78712, USA

NATO ASI Series, Series C: Mathematical and Physical SOURCE:

Sciences (1997), 499 (Modular Chemistry), 53-67

CODEN: NSCSDW; ISSN: 0258-2023

PUBLISHER: Kluwer Academic Publishers

DOCUMENT TYPE: Journal LANGUAGE: English

UV irradiation of self-assembled monolayers of cis- and trans-4-cyano-4'-(10thiodecoxy) stilbene on a polycryst. gold surface results in visual surface patterning as a consequence of pronounced changes in the surface hydrophobicity induced by photochem. geometric isomerization. The metal surface influences the efficiency of the photoconversion but does not completely quench excited state reactivity. A novel series of dendrimer segments bearing functionalized axyl chromophores (such as pyrene and naphthalene) at the periphery has been synthesized using a convergent-growth methodol. Selective excitation of the naphthyl -substituted dendrons shows no intramol. excimer formation, although substantial excimer emission is observed with the pyrenyl substituted dendrons. Fluorescence quantum yields are used to define energy migration through the dendritic backbone.

CC 74-1 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

ΙT Fluorescence

(of dendrimer segments bearing functionalized aryl

chromophores in study of intramol. excimer formation)

REFERENCE COUNT: 21 THERE ARE 21 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L47 ANSWER 14 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 1995:654664 HCAPLUS Full-text

DOCUMENT NUMBER: 123:241688

ORIGINAL REFERENCE NO.: 123:42939a,42942a

High Lateral Resolution Imaging by Secondary Ion Mass TITLE:

> Spectrometry of Photopatterned Self-Assembled Monolayers Containing

Arvl Azide

AUTHOR(S): Frisbie, C. Daniel; Wollman, Eric W.; Wrighton, Mark

S.

CORPORATE SOURCE: Department of Chemistry, Massachusetts Institute of

Technology, Cambridge, MA, 02139, USA

SOURCE: Langmuir (1995), 11(7), 2563-71

CODEN: LANGD5; ISSN: 0743-7463

PUBLISHER: American Chemical Society

DOCUMENT TYPE: Journal LANGUAGE: English

Imaging secondary ion mass spectrometry (SIMS) is used to map the distribution AB of mol. and elemental species in a patterned self- assembled monolayer (SAM) with 1  $\mu m$  lateral resolution. The patterned SAMs are made by exposing polycryst. Au to a solution of bis(11-(4-azido(benzoyloxy))-1-undecyl) disulfide, I, which forms a photosensitive SAM (Au-I) on the Au. Subsequent UV irradiation ( $\lambda > 260$  nm) of Au-I SAMs through a mask and a thin film of a secondary amine results in attachment of the amine to the Au-I SAM only in the irradiated regions. The Au-I SAM is photosensitive by virtue of a pendant aryl azide group which reacts with secondary amines under UV irradiation to form hydrazine or azepine photoadducts. A large mol. fragment ion corresponding to vinylferrocene (m/z 212) was mapped with 1  $\mu m$  lateral resolution on a Au-I SAM that had been irradiated through a mask and a thin film of (2-ferrocenylethyl)(2',2',2'-trifluoroethyl)amine. SIMS can also detect intact mol. ions M+ corresponding to the 3H-azepine and hydrazine photoadducts obtained upon irradiation of Au-I SAMs in the presence of diethyl- and dibutylamines. Smaller fragment ions characteristic of the 3Hazepine and hydrazine adducts were also observed. The mass assignments were verified by a series of isotopic labeling expts. in which the observed ions displayed the expected isotopic shifts.

- CC 74-1 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
- ST SIM imaging photoreaction selfassembled monolayer azide; aryl azide monolayer photolysis mass spectrometry; lithog photoimaging azide monolayer amine photoreaction; amine photopatterning aryl azide monolayer; surface photochem aryl azide monolayer amine
- IT Lithography

(photo-, surface photochem. to pattern self-assembled monolayers of aryl azide with amines on gold surface and SIMS imaging of ion distribution in)

IT Mass spectra

(secondary-ion, imaging; in photopatterning based on surface photochem. of self-assembled monolayers of

aryl azide with amines on gold surface)

IT Photolysis

(surface, SIMS imaging in photopatterning based on photoreaction of self-assembled monolayers of aryl

azide with amines on gold surface and)

IT 7440-57-5, Gold, processes

RL: PEP (Physical, engineering or chemical process); PROC (Process) (photopatterning based on photochem. reaction of self-assembled monolayers of aryl azide with amines on gold surface)

IT 109-89-7, reactions 111-92-2, Dibutylamine 148149-86-4, Bis(11-(4-azido(benzoyloxy))-1-undecyl) disulfide 148752-29-8 168985-46-4 168985-47-5

RL: PEP (Physical, engineering or chemical process); RCT (Reactant); PROC (Process); RACT (Reactant or reagent)

(photopatterning based on photochem. reaction of  $\mathfrak{sel}\mathfrak{t}-$ 

assembled monolayers of anyl azide with amines on gold surface) ΙT 121195-16-2P 168985-42-0P RL: PEP (Physical, engineering or chemical process); RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); PROC (Process); RACT (Reactant or reagent) (photopatterning based on photochem. reaction of selfassembled monolayers of anyl azide with amines on gold surface) OS.CITING REF COUNT: THERE ARE 21 CAPLUS RECORDS THAT CITE THIS 21 RECORD (21 CITINGS) L47 ANSWER 15 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 1994:469310 HCAPLUS Full-text 121:69310 DOCUMENT NUMBER: ORIGINAL REFERENCE NO.: 121:12261a,12264a Selective Electrochemical Deposition of Polyaniline via Photopatterning of a Monolayer-Modified Substrate Rozsnyai, Lawrence F.; Wrighton, Mark S. AUTHOR(S): CORPORATE SOURCE: Department of Chemistry, Massachusetts Institute of Technology, Cambridge, MA, 02139, USA Journal of the American Chemical Society (1994), SOURCE: 116(13), 5993-4 CODEN: JACSAT; ISSN: 0002-7863 DOCUMENT TYPE: Journal English LANGUAGE: The authors demonstrate that a pattern of electropolymd. aniline replicates the pattern formed by irradiation of a self-assembled monolayer. Selfassembled monolayers of an alkyl thiolate terminating in a photosensitive aryl azide group formed on a Au substrate can be patterned photochem. by near-UV irradiation through a mask in the presence of an amine such as HNEt2, HN(n-Bu)2, or HN(CH2CH2OH)2. Initially, electropolymn. of aniline on such a substrate results in deposition of polyaniline selectively on the unirradiated regions of the surface. While the self-assembled monolayer itself inhibits oxidation of aniline compared to bare Au, the irradiated portions of the surface bearing the amine functional groups inhibit electron transfer to a greater extent than the unirradiated areas. The rate of aniline oxidation can be determined by measuring the c.d. associated with oxidation of  $0.11\ \mathrm{M}$ aniline in aqueous 0.85 M H2SO4, 0.25 M NaHSO4 as a function of potential. Inhibition of polyaniline oxidation depends on the amine used, with HN(n-Bu)2 > HNEt2 > HN(CH2CH2OH)2, and on the potential used in the deposition. Approx. micron-sized polymer features are easily fabricated using this technique. CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes) Section cross-reference(s): 35, 72 ΤT Photolysis (of self-assembled monolayer of disulfides on gold, selective electrochem. deposition of polyaniline by photopatterning in) ΤT Lithography (photo-, selective electrochem. deposition of polyaniline via photopatterning of monolayer-modified gold substrate) 111-42-2, Diethanolamine, reactions TΤ RL: RCT (Reactant); RACT (Reactant or reagent) (photochem. reaction of, with self-assembled monolayer of disulfides on gold, selective electrochem. deposition of polyaniline in) 111-92-2, Dibutylamine ΙT RL: USES (Uses) (photochem. reaction with self-assembled

monolayer of disulfides on gold, electrochem. deposition of polyaniline in)

IT 109-89-7, Diethylamine, reactions

RL: RCT (Reactant); RACT (Reactant or reagent)
(photochem. reaction with self-assembled
monolayer of disulfides on gold, electrochem. deposition of

polyaniline in)

IT 148149-86-4, Bis(11-((4-azidobenzoyl)oxy)-1-undecyl)disulfide

RL: USES (Uses)

(self-assembled monolayer of, on gold,

selective electrochem. deposition of polyaniline via photopatterning

OS.CITING REF COUNT: 68 THERE ARE 68 CAPLUS RECORDS THAT CITE THIS RECORD (68 CITINGS)

L47 ANSWER 16 OF 22 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 1994:334598 HCAPLUS Full-text

DOCUMENT NUMBER: 120:334598

ORIGINAL REFERENCE NO.: 120:58624h,58625a

TITLE: Photosensitive Self-Assembled

Monolayers on Gold: Photochemistry of Surface-Confined Aryl Azide and

Cyclopentadienylmanganese Tricarbonyl

AUTHOR(S): Wollman, Eric W.; Kang, Doris; Frisbie, C. Daniel;

Lorkovic, Ivan M.; Wrighton, Mark S.

CORPORATE SOURCE: Department of Chemistry, Massachusetts Institute of

Technology, Cambridge, MA, 02139, USA

SOURCE: Journal of the American Chemical Society (1994),

116(10), 4395-404

CODEN: JACSAT; ISSN: 0002-7863

DOCUMENT TYPE: Journal LANGUAGE: English

Photosensitive self-assembled monolayers ( SAMs) are prepared by the spontaneous reaction of di-11-(4-azidobenzoate)-1-undecyl disulfide (I), or 11-mercaptoundecylcyclopentadienylmanganese tricarbonyl (II) with polycryst. Au. SAMs of I are photosensitive by virtue of a pendant axyl azide moiety ( $\lambda$ max = 270 nm, log  $\varepsilon$  = 4.2) which undergoes photoreaction with secondary amines to form Au-confined derivs. of 3-H azepine and hydrazine, while Au-II SAMs undergo photosubstitution of phosphine for CO. Au-I SAMs irradiated in the presence of various secondary amines were characterized by reflection absorption IR spectroscopy (RAIRS), XPS, and cyclic voltammetry, and showed persistent attachment of approx. one monolayer of amine. IR spectroscopy was used to establish that primary photoproducts obtained upon irradiation of Au-I SAMs in diethylamine are nearly identical to primary photoproducts obtained upon irradiating an analog of I, Me 4-azidobenzoate, in diethylamine solution XPS anal. of Au-I SAMS before and after irradiation in the presence of secondary amines confirms loss of N2 from the Au-I SAM and incorporation of one nitrogen atom per surface-confined mol. Most definitively, cyclic voltammetry of Au-I after irradiation in the presence of 2-ferrocenylethyl-2',2',2'-trifluoroethylamine (III) showed 3.3 + 10-10 mol-cm-2 of surfaceconfined ferrocene. Pos. ion SIMS spectra of Au-II irradiated in the presence of PPh2Et, PPh2(n-Pr), PPh2(CH2)11Fc (Fc = ferrocenyl), or PPh2(CH2)2(CF2)5CF3, show that introduction of the phosphine onto the surface occurs upon near-UV irradiation Importantly, the surface photochem. of I and II allows the high lateral resolution patterning of Au surfaces and Au microstructures with a variety of mol. reagents. SIMS maps for vinyl ferrocenium (m/z 212) or F- (m/z 19) of flat Au-II substrates irradiated through a Cr-on-glass mask in the presence of PPh2(CH2)11Fc or PPh2(CH2)2(CF2)5CF3 demonstrate photochem. patterning at a lateral resolution of <2  $\mu m$ . SEM confirms the resolution of 2  $\mu m$  features in the irradiated

CC

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RL: USES (Uses)

monolayer. Cyclic voltammetry and SIMS were used to demonstrate that Au microstructures derivatized with I can be patterned with mol. reagents, also at a lateral resolution of  $<2~\mu m$  by UV irradiation through a mask and a thin film of the desired amine. A condensation figure was used to demonstrate photopatterning of a flat Au-I substrate irradiated through a mask and a thin film of (C2H5OH) 2NH. 74-1 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes) surface photolysis axyl azide cyclopentadienylmanganese tricarbonyl; manganese cyclopentadienyl tricarbonyl gold surface photolysis; photoimaging microlithog selfassembled monolayers gold; photoattachment amine phosphine surface modification photopatterning Photoimaging compositions and processes (of self-assembled monolayers of diazidobenzoateundecyl disulfide and mercaptoundecylcyclopentadienylmanganese tricarbonyl on gold in presence of amines and phosphines) Interface (photochem. at, of self-assembled monolayers of aryl azide and cyclopentadienylmanganese tricarbonyl on gold in presence of amine and phosphine reagent) Lithography (photo-, patterning of self-assembled monolayers of diazidobenzoateundecyl disulfide and mercaptoundecylcyclopentadienylmanganese tricarbonyl on gold surface for) Resists (photo-, self-assembled monolayers of diazidobenzoateundecyl disulfide and mercaptoundecylcyclopentadienylmanganese tricarbonyl on gold surface in relation to) Photolysis (surface, of self-assembled monolayers of diazidobenzoateundecyl disulfide and mercaptoundecylcyclopentadienylmanganese tricarbonyl on gold, in presence of amines and phosphines) 155452-33-8P RL: FORM (Formation, nonpreparative); PREP (Preparation) (formation of, in photoimaging reaction of selfassembled monolayers of diazidobenzoateundecyl disulfide on gold surface) 148752-29-8 RL: USES (Uses) (photolysis of self-assembled monolayers of diazidobenzoateundecyl disulfide on gold surface containing, photoimaging in relation to) 109-89-7, Diethylamine, reactions RL: RCT (Reactant); RACT (Reactant or reagent) (photolysis of self-assembled monolayers of diazidobenzoateundecyl disulfide on gold surface containing, photoimaging in relation to) 7650-84-2 607-01-2 154925-69-6 155452-32-7 RL: USES (Uses) (photolysis of self-assembled monolayers of mercaptoundecylcyclopentadienylmanganese tricarbonyl on gold surface containing, photoimaging in relation to) 148149-86-4

(photolysis of self-assembled monolayers

of, on gold surface, photoimaging reaction with amines in) ΙT 135972-97-3 RL: USES (Uses) (photolysis of self-assembled monolayers of, on gold surface, photoimaging reaction with phosphines in) ΙT 111-42-2, Diethanolamine, uses RL: USES (Uses) (photopatterning of self-assembled monolayers of diazidobenzoateundecyl disulfide on gold surface using film of) THERE ARE 94 CAPLUS RECORDS THAT CITE THIS OS.CITING REF COUNT: 94 RECORD (94 CITINGS) ANSWER 17 OF 22 COMPENDEX COPYRIGHT 2009 EEI on STNDUPLICATE 2 T.47 ACCESSION NUMBER: 2004-027809601 COMPENDEX Full-text TITLE: Effect of surface functional groups on nanostructure fabrication using AFM lithography AUTHOR(S): Park Jinyoung; Lee Haiwon Park Jinyoung; Lee Haiwon (Department of Chemistry, CORPORATE SOURCE: Hanyang University, 17 Haengdang-dong, Sungdong-gu, Seoul 133-791 (KR)) EMAIL: haiwon@hanyang.ac.kr SOURCE: Materials Science and Engineering C (5 Jan 2004) Volume 24, Number 1-2, pp. 311-314, 8 refs. ISSN: 0928-4931 DOI: 10.1016/j.msec.2003.09.061 Published by: Elsevier Ltd COUNTRY OF PUBLICATION: United Kingdom DOCUMENT TYPE: Journal; Article; Theoretical; Experimental LANGUAGE: English SUMMARY LANGUAGE: English Entered STN: 4 Jan 2009 ENTRY DATE: Last updated on STN: 4 Jan 2009 The surface functional group dependency of atomic force microscope (AFM) AΒ lithography was investigated using three kinds of self -assembled monolayers (SAMs) as a resist film on silicon wafer. The amine-modified surface of 3aminopropyltriethoxysilane, phenyl-modified surface of phenyltriethoxysilane and methyl-modified surface of octadecyltrichlorosilane SAMs were investigated. The characterizations of these SAMs were carried out by ellipsometer, contact angle goniometer and AFM. The effect of applied voltage of AFM lithography on the line-height and the effect of surface chemical functionality of the resist film on the line-width are discussed in this paper. . COPYRGT. 2003 Elsevier B.V. All rights reserved. ΑN 2004-027809601 COMPENDEX Full-text CC 714.2 Semiconductor Devices and Integrated Circuits; 741.3 Optical Devices and Systems; 931.2 Physical Properties of Gases, Liquids and Solids; 933.1 Crystalline Solids; 941.4 Optical Variables Measurements; 943.3 Special Purpose Instruments CT\*Materials science; Atomic force microscopy; Ellipsometry; Fabrication; Goniometers; Lithography; Nanostructured materials; Self assembly; Silicon wafers ST Resist films ANSWER 18 OF 22 INSPEC (C) 2009 IET on STN DUPLICATE 3 ACCESSION NUMBER: 2002:7256629 INSPEC Full-text DOCUMENT NUMBER: A2002-12-6817-002 Selective deposition of rod-like phthalocyanine TITLE: aggregates on Au surfaces patterned with a combination of microcontact printing and electropolymerization

11/594654 Zangmeister, R.A.P.; O'Brien, D.F.; Armstrong, N.R. AUTHOR: (Dept. of Chem., Arizona Univ., Tucson, AZ, USA) SOURCE: Advanced Functional Materials (March 2002), vol.12, no.3, p. 179-86, 51 refs. CODEN: AFMDC6, ISSN: 1616-301X SICI: 1616-301X(200203)12:3L.179:SDLP;1-T Price: 1616-301X/02/\$17.50+.50/0 Published by: Wiley-VCH, Germany DOCUMENT TYPE: Journal Experimental TREATMENT CODE: COUNTRY: Germany English LANGUAGE: Patterned thin films of a unique phthalocyanine (Pc), (2,3,9,10,16,17,23,24oktakis((2-benzyloxy)ethoxy)phthalocyaninato) copper (1), are created by means of capillary flow of chloroform solutions into micrometer-dimension hydrophobic/hydrophilic channels. These channels are created by a combination of microcontact printing of octadecylmercaptan (C18-SH) layers on gold, creating a hydrophobic channel bottom, and oxidative electropolymerization of m-aminophenol (at pH 4), creating hydrophilic channel walls (microcontact printing/electropolymerization,  $\mu$ CP-EP). The polyphenoxide channel walls grow perpendicular to the substrate plane, with excellent retention of structure to thicknesses (ca. 30 nm) far exceeding the height of the C18-self-assembled monolayer (SAM ). Doping of the C18-SAM layers with small percentages of 1phenyldodecane provides for efficient wetting of the channel bottoms with solutions of 1, consistent with recent studies, which have shown the need for phenyi-termination of substrates surfaces to create coherent rod-like aggregate structures. These optimized channels provide for excellent capillary flow conditions for chloroform solutions of 1, yielding 10  $\mu m$  width Pc films with thicknesses exceeding the height of the polyphenoxide channel walls by up to 10+. We also present evidence for formation of birefringent (ordered) material near the hydrophilic walls 2002:7256629 INSPEC DN A2002-12-6817-002 Full-text ΑN A6817 Monolayers and Langmuir-Blodgett films; A7865T Optical properties CC of organic compounds and polymers (thin films/low-dimensional structures); A8235 Polymer reactions and polymerization; A4760 Flows in ducts, channels, and conduits; A7820F Birefringence (condensed matter); A6130 Liquid crystals birefringence; capillarity; channel flow; discotic liquid crystals; CTLangmuir-Blodgett films; lithography; organic compounds; polymerisation; wetting ST rod-like phthalocyanine aggregates; selective deposition; Au surfaces; microcontact printing; electropolymerization; patterned thin films; (2,3,9,10,16,17,23,24-oktakis((2-benzyloxy)ethoxy)phthalocyaninato) copper; capillary flow; chloroform solutions; micrometer-dimension hydrophobic/hydrophilic channels; octadecylmercaptan layers; hydrophobic channel bottom; m-aminophenol; hydrophilic channel walls; polyphenoxide channel walls; C18-self-assembled monolayer ; 1-phenyldodecane; channel bottom wetting; birefringent material; discotic liquid crystals; liquid crystal confinement; soft lithography; LB films; Au CHI Au sur, Au el EΤ Au; C\*H\*S; SH; S cp; cp; H cp; C18-SH ANSWER 19 OF 22 INSPEC (C) 2009 IET on STN 2009:10551850 INSPEC Full-text ACCESSION NUMBER: TITLE: Sum frequency generation imaging microscopy of patterned self-assembled monolayers with terminal -CH3, -OCH3, -CF2CF3,

AUTHOR:

-C=C, -phenyl, and -cyclopropyl groups

Cimatu, K. (Dept. of Chem., Univ. of Houston, Houston,

TX, USA), Moore, H.J. (Dept. of Chem., Univ. of Houston, Houston, TX, USA), Barriet, D. (Dept. of Chem., Univ. of Houston, Houston, TX, USA),

Chinwangso, P. (Dept. of Chem., Univ. of Houston, Houston, TX, USA), Lee, T.R. (Dept. of Chem., Univ. of Houston, Houston, TX, USA), Baldelli, S. (Dept. of

Chem., Univ. of Houston, Houston, TX, USA)

SOURCE: Journal of Physical Chemistry C (18 Sept. 2008),

vol.112, no.37, p. 14529-37, 47 refs.ISSN: 1932-7447

Published by: American Chemical Society, USA

DOCUMENT TYPE: Journal
TREATMENT CODE: Experimental
COUNTRY: United States

LANGUAGE: English

Vibrational spectroscopic imaging is demonstrated for a variety of organic monolayer-functionalized surfaces patterned using microcontact printing. The images from sum frequency generation imaging microscopy (SFGIM) are analyzed using different contrast mechanisms in the interpretation of the transition from stamped to backfilled regions of interest. For this experiment, microcontact printing is used to spatially control the surface monolayers by using a patterned stamp and by varying the terminal functional group of the backfilling solutions. Analysis by the three different methods suggests that significant mixing occurs between the stamped and backfilled regions, which influence the contrast in the images at the resonant peaks. In addition, the interference between the resonant peaks and nonresonant background also has an effect on the appearance of the image.

AN 2009:10551850 INSPEC Full-text

- CC A6817 Monolayers and Langmuir-Blodgett films; A4265K Optical harmonic generation, frequency conversion, parametric oscillation and amplification; A7830J Infrared and Raman spectra in organic crystals; A8116R Nanopatterning; A6845D Adsorption and desorption kinetics; evaporation and condensation; A8265M Sorption and accommodation coefficients (surface chemistry)
- CT adsorption; gold; monolayers; nanopatterning; optical frequency conversion; organic compounds; self-assembly; soft lithography; vibrational modes
- sum frequency generation imaging microscopy; patterned selfassembled monolayers; cyclopropyl groups;
  phenyl groups; vibrational spectroscopic imaging; organic
  monolayer-functionalized surfaces; microcontact printing; terminal
  functional group; interference; CH3 group; OCH3 group; CF2CF3 group; C=C
  group; adsorption; Au

CHI Au sur, Au el

ET C\*F; CF3; C cp; cp; F cp; C; Au; C\*H; CH3; H cp; C\*H\*O; OCH3; O cp; CF2CF3

L47 ANSWER 20 OF 22 SCISEARCH COPYRIGHT (c) 2009 The Thomson Corporation on STN

ACCESSION NUMBER: 2003:1006773 SCISEARCH Full-text

THE GENUINE ARTICLE: 741XC

TITLE: Formation, characterization, and sub-50-nm patterning of

organosilane monolayers with embedded disulfide bonds: An

engineered self-assembled

monolayer resist for electron-beam

lithography

AUTHOR: Lieberman M (Reprint)

CORPORATE SOURCE: Univ Notre Dame, Dept Chem & Biochem, Notre Dame, IN 46556

USA (Reprint)

AUTHOR: Wang X J; Hu W C; Ramasubramaniam R; Bernstein G H; Snider

G

CORPORATE SOURCE: Univ Notre Dame, Dept Elect Engn, Notre Dame, IN 46556 USA

COUNTRY OF AUTHOR: USA

SOURCE:

LANGMUIR, (11 NOV 2003) Vol. 19, No. 23, pp. 9748-9758.

ISSN: 0743-7463.

PUBLISHER: AMER CHEMICAL SOC, 1155 16TH ST, NW, WASHINGTON, DC 20036

USA.

DOCUMENT TYPE: Article; Journal

LANGUAGE: English REFERENCE COUNT: 49

ENTRY DATE: Entered STN: 8 Dec 2003

Last Updated on STN: 8 Dec 2003

\*ABSTRACT IS AVAILABLE IN THE ALL AND IALL FORMATS\*

AB This paper describes self-assembled monolayers (SAMs) that contain embedded disulfide bonds and the selective cleavage of the disulfides by electron-

beam lithography (EBL). Phenyl

(3-trimethoxysilylpropyl)-disulfide (1) forms siloxane SAMs with a root-mean-square roughness of 1.8 Angstrom. The disulfide bonds in I remain intact in the SAM and can react with dithiothreitol after monolayer formation, forming surface thiols, which can be derivatized with maleimide dyes. Atomic force microscopy (AFM) anodization and EBL have been used to create high-resolution patterns on the disulfide-containing monolayer. AFM anodization on monolayer I achieves 20-nm resolution lines with both topographic and chemical alterations in the patterned region. EBL with an accelerating voltage of 30 kV generates trenches 3-4 Angstrom deep and 30 nm wide. According to AFM topographic and friction images, X-ray photoelectron spectroscopy damage simulation, and chemical rebinding tests, the chemical changes induced by EBL are consistent with cleavage of the disulfide bonds to form sulfhydryl groups. The resulting chemical patterns can be further developed by reaction with N-(1-pyrene)maleimide.

CC CHEMISTRY, PHYSICAL

STP KeyWords Plus (R): RAY PHOTOELECTRON-SPECTROSCOPY; CONSTRUCTIVE NANOLITHOGRAPHY; SURFACE MODIFICATION; SILICON; NANOFABRICATION; TEMPLATES; DAMAGE; PHOTOCHEMISTRY; MICROSCOPE; NANOWIRES \*ABSTRACT IS AVAILABLE IN THE ALL AND IALL FORMATS\*

 ${\tt L47}$  ANSWER 21 OF 22 SCISEARCH COPYRIGHT (c) 2009 The Thomson Corporation on

STN

ACCESSION NUMBER: 2003:414800 SCISEARCH Full-text

THE GENUINE ARTICLE: 676ZB

TITLE: Sub-100-nm pattern formation through selective chemical

transformation of self-assembled monolayers by soft X-ray irradiation

AUTHOR: Park J W (Reprint)

CORPORATE SOURCE: Pohang Univ Sci & Technol, Div Mol & Life Sci, Dept Chem,

Ctr Integrated Mol Syst, San 31 Hyoja Dong, Pohang 790784,

South Korea (Reprint)

AUTHOR: La Y H; Jung Y J; Kim H J; Kang T H; Ihm K; Kim K J; Kim B

CORPORATE SOURCE: Pohang Univ Sci & Technol, Div Mol & Life Sci, Dept Chem,

Ctr Integrated Mol Syst, Pohang 790784, South Korea; Pohang Accelerator Lab, Pohang 790784, South Korea

COUNTRY OF AUTHOR: South Korea

SOURCE: LANGMUIR, (13 MAY 2003) Vol. 19, No. 10, pp. 4390-4395.

ISSN: 0743-7463.

PUBLISHER: AMER CHEMICAL SOC, 1155 16TH ST, NW, WASHINGTON, DC 20036

USA.

DOCUMENT TYPE: Article; Journal

LANGUAGE: English REFERENCE COUNT: 87

ENTRY DATE: Entered STN: 30 May 2003

Last Updated on STN: 30 May 2003

\*ABSTRACT IS AVAILABLE IN THE ALL AND IALL FORMATS\*

AΒ A new nanopatterning system based on a soft X-ray induced chemical transformation of a nitro-substituted aromatic imine monolayer has been developed. The molecular layer was exposed to soft X-rays, and the involved chemical transformation on the molecular layer was analyzed by using Fourier transform infrared reflection-absorption spectroscopy. As a result, we could confirm that the nitro group on the imine monolayer was cleaved upon the soft X-ray irradiation, leaving the hydrophobic phenyl unit intact on the monolayer surface, while the imine functionality was transformed into a new nonhydrolyzable one. However, the source of the hydrogen atom for the reduction and the final functionality at the para position of the aromatic group are unknown yet. Whereas, we could restore the hydrophilic amine functionality from the unexposed imine monolayer through hydrolysis, These phenomena were applied to the patterning of selfassembled monolayers featuring alternating height, chemical reactivity, and wettability. Alternating surface wettability is evident when water is sprayed on a macroscopically patterned substrate and the plate is tilted to drip the water. Also, atomic force microscope images revealed patterns as small as less than or equal to 100 nm with regular height and phase variations. The patterned monolayer was further modified with a linker and Cy3-tagged oligonucleotide, sequentially. Fluorescence images showed that the above molecules were selectively immobilized onto the amine-terminated region of the patterned surface.

CC CHEMISTRY, PHYSICAL

STP KeyWords Plus (R): ELECTRON-BEAM LITHOGRAPHY; OPTICAL LITHOGRAPHY; PHOTOELECTRON-SPECTROSCOPY; SURFACE-DENSITY; THIN-LAYERS; AMINE GROUP; SENSORS; FUTURE; DAMAGE; RESOLUTION \*ABSTRACT IS AVAILABLE IN THE ALL AND IALL FORMATS\*

L47 ANSWER 22 OF 22 SCISEARCH COPYRIGHT (c) 2009 The Thomson Corporation on

STN

ACCESSION NUMBER: 1999:332481 SCISEARCH <u>Full-text</u>

THE GENUINE ARTICLE: 189YV

TITLE: Surface functionalization and imaging using monolayers and

surface-grafted polymer layers

AUTHOR: Bianconi P A (Reprint)

CORPORATE SOURCE: Univ Massachusetts, Dept Chem, Amherst, MA 01003 USA

(Reprint)

AUTHOR: Ingall M D K; Honeyman C H; Mercure J V; Kunz R R

CORPORATE SOURCE: Penn State Univ, Dept Chem, University Pk, PA 16802 USA;

MIT, Lincoln Lab, Lexington, MA 02173 USA

COUNTRY OF AUTHOR: USA

SOURCE: JOURNAL OF THE AMERICAN CHEMICAL SOCIETY, (21 APR 1999)

Vol. 121, No. 15, pp. 3607-3613.

ISSN: 0002-7863.

PUBLISHER: AMER CHEMICAL SOC, 1155 16TH ST, NW, WASHINGTON, DC 20036

USA.

DOCUMENT TYPE: Article; Journal

LANGUAGE: English

REFERENCE COUNT: 67

ENTRY DATE: Entered STN: 1999

Last Updated on STN: 1999

\*ABSTRACT IS AVAILABLE IN THE ALL AND IALL FORMATS\*

AB A method of surface functionalization of ceramics with monolayers and surface grafted polymer layers is described. A phenylsilane monolayer is created on the substrate's oxide surface by using phenyltrichlorosilane as the silane coupling agent. To control the formation of the monolayer and ensure the growth of a dense, homogeneous layer, the ceramic surface is first dried and then a controlled amount of water is adsorbed onto it, and a hindered organic base is added to the phenyltrichlorosilane solution to

absorb acid generated in the reaction of the silane coupling agent with hydroxyl groups on the ceramic surface. This procedure results in dense homogeneous phenylsilane monolayers on a variety of surfaces, including silicon, Pt/PtO, and quartz. These layers can now be functionalized by addition of triflic acid, which removes the phanyl ring as benzene, and introduction of a nucleophile. Monolayers of -C=CH, -OCH2CF3, [(OCH2CH2)(2)0], -OCH2CF2CF3, and -O(CH2)(6)NH2 were generated in this fashion, all proving to be continuous and homogeneous. In addition, the cationic silvl triflate site generated by the removal of the phenyl ring is capable of initiating polymerization to form covalently bound polymer layers on the surface. Polymer layers of poly(methyl methacrylate), poly(propylene oxide), and poly(dimethylsiloxane) were generated in this manner; in the case of poly (dimethylsiloxane), layers up to 300 Angstrom thick were formed. Anionic initiation of polymerization is also possible, using a bromopropyl trichlorosilane coupling agent to form the initial monolayer, followed by lithiation with lithium di-tert-butylbiphenyl. Acrylonitrile can be anionically polymerized to films of up to 2450 Angstrom in thickness. The monolayers and polymer layers were characterized by XPS, AFM, contact angle measurements, and profilometry and were found to be continuous. The initial phenylsilane monolayer can be lithographically patterned by using 193 nm Light to cleave the surface phanyl groups; the remaining groups can then be functionalized as discussed above to create surface-grafted patterned polymer layers.

- CC CHEMISTRY, MULTIDISCIPLINARY
- STP KeyWords Plus (R): SELF-ASSEMBLED MONOLAYERS
  - ; COPLANAR MOLECULAR ASSEMBLIES; CHEMICAL-VAPOR-DEPOSITION; CATIONIC POLYMERIZATION; THIN-FILMS; NEGATIVE RESIST; EDGE ROUGHNESS; ACID-DIFFUSION; GOLD; SOLVENT
  - \*ABSTRACT IS AVAILABLE IN THE ALL AND IALL FORMATS\*

# \*\*\*\*\* SEARCH HISTORY \*\*\*\*\*

=> d his nofi

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(FILE 'HOME' ENTERED AT 14:31:42 ON 28 OCT 2009)
    FILE 'HCAPLUS' ENTERED AT 14:31:59 ON 28 OCT 2009
             1 SEA ABB=ON PLU=ON US20070140901/PN
L1
               D IALL
     FILE 'REGISTRY' ENTERED AT 14:33:24 ON 28 OCT 2009
             1 SEA ABB=ON PLU=ON 2396-01-2/RN
L2
             1 SEA ABB=ON PLU=ON 92-52-4/RN
L3
T. 4
             1 SEA ABB=ON PLU=ON 26140-60-3/RN
L5
             1 SEA ABB=ON PLU=ON 37361-95-8/RN
L6
             1 SEA ABB=ON PLU=ON 37275-48-2/RN
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          942 SEA ABB=ON PLU=ON SURFACE(W)MODIF? (3A) LAYER?
L7
          18364 SEA ABB=ON PLU=ON ((SELF(W)ASSEMBL?)(W) (MONOLAYER# OR
L8
               MONO(W)LAYER#))
         14707 SEA ABB=ON PLU=ON "SAM"
L9
L10
       1828847 SEA ABB=ON PLU=ON PHENYL OR BIPHENYL OR TERPHENYL
         70335 SEA ABB=ON PLU=ON ANTHRACYL OR NAPHTHYL OR BIPYRIDYL OR
L11
               TERPYRIDYL
          6620 SEA ABB=ON PLU=ON THIOPHENYL OR BITHIENYL OR TERTHIENYL OR
L12
               PYRROLYL
            12 SEA ABB=ON PLU=ON (BI OR TRI)(W) CYCLOALKANE# OR TETRA(W)CYCL
L13
               OALKANE#
L14
          2116 SEA ABB=ON PLU=ON (L8 OR L9) AND ((L10 OR L11 OR L12 OR
               L13))
L15
             1 SEA ABB=ON PLU=ON L14 AND L7
               D SCA TI HIT
          48885\ \text{SEA}\ \text{ABB=ON}\ \text{PLU=ON}\ \text{(L2 OR L3 OR L4 OR L5 OR L6)}
L16
L17
            24 SEA ABB=ON PLU=ON (L8 OR L9) AND L16
L18
             7 SEA ABB=ON PLU=ON L17 AND 66/SC, SX
               D SCA TI HIT
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        245508 SEA ABB=ON PLU=ON ARYL
T.19
L20
         21238 SEA ABB=ON PLU=ON ALICYCLIC
           165 SEA ABB=ON PLU=ON (L8 OR L9) AND (L19 OR L20)
             1 SEA ABB=ON PLU=ON L21 AND L1
L22
            69 SEA ABB=ON PLU=ON L21 AND 66/SC,SX
L23
             1 SEA ABB=ON PLU=ON L23 AND L7
L24
L25
             4 SEA ABB=ON PLU=ON L23 AND (SURFACE(W)MODIF?)
              D SCA TI HIT
L26
            8 SEA ABB=ON PLU=ON L21 AND LITHOGRAPH?
L27
            10 SEA ABB=ON PLU=ON (L24 OR L25 OR L26)
            46 SEA ABB=ON PLU=ON L21 AND ((L10 OR L11 OR L12 OR L13))
L28
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L29
             9 SEA ABB=ON PLU=ON L28 AND (SURFAC?) (2A) (TRANSIT? OR MODIF?
L30
               OR PATTERN?)
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            17 SEA ABB=ON PLU=ON L27 OR L30
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L32
L33
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FILE 'WPIX' ENTERED AT 15:11:30 ON 28 OCT 2009
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               L13))
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L35
               D TI KWIC
               D TI KWIC 2-5
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L36
               OR PATTERN?)
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L37
L38
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L39
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L40
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    15:18:20 ON 28 OCT 2009
L41
           102 SEA ABB=ON PLU=ON L35
             11 SEA ABB=ON PLU=ON L41 AND (SURFAC?) (2N) (TRANSIT? OR MODIF?
L42
               OR PATTERN?)
             1 SEA ABB=ON PLU=ON L41 AND (ARYL OR HETERO(W) ARYL OR
L43
               ALICYCLIC OR HETERO(W) CYCLIC)
L44
             11 SEA ABB=ON PLU=ON L42 OR L43
               D SCA L43
               SAVE TEMP L44 LEE654MULTI/A
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FILE 'WPIX' ENTERED AT 15:21:47 ON 28 OCT 2009

SEL L40 AP PN L45 18 SEA ABB=ON PLU=ON (WO2002-EP14769/AP OR WO2005-GB1159/AP OR US2001-350090P/AP OR US2002-284794/AP OR WO2000-US25518/AP OR AU2002-321990/AP OR AU2002-358799/AP OR AU2002-365147/AP OR AU2002-367538/AP OR AU2002321990/PN OR AU2002358799/PN OR AU2002365147/PN OR AU2002367538/PN OR AU2003-233579/AP OR AU2003233579/PN OR CN2005-10087971/AP OR GB2006-18673/AP OR GB2426724/PN OR US2002-381913P/AP OR US2003-441965/AP OR WO2002-US34970/AP OR WO2002-US35134/AP OR WO2003-US15757/AP OR WO2005-US8850/AP OR WO2005089415/PN OR WO2007-US19894/AP OR WO2008108809/PN OR AU2001-32614/AP OR AU2001032614/PN OR "CN100539201 C"/PN OR CN1734792/PN OR CN1958301/PN OR CN2006-10 143605/AP OR DE10164309/PN OR DE2001-10164309/AP OR EP1441695/P N OR EP1461619/PN OR EP1509336/PN OR EP1542869/PN OR EP1630883/ PN OR EP1782886/PN OR EP2000-991376/AP OR EP2002-793118/AP OR EP2002-803299/AP OR EP2003-729016/AP OR EP2005-23880/AP OR EP2005-254258/AP OR JP2001-530895/AP OR JP2003-556808/AP OR JP2004518268/PN OR JP2005-216748/AP OR JP2005524829/PN OR JP2006049890/PN OR JP2007-274254/AP OR JP2008183702/PN OR KR2007-8357/AP OR KR825176/PN OR TW2000-119232/AP OR TW463183/P N OR US1999-154716P/AP OR US1999-157149P/AP OR US2000-527885/AP OR US2000-551716/AP OR US2001-335165P/AP OR US2001-864384/AP OR US2002-287935/AP OR US2002-307069/AP OR US20020177083/PN OR US2003-421355/AP OR US20030142901/PN OR US2004-494122/AP OR US2004-500425/AP OR US2004-555770P/AP OR US2004-900624/AP OR US20040014186/PN OR US20040087177/PN OR US20040102050/PN OR US2005-83739/AP OR US20050048570/PN OR US20050221081/PN OR US20050227232/PN OR US2006-390405/AP OR US2006-477655/AP OR US2006-594654/AP OR US20060021647/PN OR US20060263033/PN OR

US2007-757018/AP OR US20070098899/PN OR US20070140901/PN OR US20080182072/PN OR US6586158/PN OR US6756605/PN OR US6893966/PN OR US7020355/PN OR US7381789/PN OR WO2001027972/PN OR WO2002-US3885/AP OR WO2002095787/PN OR WO2003055590/PN OR WO2003056336/PN OR WO2003076082/PN OR WO2003099465/PN OR WO2005092516/PN)

FILE 'HCAPLUS' ENTERED AT 15:22:08 ON 28 OCT 2009 L46 16 SEA ABB=ON PLU=ON L32 NOT L45

FILE 'STNGUIDE' ENTERED AT 15:22:37 ON 28 OCT 2009
D OUE L40

FILE 'WPIX' ENTERED AT 15:23:27 ON 28 OCT 2009
D L40 1-14 IALL ABEQ TECH ABEX

FILE 'STNGUIDE' ENTERED AT 15:23:38 ON 28 OCT 2009

D QUE L46

D QUE L44

FILE 'HCAPLUS, COMPENDEX, INSPEC, SCISEARCH, PASCAL' ENTERED AT 15:24:08 ON 28 OCT 2009

L47

22 DUP REM L46 L44 (5 DUPLICATES REMOVED)

ANSWERS '1-16' FROM FILE HCAPLUS

ANSWER '17' FROM FILE COMPENDEX

ANSWERS '18-19' FROM FILE INSPEC

ANSWERS '20-22' FROM FILE SCISEARCH

D L47 1-16 IBIB ABS HITIND D L47 17-22 IBIB AB IND